Tracking detectors and Triggering at the LHC

P. Silva (CERN)
Course on Physics at the LHC
LIP, 7th March 2016

Tracking

Simplified overview of the LHC detectors concept

- **Inner tracking**
  - minimal interference with the event
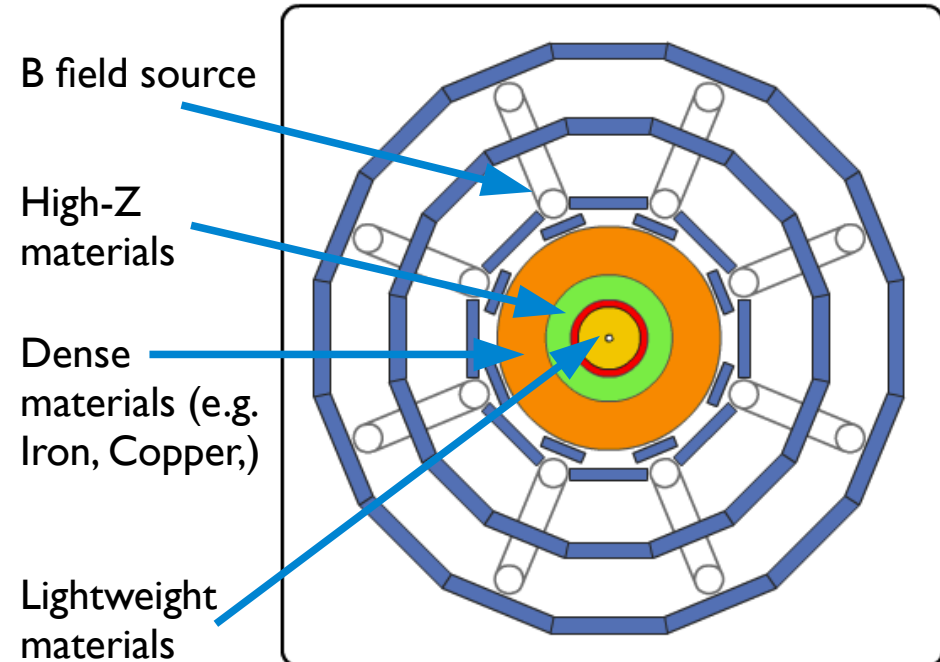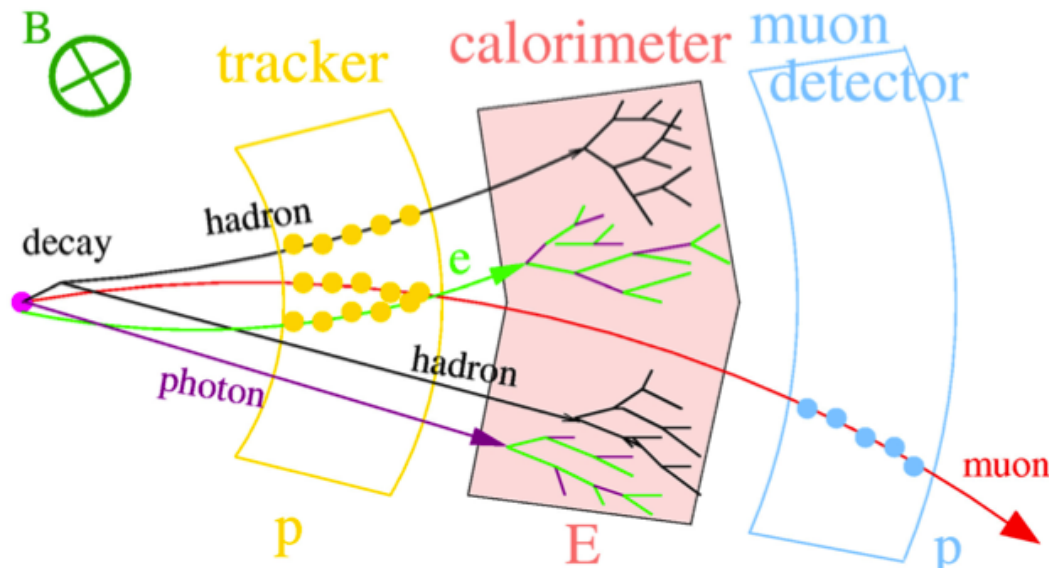 - identify and measure charged particles

- **Calorimetry**
  - absorb electromagnetic and hadronic E
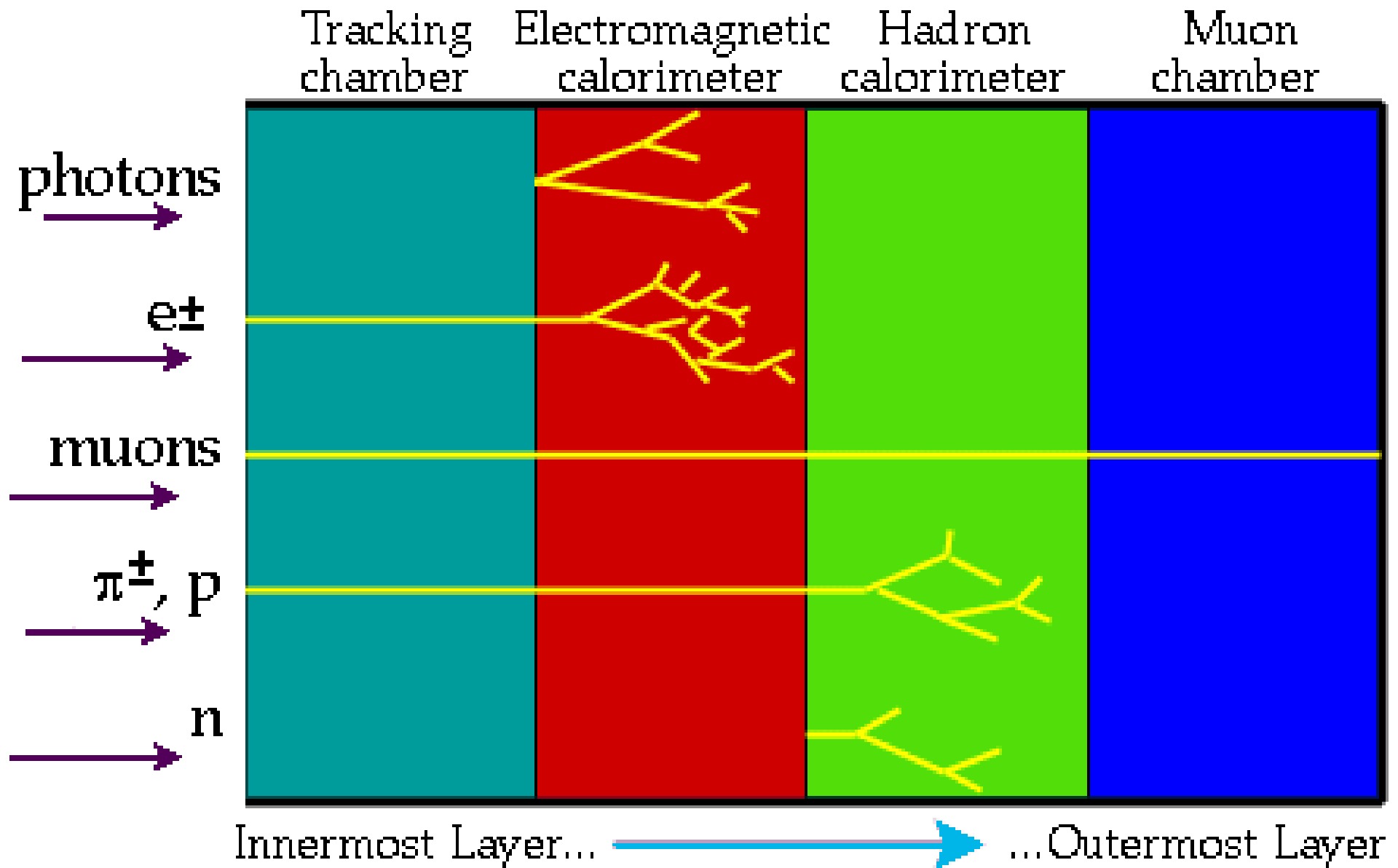 - avoid leakages $\rightarrow$ hermetic

- **Outer tracking**
  - Weakly interacting charged particles: muons
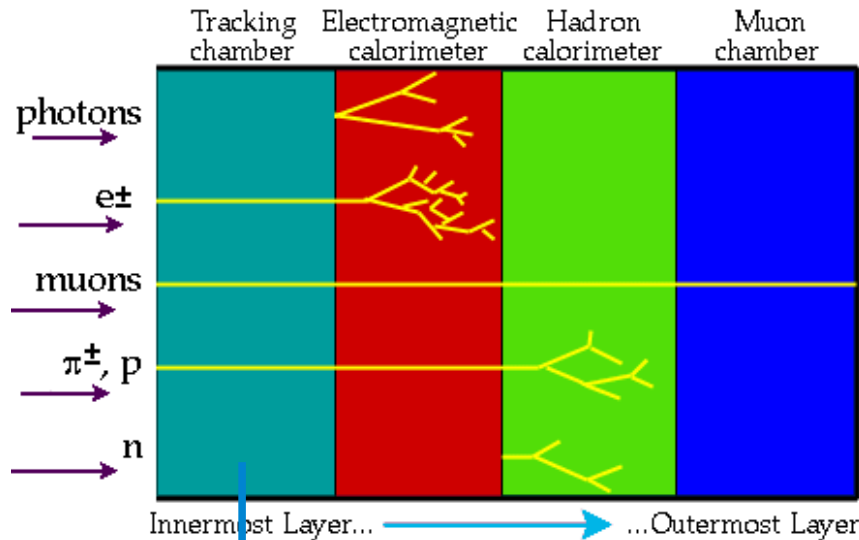
- **Magnetic field**
  - Field integral: B.r
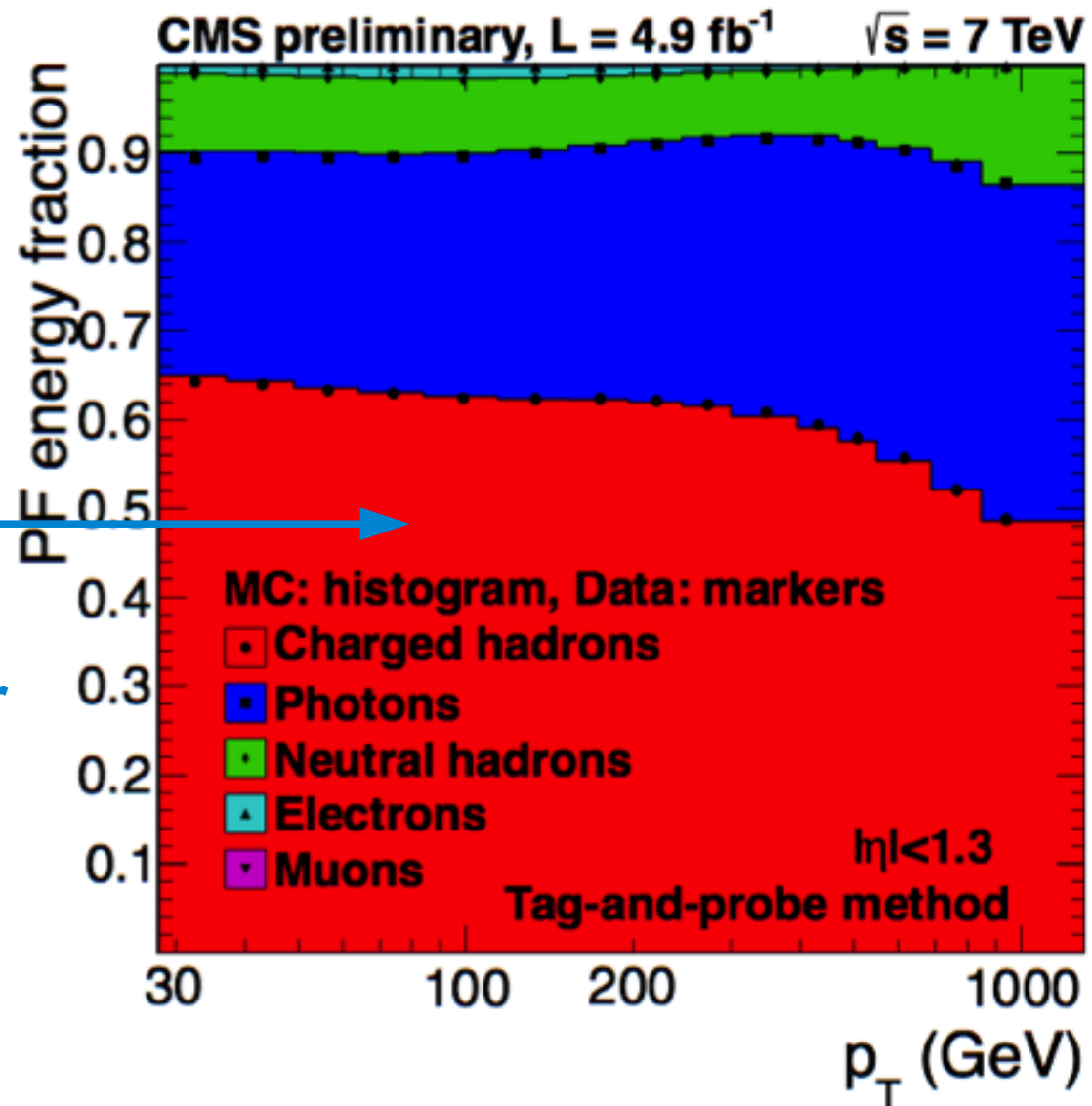 - Crucial for particle separation and p measurement

B field source

High-Z materials

Dense materials (e.g. Iron, Copper,)

Lightweight materials

Particles and their decays

Particles and their decays

Tracking chamber | Electromagnetic calorimeter | Hadron calorimeter | Muon chamber

photons

e±

muons

π±, p

n

Innermost Layer... → ...Outermost Layer

>60% of the energy of a jet may be reconstructed at the level of the tracker

CMS preliminary, L = 4.9 fb⁻¹   √s = 7 TeV

PF energy fraction

MC: histogram, Data: markers
⊡ Charged hadrons
▪ Photons
▪ Neutral hadrons
▪ Electrons
▪ Muons

|η|<1.3
Tag-and-probe method

p_T (GeV)

Tracking: why?

- Identify the **hard interaction vertex**

- Reconstruct **secondary vertices** from long lived particles

- Measure **particle trajectories**

  → Momentum (p)

  → Energy loss (dE/dx)

  → Link to calorimeters (identify electrons, conversions)

 → Link to muon chambers : inner leg for muon reconstruction

Tracking: why?

- Identify the **hard interaction vertex**

- Reconstruct **secondary vertices** from long lived particles

- Measure **particle trajectories**

  - Momentum (p)

  - Energy loss (dE/dx)

  - Link to calorimeters (identify electrons, conversions)

  - Link to muon chambers : inner leg for muon reconstruction

JHEP 07 (2013) 122

PRD 89, 012003 (2014)

arXiv:1411.4413

sub.to Nature
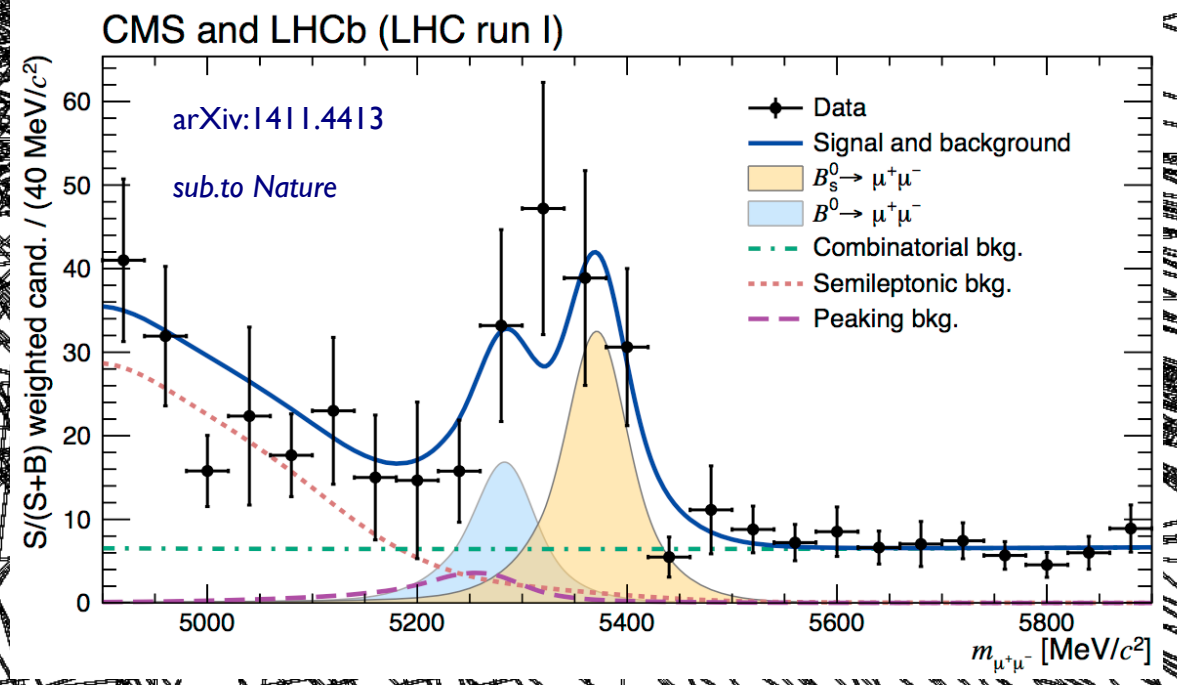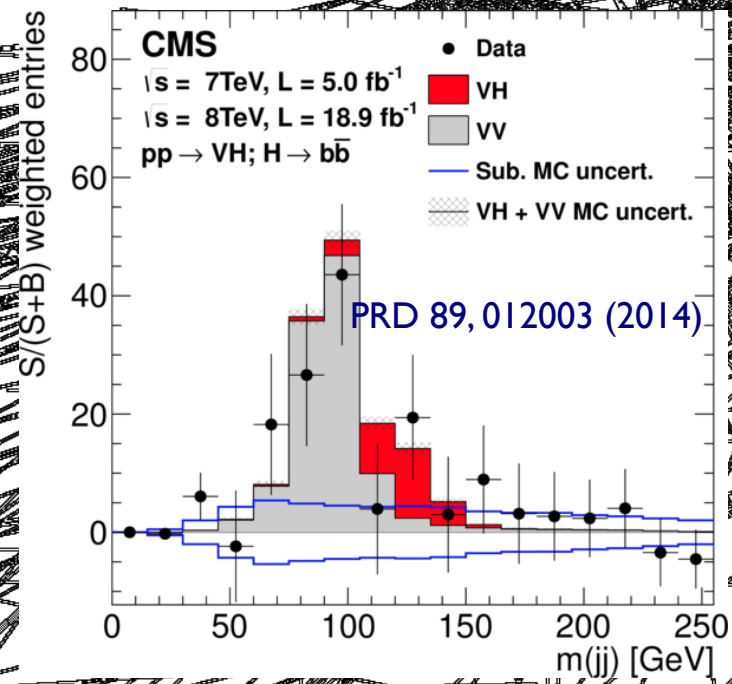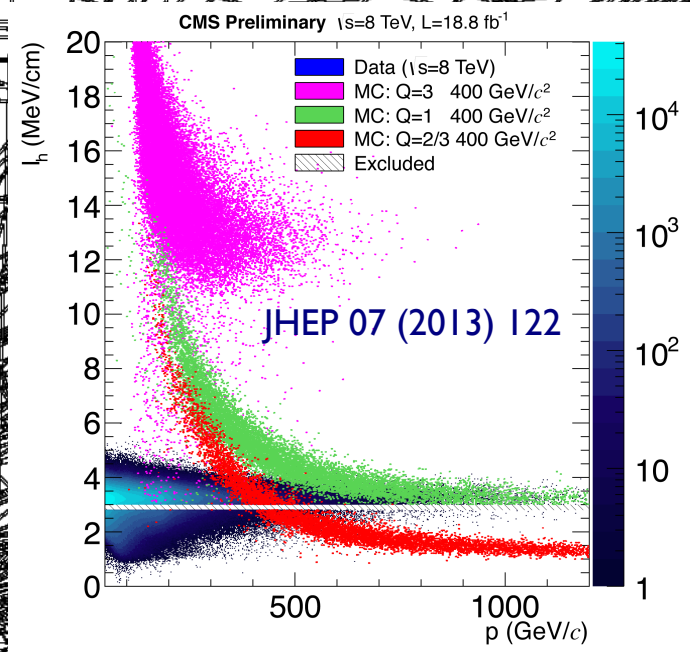
Usage of Si-based trackers for HEP

- **Kemmer, 1979** transferred Si-technology for electrons to detector - NIM 169(1980)499

- **NA11/32** spectrometer at CERN ▶

  - 6 planes Si-Strip, <2k channels

  - Resolution ~4.5μm

- **SLD** vertex detector at SLAC ▶

  - 120-307 M pixels: 0.4%X0

  - Resolution <4μm, d_0~11-9μm

- **ALEPH** detector at LEP ▶

  - Enable precise measurements for B-physics (lifetime, b-tagging)
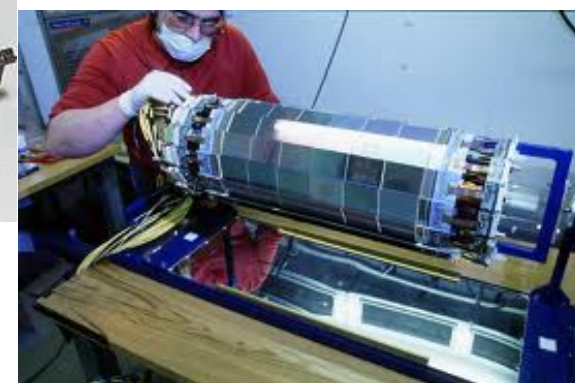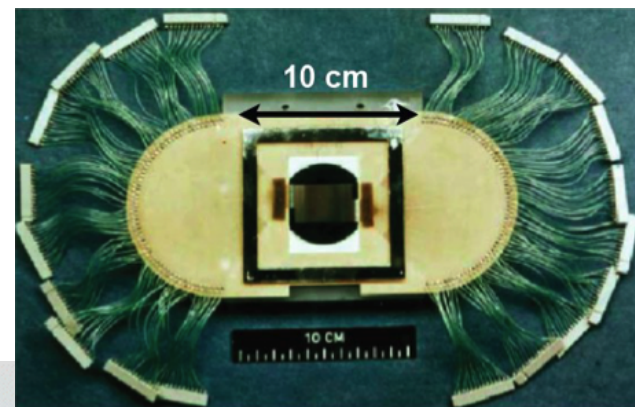
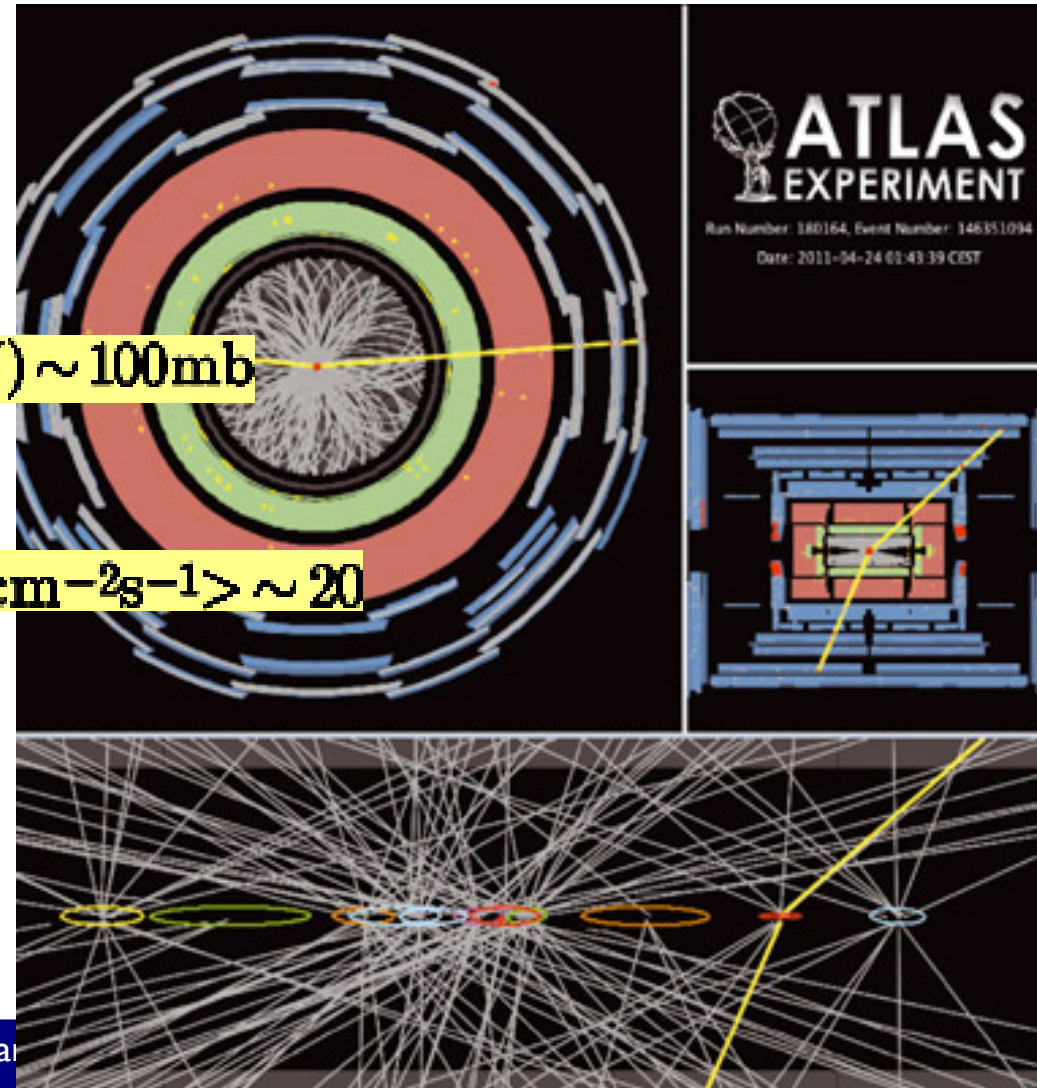| Experiment	Detectors	Channels (10^3)	Si area [m^2]
Aleph (LEP)	144	95	0.49
CDF II (TEV)	720	405	1.9
D0 II (TEV)	768	793	4.7
AMS II	2300	196	6.5
ATLAS (LHC)	4088	6300	61
CMS (LHC)	15148	10000	200

- Resolve 25 ns bunch crossings, keep low occupancy in high pileup regime

- Radiation hard, low material budget in front of calorimeters

- Good momentum resolution, and high efficiency

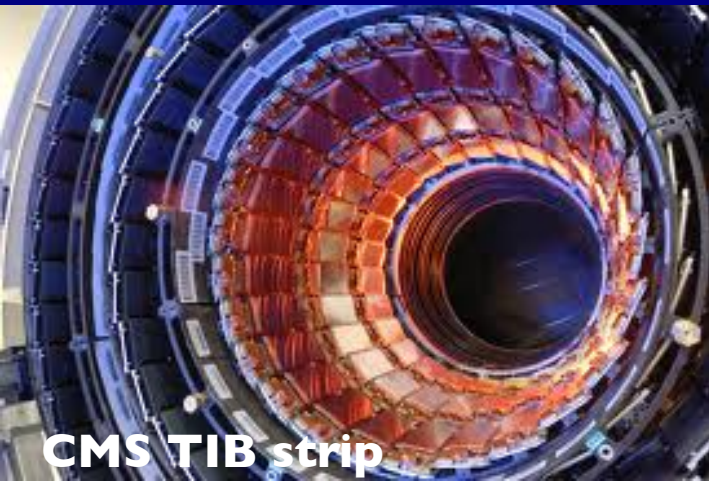- Identify b-jets and hadronically decaying tau leptons (τ)

PYTHIA6.214 - tuned

PHOJET1.12
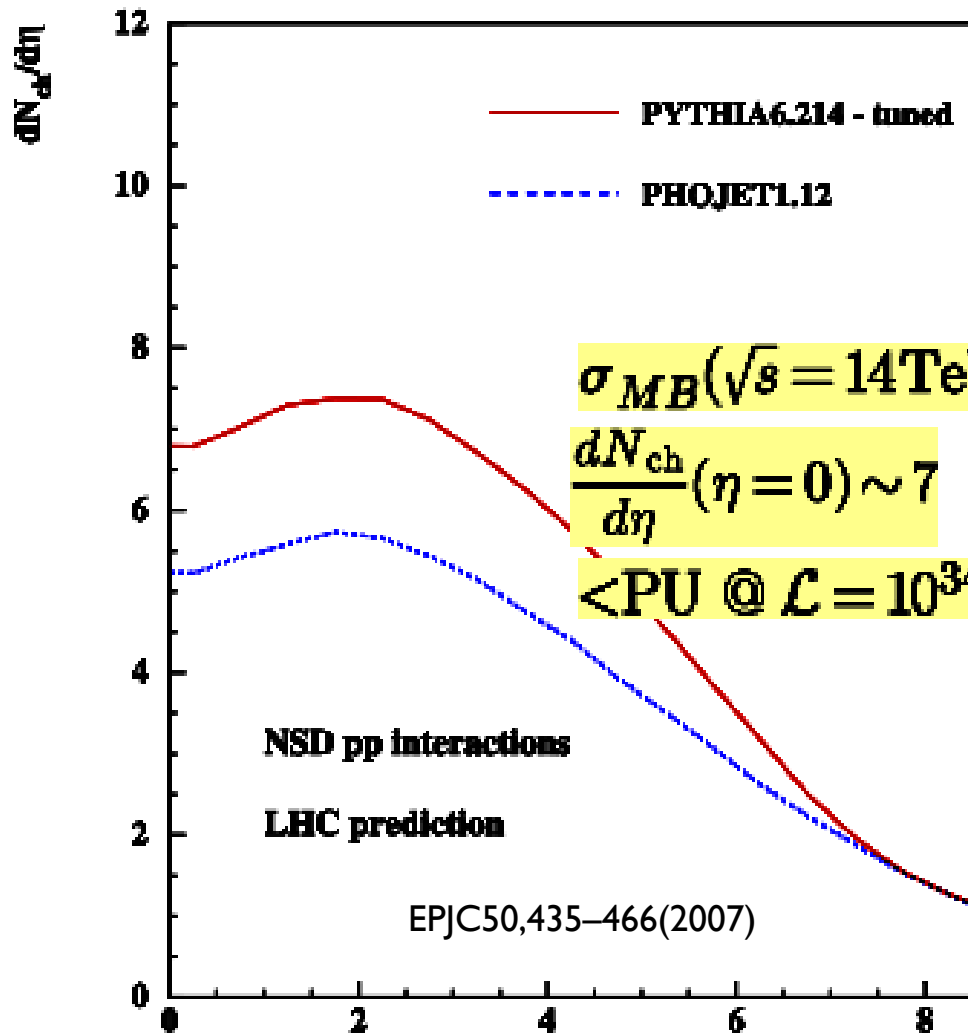
$\sigma_{MB}(\sqrt{s} = 14\,\text{TeV}) \sim 100\,\text{mb}$

$\dfrac{dN_{ch}}{d\eta}(\eta = 0) \sim 7$

$<\text{PU} @ \mathcal{L} = 10^{34}\text{cm}^{-2}\text{s}^{-1}> \sim 20$
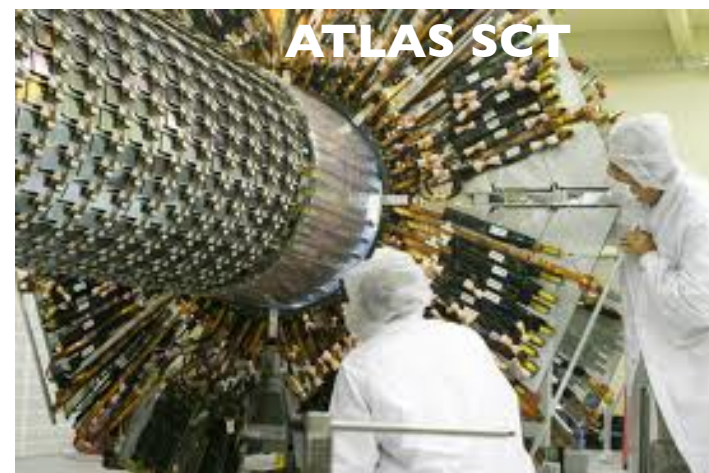
NSD pp interactions

LHC prediction
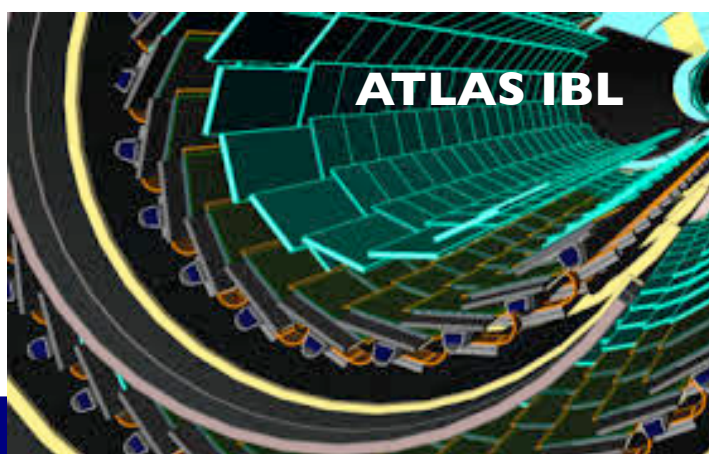
EPJC50,435–466(2007)

CMS TIB strip
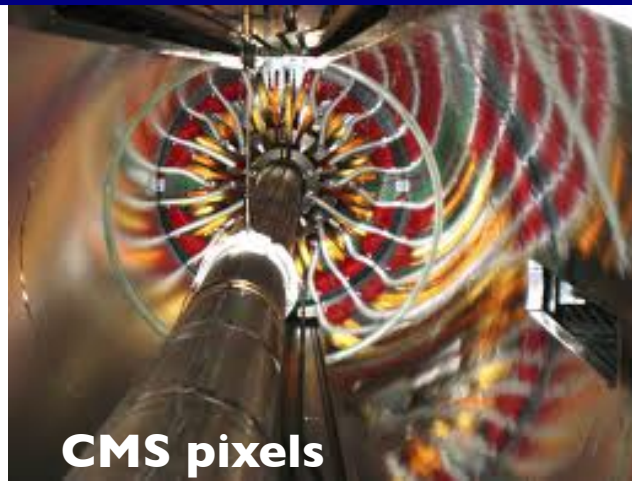
CMS pixels

LHCb VELO

ATLAS SCT

ALICE pixels

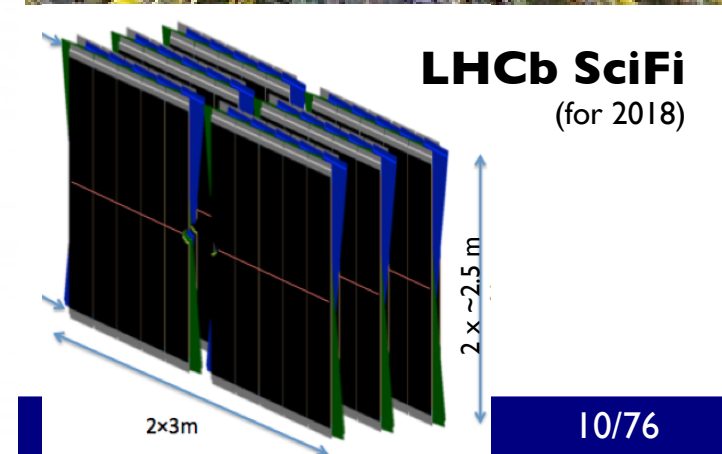ATLAS pixels

ATLAS IBL
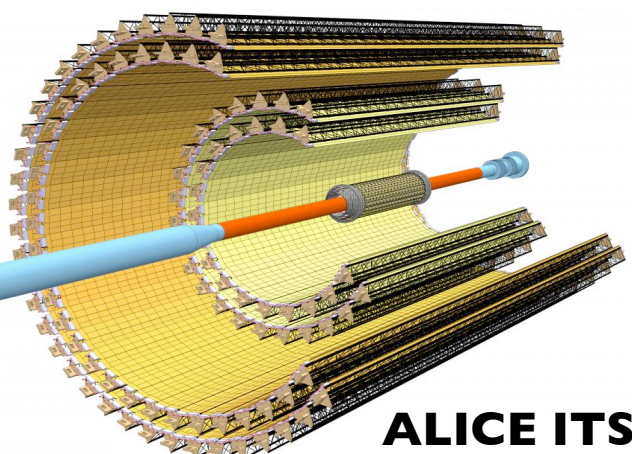
ALICE ITS

LHCb SciFi
(for 2018)

$2 \times {\sim}2.5$ m

2×3 m

Tracking: what?

- While transversing a medium a **charged particle leaves an ionization trace**

  - create a depletion zone in between electrodes: gaseous, liquid or solid-state (semi-conductor)

  - ionization charges drift towards electrodes

  - amplify electric charge signal and deduce position from signals collected in individual strips

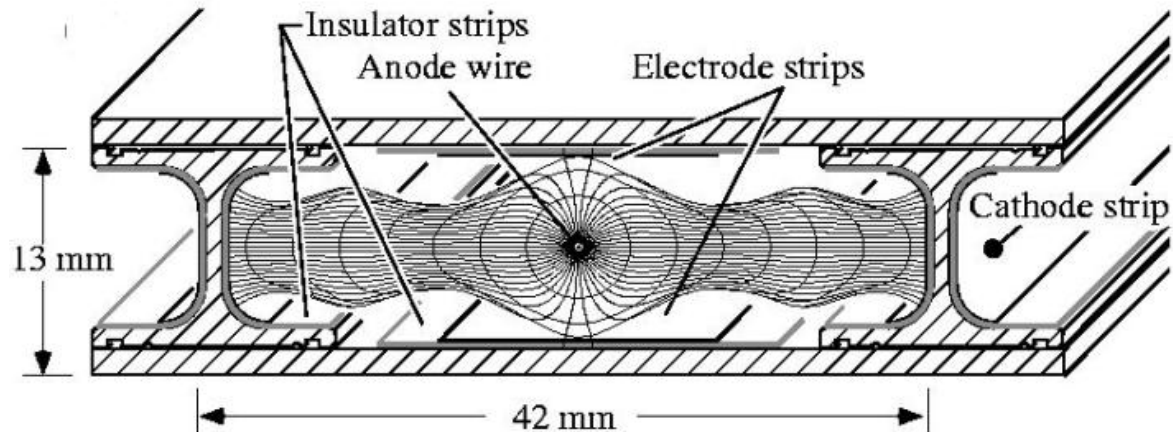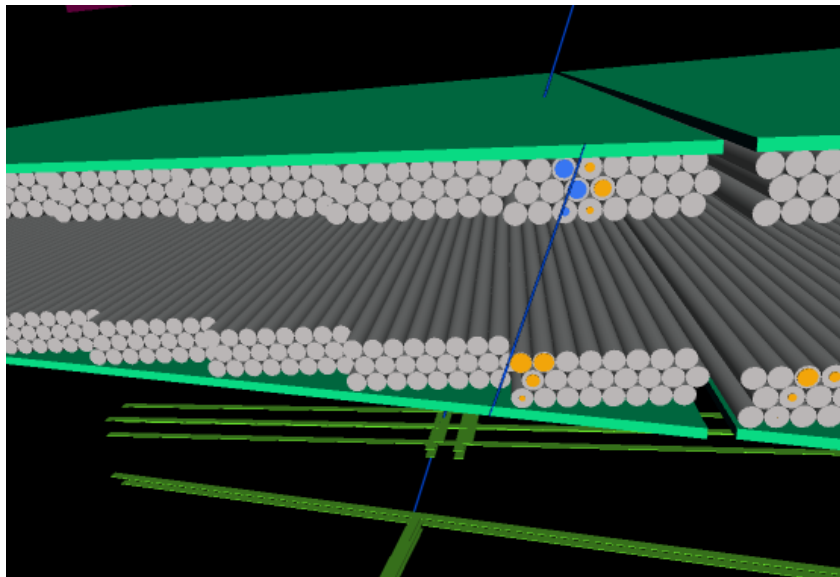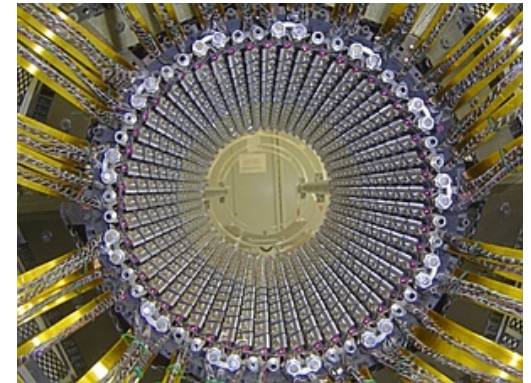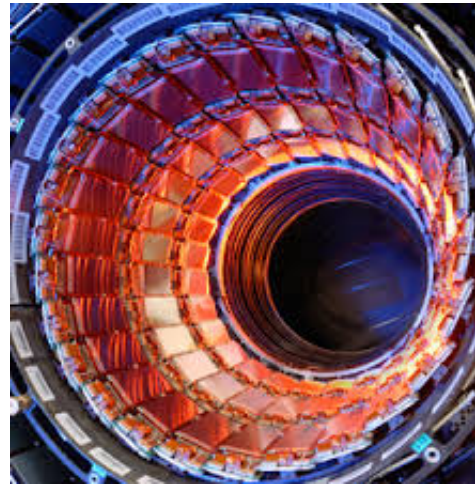*ionization chamber* ~ *Si strip detector*
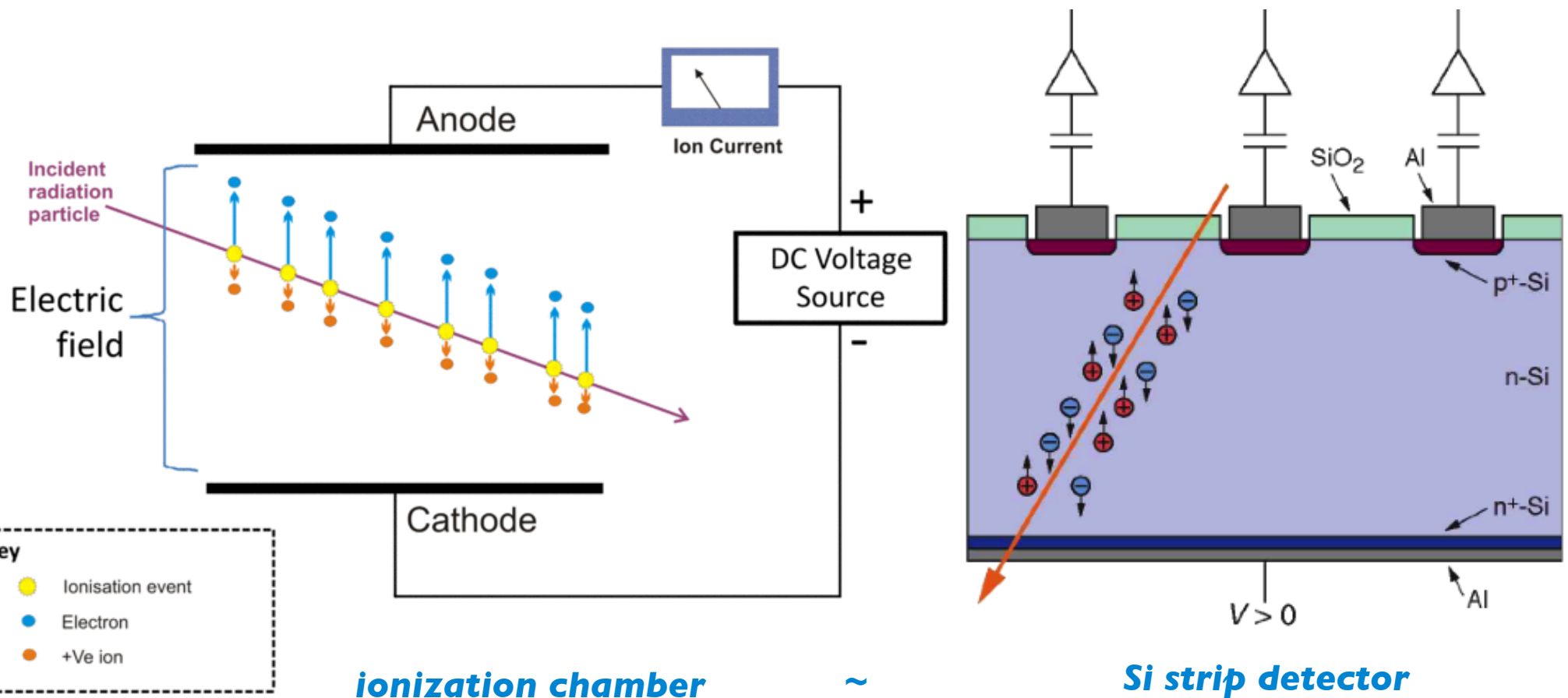
Tracking: how?

- **Solid state detectors**
  - Ge, Si, Diamond,...
  - Pixels for vertexing, strips for tracking

- **Gaseous detectors**
  - drift tubes, resistive plate chambers, gas electron multipliers, ...
  - usually for outer tracking

Insulator strips • Anode wire — Electrode strips • Cathode strip — 13 mm — 42 mm

Gaseous versus solid state

	Gas		Solid state	
		$C_2H_2F_4$		Si
Density (g/cm³)	Low		High	
Atomic number (Z)	Low	(~95% for CMS RPC)	Moderate	
Ionization energy (ε_i)	Moderate	30eV	Low	3.6eV
Signal speed	Moderate	10ns-10µs	Fast	<20ns

- In solid state detectors ionization energy converts in e-h pairs

  → 10 times smaller with respect to gaseous-based ionization

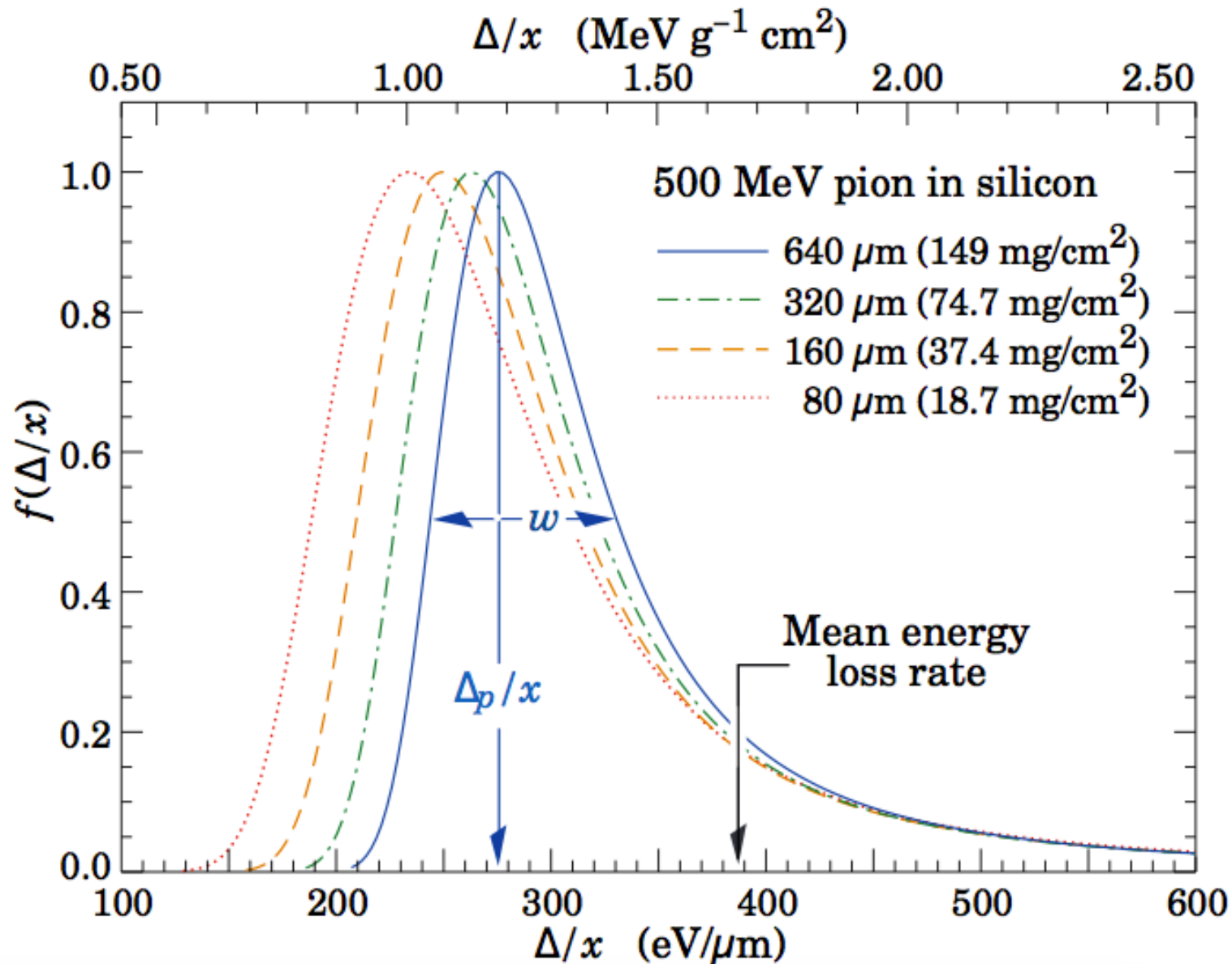 → Charge is increased → improved E resolution

$$n = \frac{E_{loss}}{E_{eh}} \to \frac{\sigma_E}{E} \propto \frac{1}{\sqrt{n}} \propto \sqrt{E_{eh}}$$

- Higher density materials used in solid state detectors

  → Charge collected is proportional to the thickness

  → Most probable value:

$$\frac{\Delta_p}{x} \sim 0.74 \cdot 3.876 \mathrm{MeV}/\mathrm{cm} \to N_{eh} \sim \frac{23 \cdot 10^3}{300 \mu m}$$
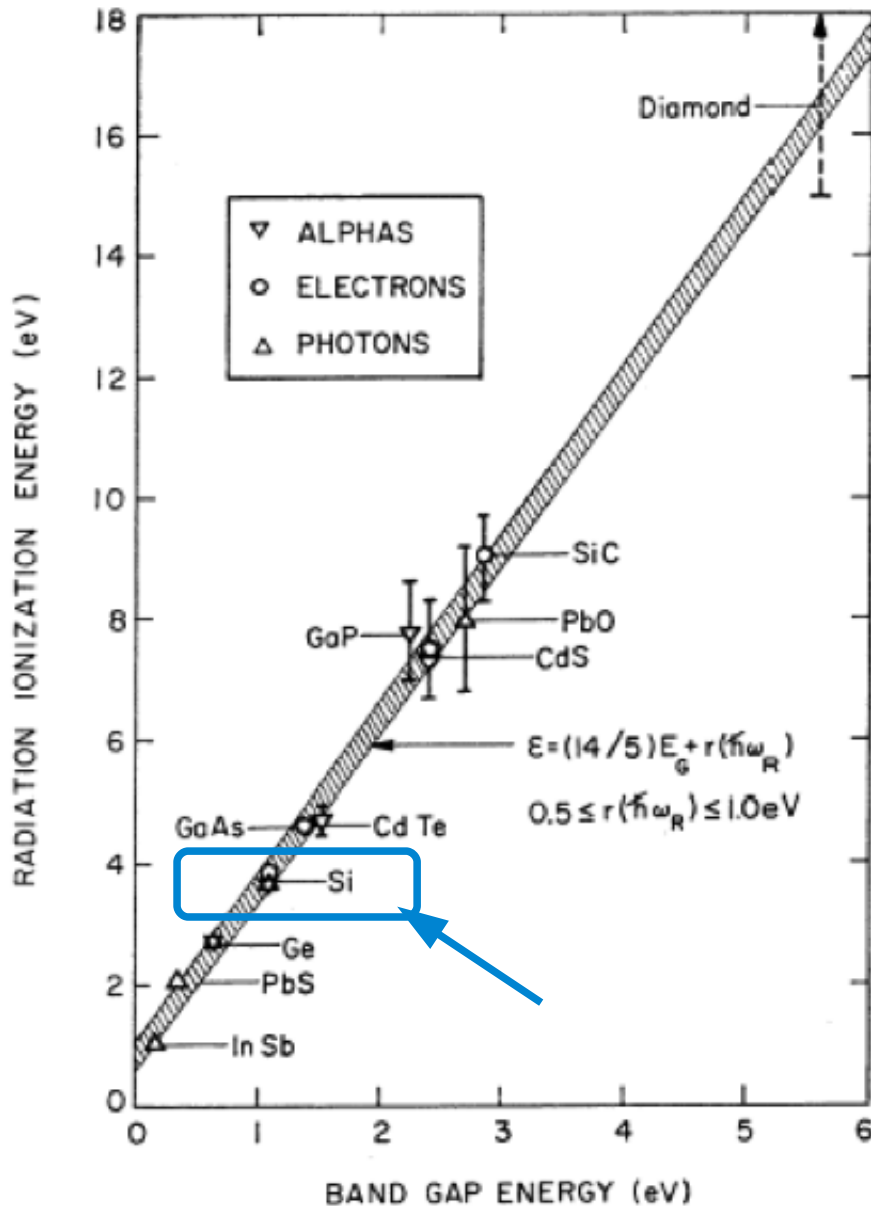
  → Excellent spatial resolution: short range for secondary electrons

- Most probable value of the Landau distribution for energy loss defines the minimum ionizing particle

Si properties

Excellent material for HEP detectors

- **Low ionization energy**
  - Band gap is 1.12 eV
  - Takes 3.6 eV to ionize atom → remaining yields phonon excitations
  - Long free mean path → good charge collection efficiency
  - High mobility → fast charge collection
  - Low Z → reduced multiple scattering

- **Good electrical properties (SiO_2)**

- **Good mechanical properties**
  - Easily patterned to small dimensions
  - Can be operated at room temperature
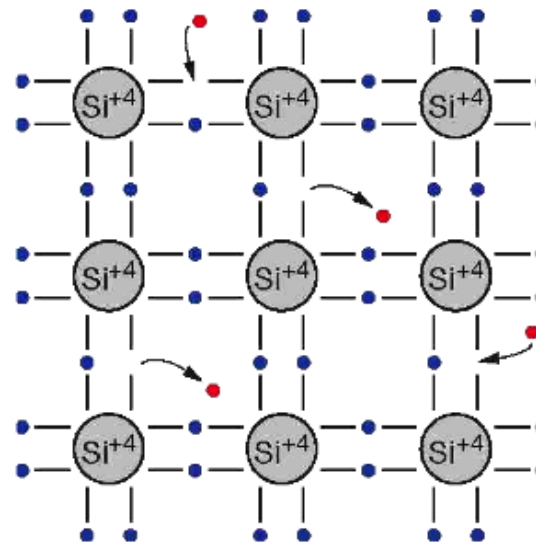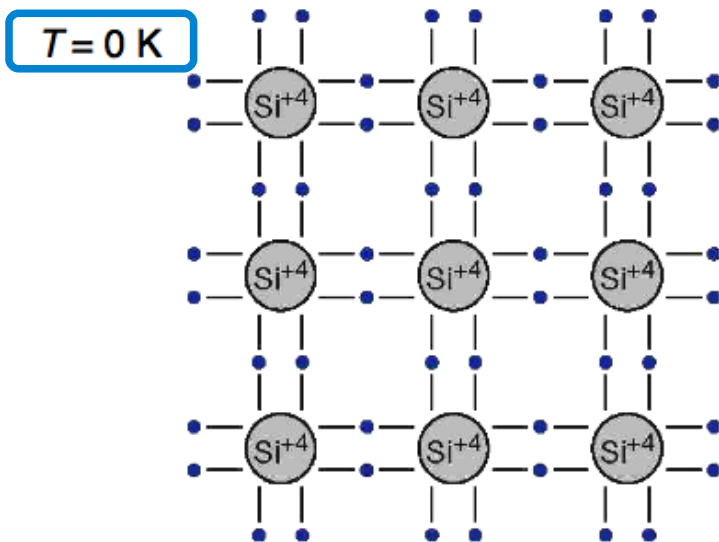 - Crystalline → resilient against radiation

- **Widely used in industry**
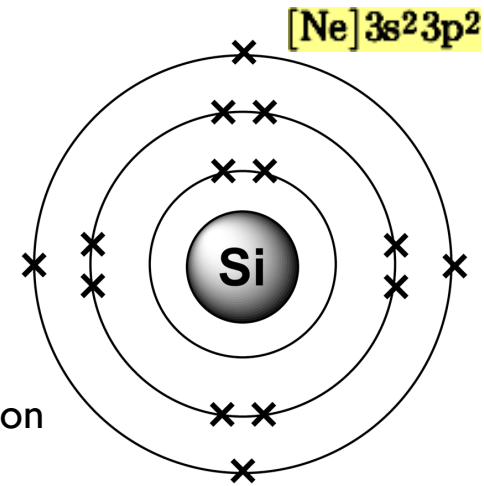
Bond model of semi-conductors

- **Covalent bonds** formed after sharing electrons in the outermost shell

- **Thermal vibrations**

  → break bonds and yield electron conduction (free e^-)

 → remaining open bonds attract free e- → holes change position → hole conduction

$[Ne]3s^23p^2$

Si

$T = 0\,K$

$T > 0\,K$

- $\cdots$ Valence electron
- $\cdots$ Conduction electron

Energy bands structure compared

- **In solids, the quantized energy levels merge**

  - Metals: conduction and valence band overlap

  - Insulators and semi-conductors: conduction and valence band separated by energy (band) gap

  - If μ (band gap) sufficiently low : electrons fill conduction band according to Fermi-Dirac statistics

$$f(E) = \frac{1}{e^{(E-\mu)/\kappa_B T} + 1}$$
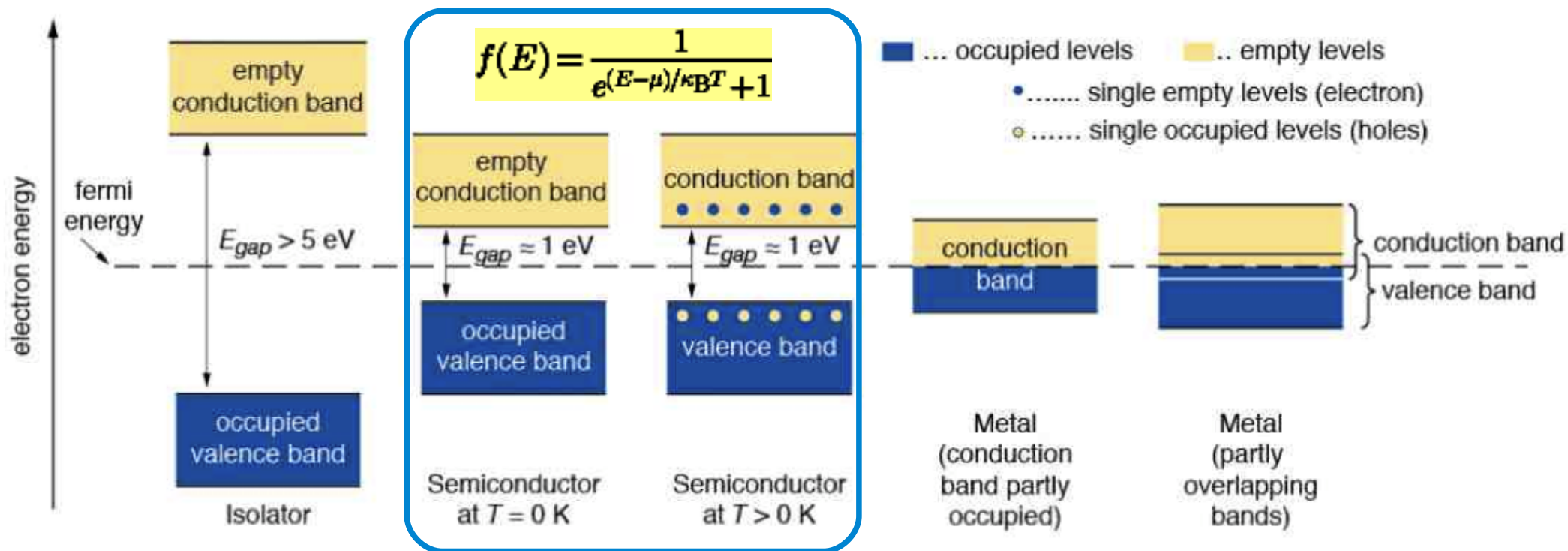
Intrinsic carrier concentration

- The probability that an energy state is occupied by an e⁻ is given by **Fermi statistics** ▼

- **At room temperature**

    → excited electrons occupy conduction band
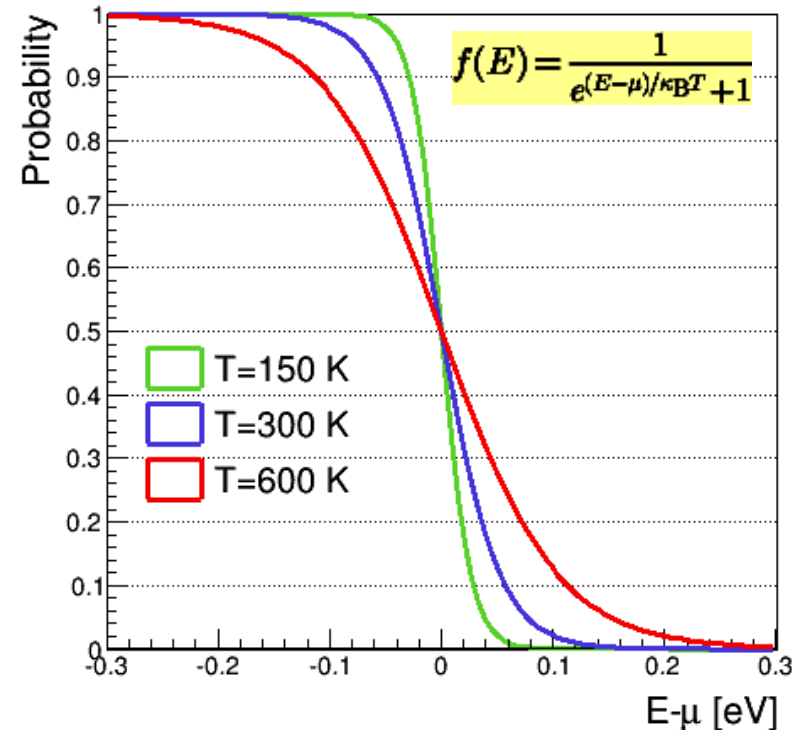
    → electrons tend to recombine with holes

- **Excitation** and **recombination in thermal equilibrium**

    → Intrinsic carrier concentration given by

    $$n_e = n_h = n_i = A \cdot T^{3/2} \cdot e^{-E_g/k_B T}$$

    with A=3.1x10^{16} K$^{-3/2}$cm^{-3} and $E_g/2k_B$=7x10^{3}K

    → n_i~1.45x10^{10} cm^{-3} → 1/10^{12} Si atoms is ionized

$$f(E) = \frac{1}{e^{(E-\mu)/\kappa_B T} + 1}$$
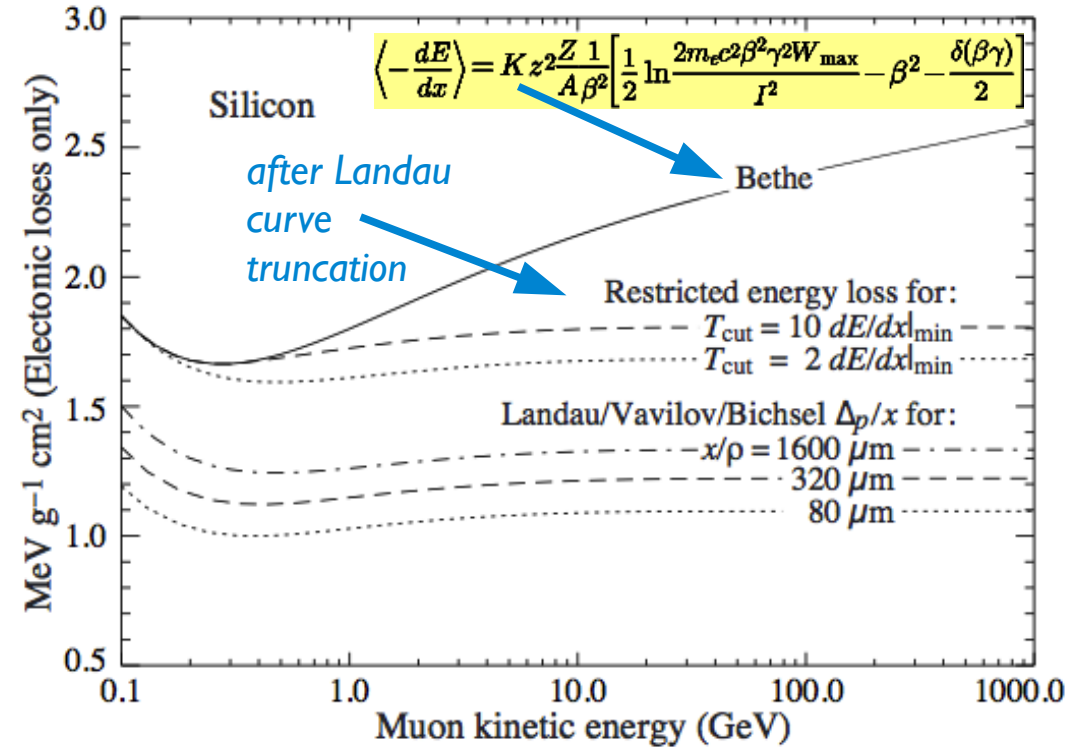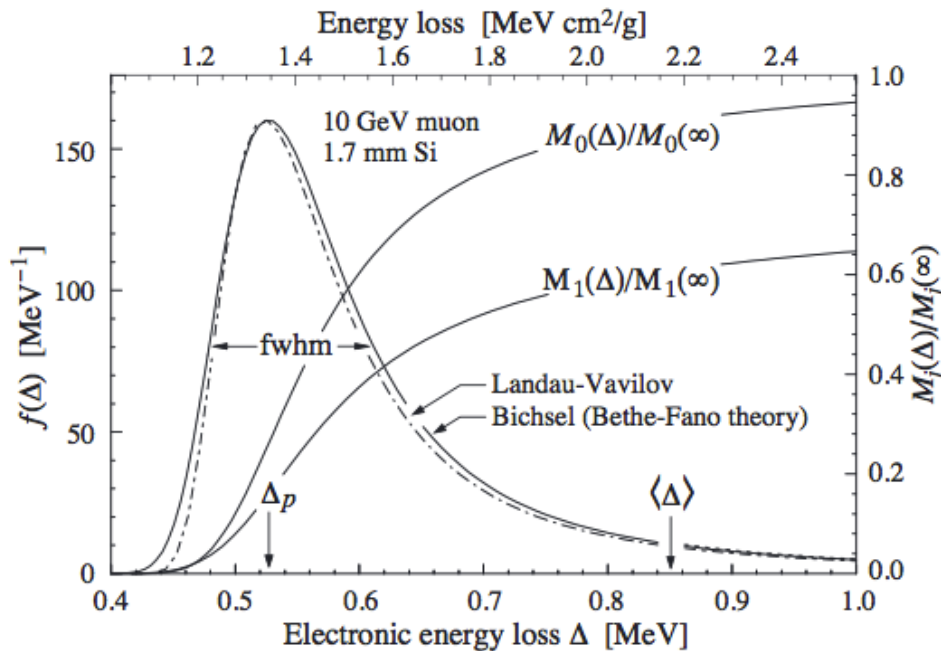
T=150 K
T=300 K
T=600 K

Probability

E-μ [eV]

- **In semi-conductors signal-to-noise (S/N) is compromised by the band gap**

    → Keep low ionization energy → small band gap

    → Keep low intrinsic charge carriers → large band gap

    → Optimal E_g~6 eV → diamond ▶

S/N in intrinsic Si detector

Example: Si detector with thickness d=300μm

- ➡ Minimum ionizing particle (MIP) creates:

$$\frac{1}{E_{eh}}\frac{dE}{dx} \cdot d = \frac{3.87 \cdot 10^6 \text{eV}/\text{cm}}{3.63 \text{eV}} \cdot 0.03 \text{cm} = 3.2 \cdot 10^4 \text{eh pairs}$$

- ➡ Intrinsic charge carriers (per cm²):

$$n_i \cdot d = 1.45 \cdot 10^{10} \text{cm}^{-3} \cdot 0.03 \text{cm} = 4.35 \cdot 10^8 \text{eh pairs}$$

- ● **Number of thermally-created e-h pairs exceeds mip signal by factor 10!**

Si doping: n-dope bond model

- Doping with a group 5 atom (e.g. P, As, Sb)

  - atom is an electron **donor/donator**

  - Weakly bound 5th valence electron

  - Positive ion is left after conduction electron is released

weakly bound elektron
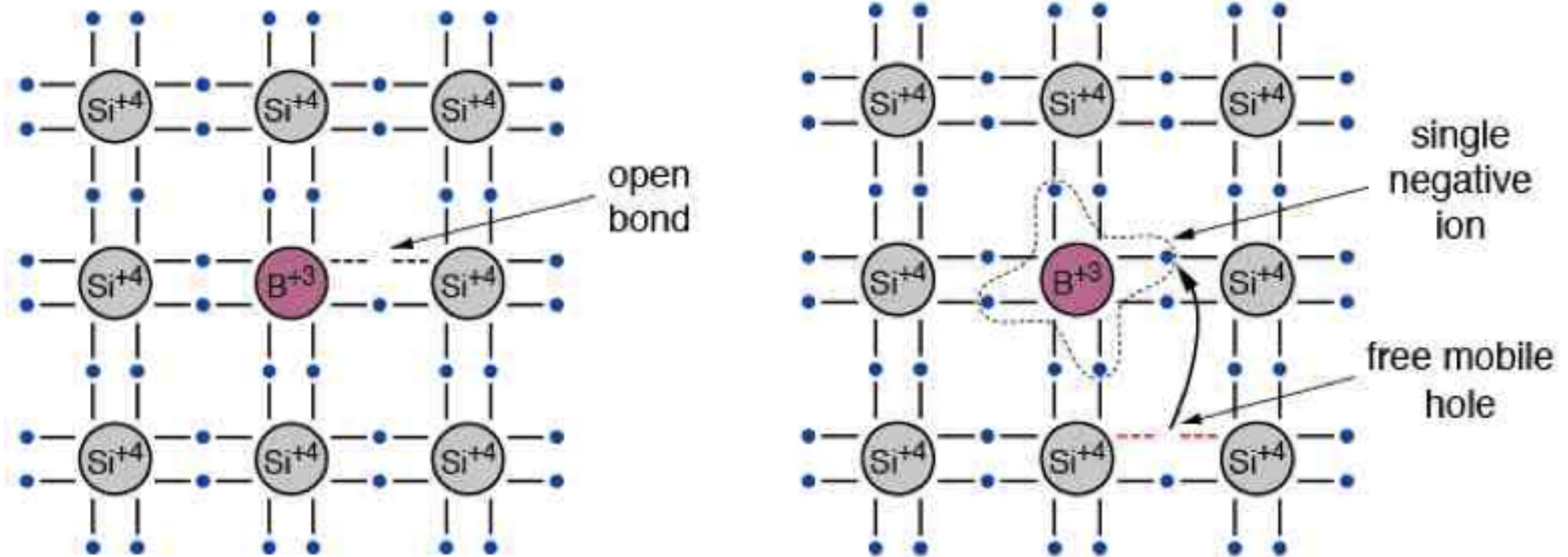
single positive ion

conduction electron
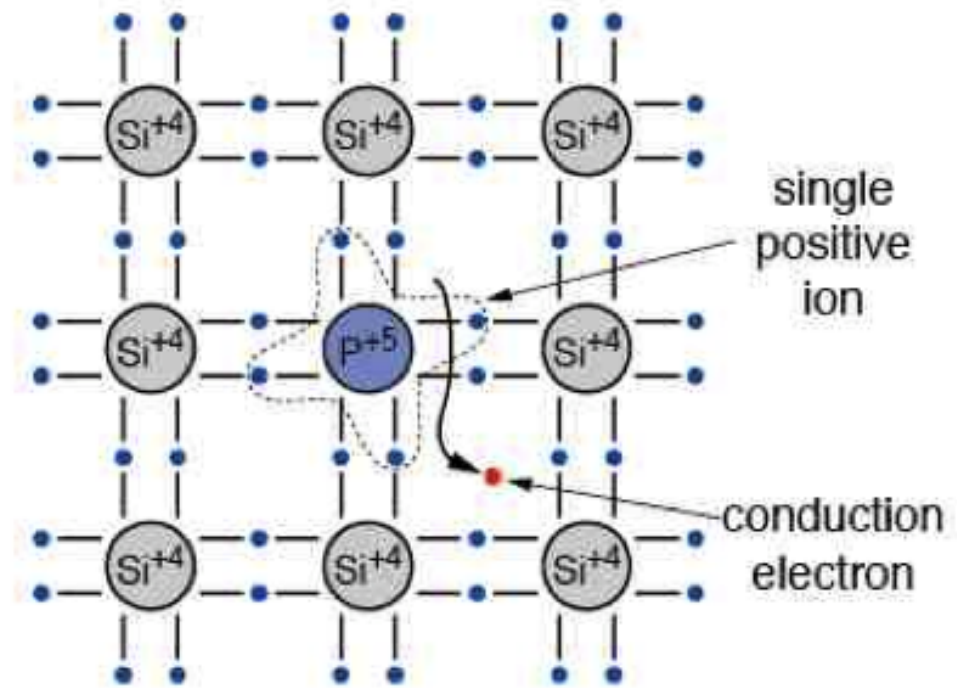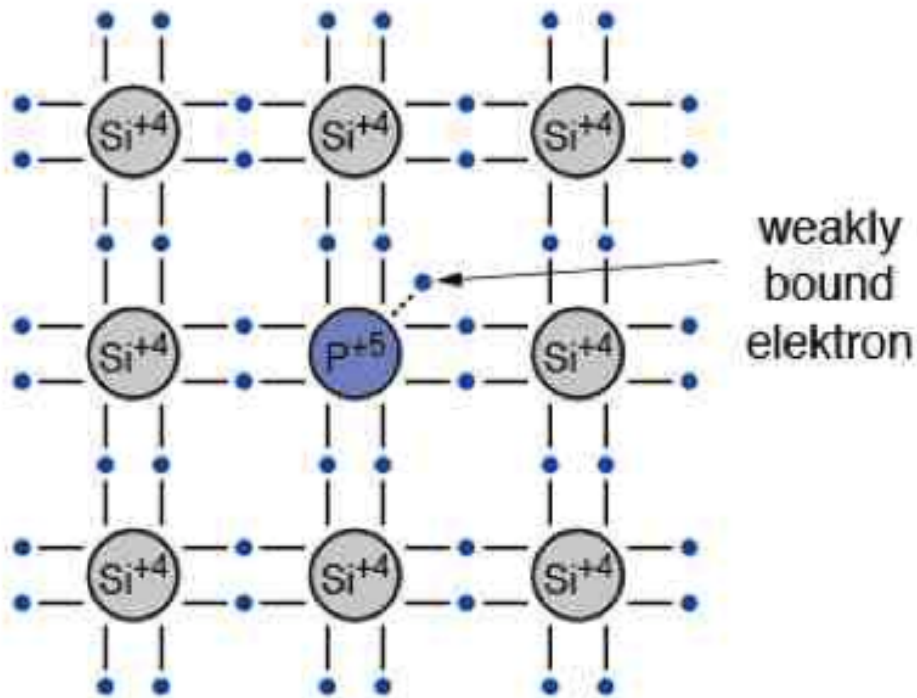
Si doping: n-dope bond model II

- Energy level of donor is below edge of conduction band

  - Most electrons enter conduction band at room temperature

 - Fermi level moves up with respect to pure Si
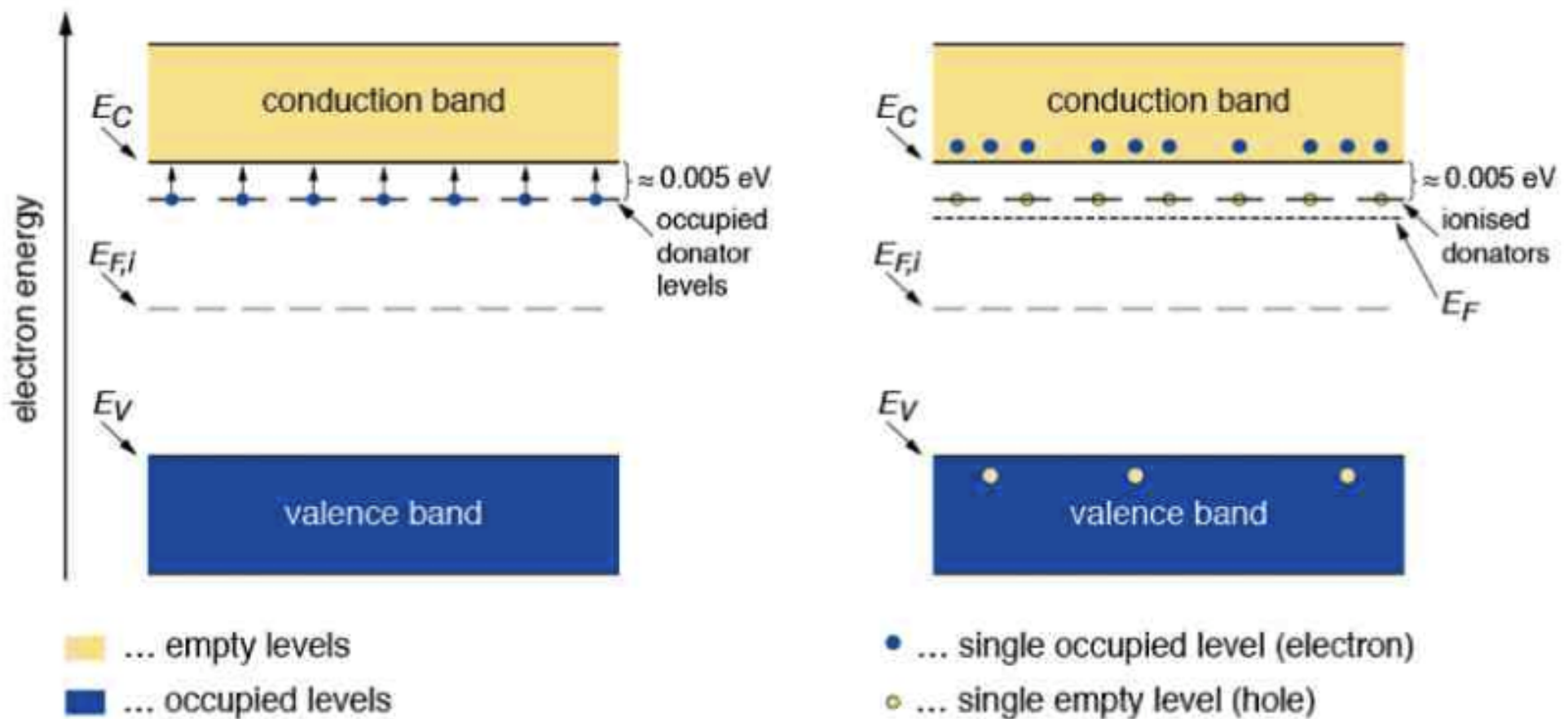
Si doping: p-dope bond model

- Doping with a group 3 atom (e.g. B, Al, Ga, In)

  - atom is an electron **acceptor**

  - open bond attracts electrons from neighboring atoms

 - acceptor atom in the lattice becomes negatively charged

- Energy level of acceptor is above edge of conduction band

  → Most levels are occupied by electrons $\rightarrow$ holes in the valence band

 → Fermi level moves down with respect to pure Si
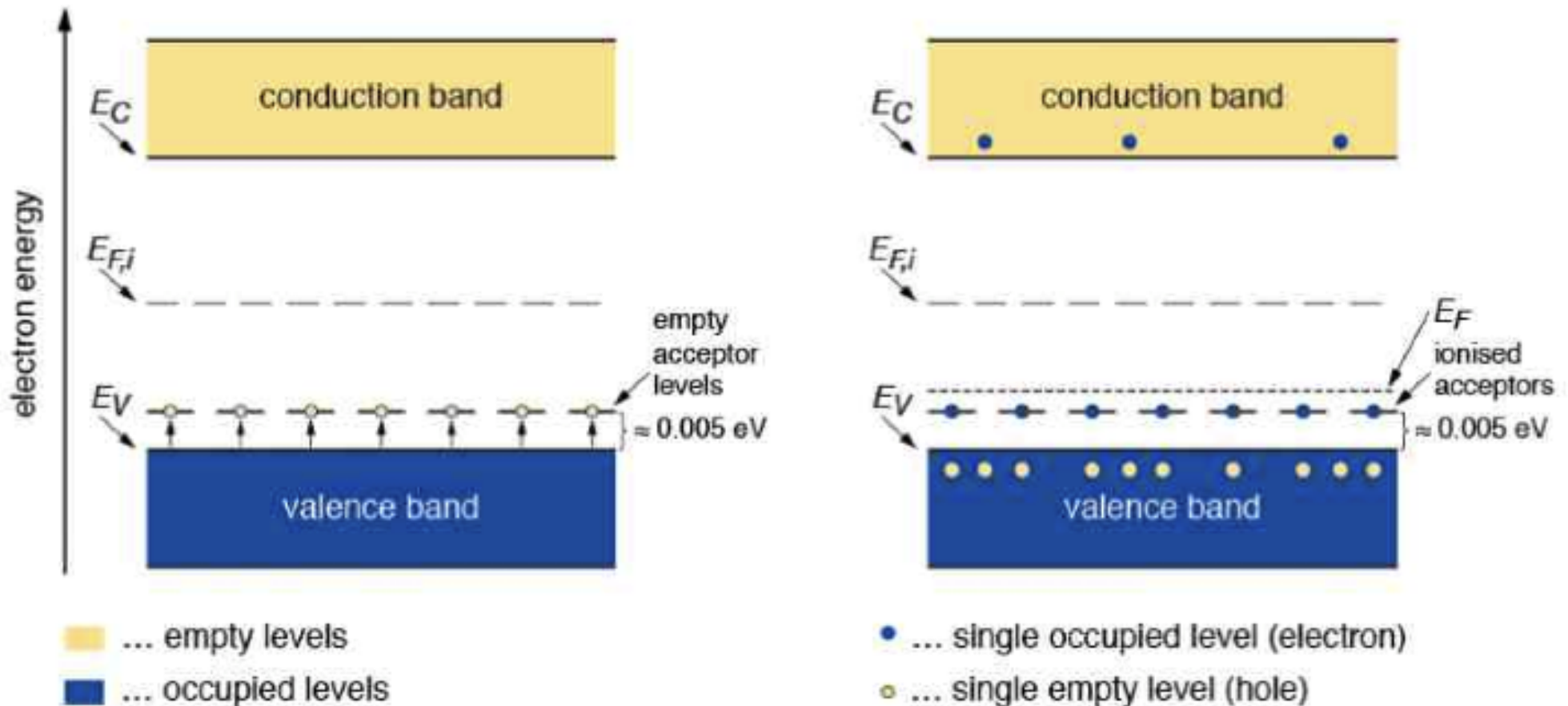
p-n junctions

- Difference in Fermi levels at the interface of n-type or p-type

    - diffusion of excess of charge carriers until thermal equilibrium (or equal Fermi level)

    - remaining ions create a **depletion zone**: electric field prevents further the diffusion
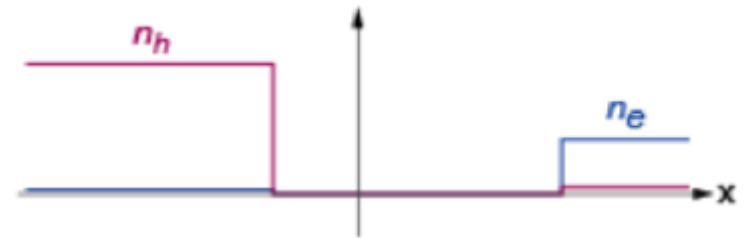

$\ominus$ ... acceptor

$\oplus$ ... donator

$+$ ... empty hole
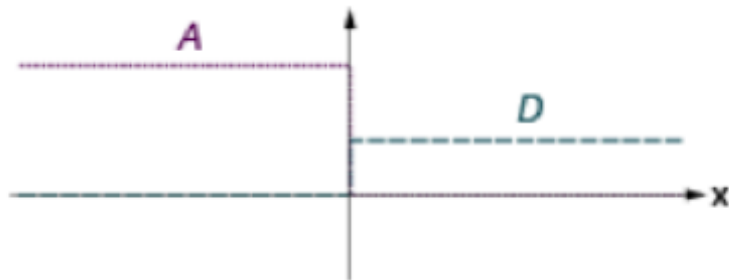
$-$ ... conduction electron
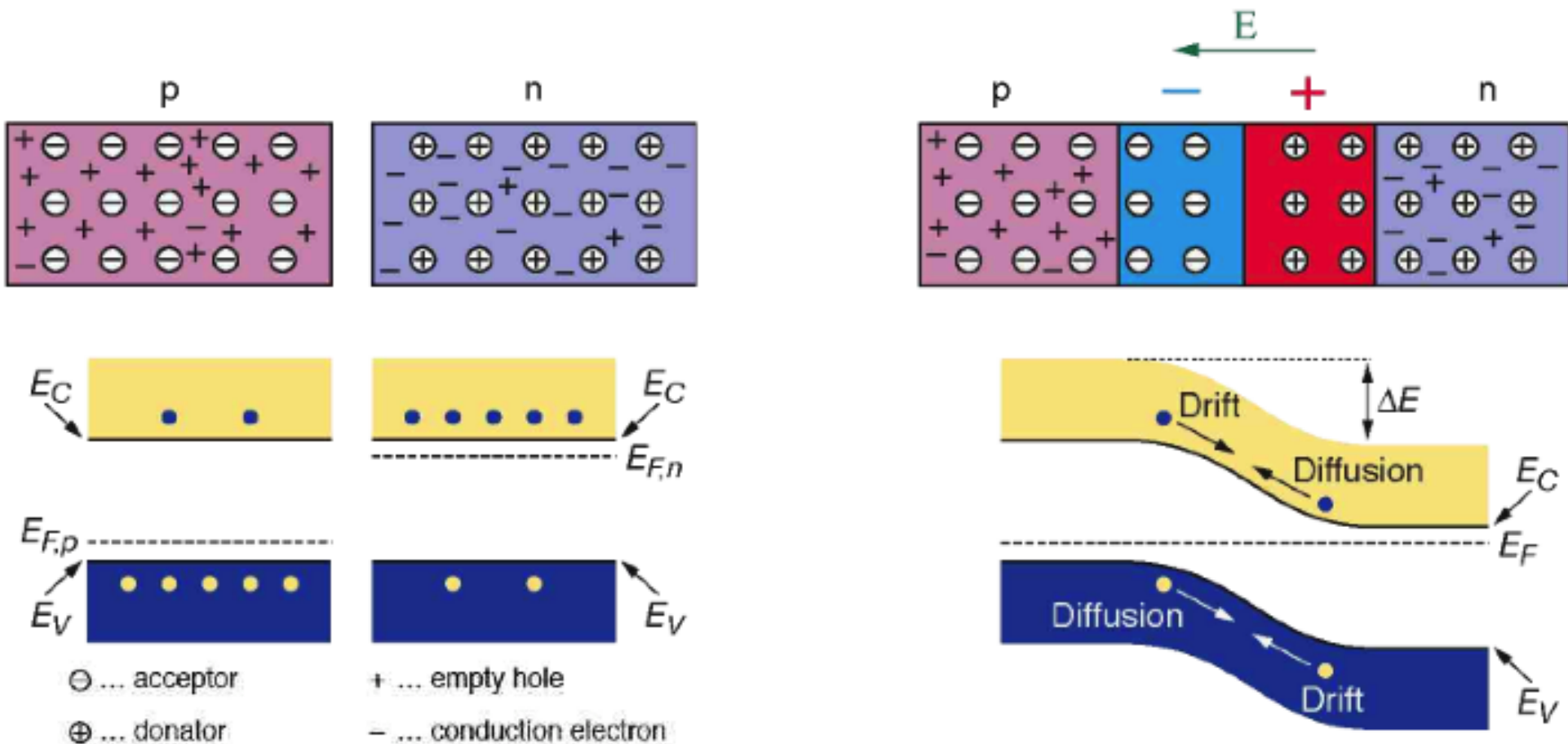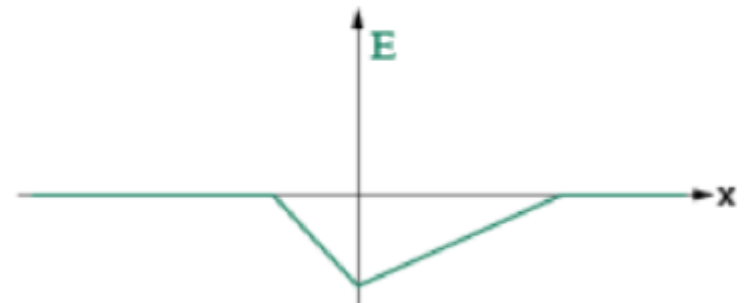
p-n junctions

pn junction scheme
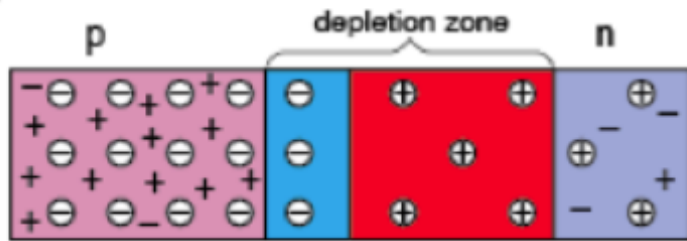
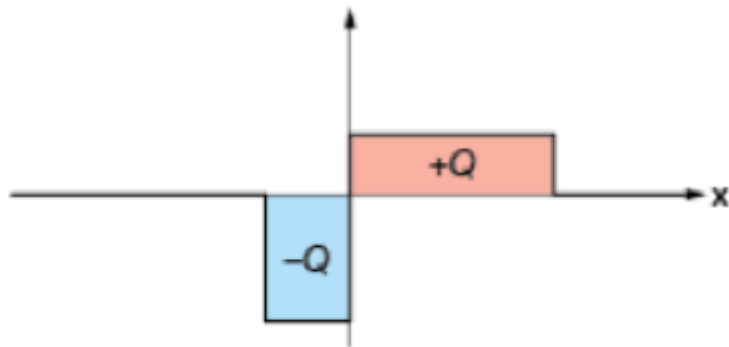concentration of free charge carriers

acceptor and donator concentration
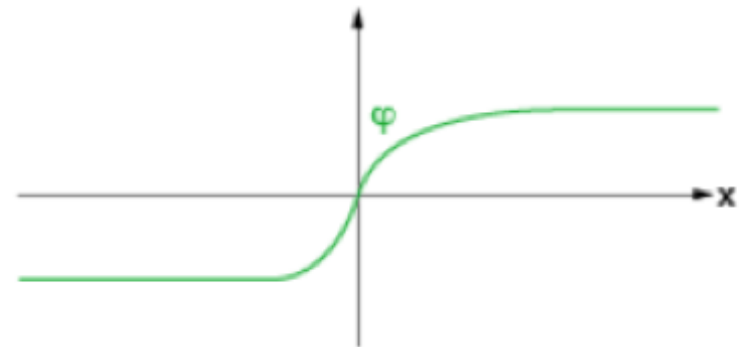

electric field

space charge density

electric potential

⊖ ... acceptor   + ... empty hole

⊕ ... donator   − ... conduction electron

Biasing p-n junctions

p-n junction with forward bias
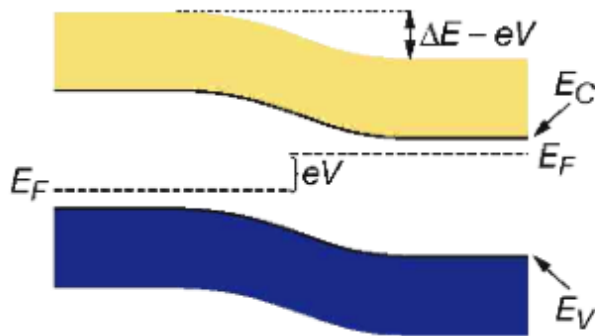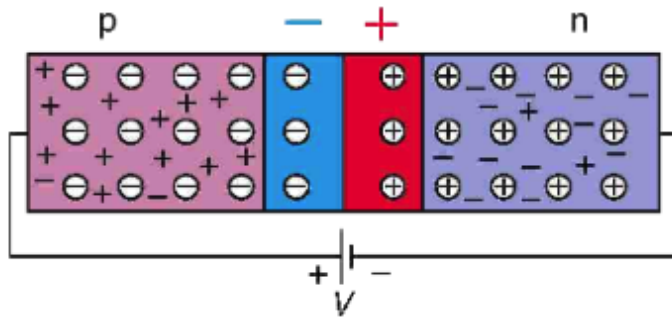
Forward-biased junction

- Anode to p, cathode to n

- Depletion zone becomes narrower

- Smaller potential barrier facilitates diffusion

- Current across the junction tends to increase

p-n junction with reverse bias

Reverse-biased junction

- Anode to n, cathode to p

- e,h pulled out of the depletion zone

- Potential barrier is suppressed

- Only **leakage current** across junction

Depletion zone width and capacitance

- Characterize depletion zone from Poisson equation with charge conservation: $\nabla^2 \phi = -\dfrac{\rho_f}{\varepsilon}$

- Typically: $N_a = 10^{15}$ cm^{-3} (p+ region) $\gg N_d = 10^{12}$ cm^{-3} (n bulk)
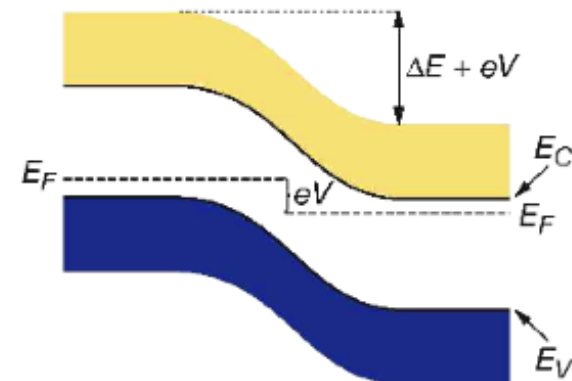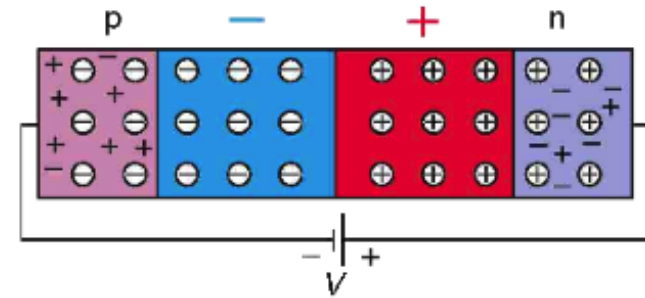
- **Width of depletion zone** (n bulk): $W \approx \sqrt{\dfrac{2\varepsilon V_{bias}}{q} \cdot \dfrac{1}{N_d}}$

Reverse bias voltage (V)	W_p (µm)	W_n (µm)
0	0.02	23
100	0.4	363
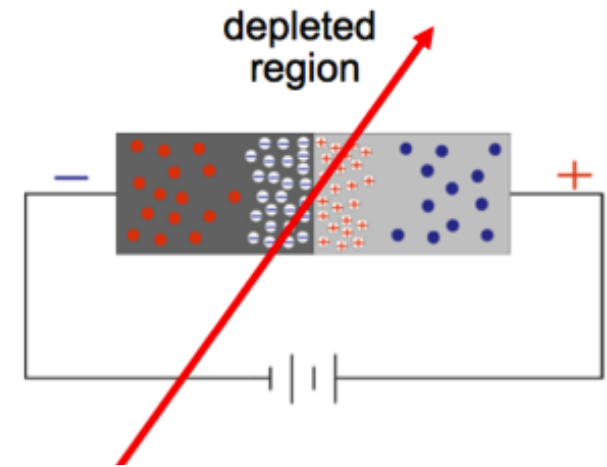
- **Device is similar to a parallel-plate capacitor**

$$C = \frac{q}{V} = \frac{\varepsilon A}{d} = A\sqrt{\frac{\varepsilon q N_d}{2V_{bias}}}$$

- ➥ Depletion voltage saturates the capacitance

- ➥ Typical curve obtained for CMS strip detector

depleted region
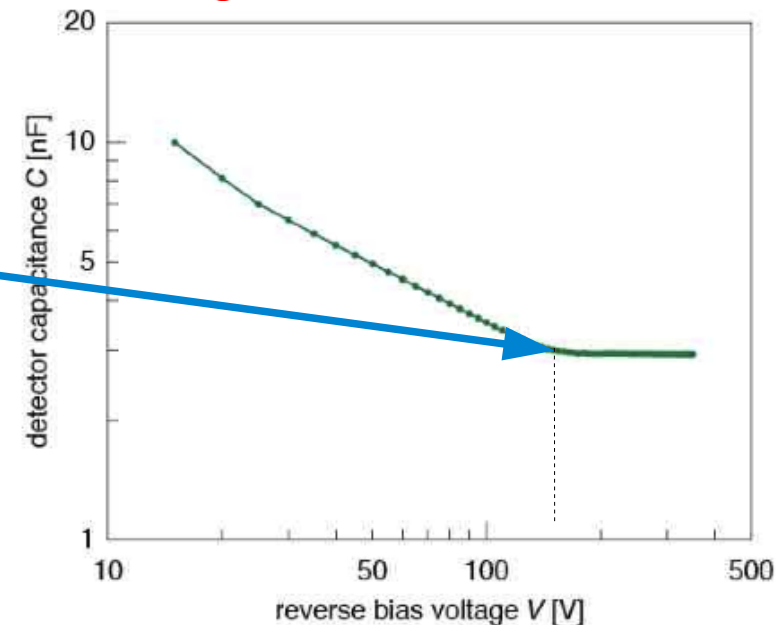
Leakage current

- Thermal excitation generates eh pairs

- Reverse bias applied separates pairs

- eh pairs do not recombine and drift

  → leads to **leakage current**

  Leakage current at room temperature for the CMS strip detector ▼
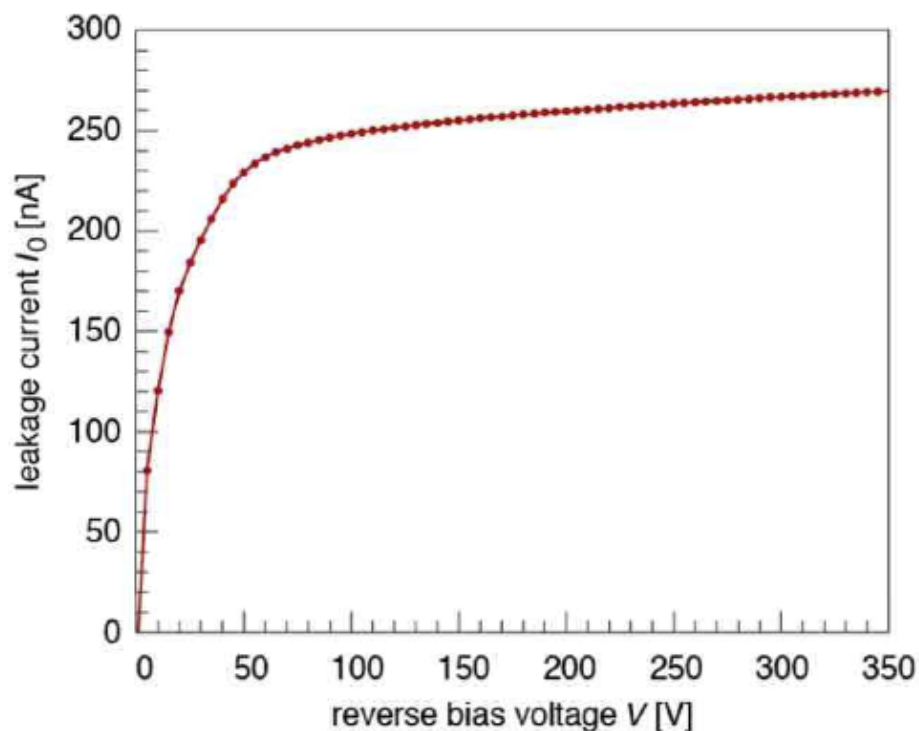
- Depends on purity and defects in material

- Depends on the temperature:

$$j_{\text{gen}} \propto T^{3/2} e^{\frac{1}{\kappa_B T}}$$

  → prefer low, stable temperatures

  → CMS tracker operated at <-10°C

Leakage Current Vs Temperature

Factor 2 every 8 °C
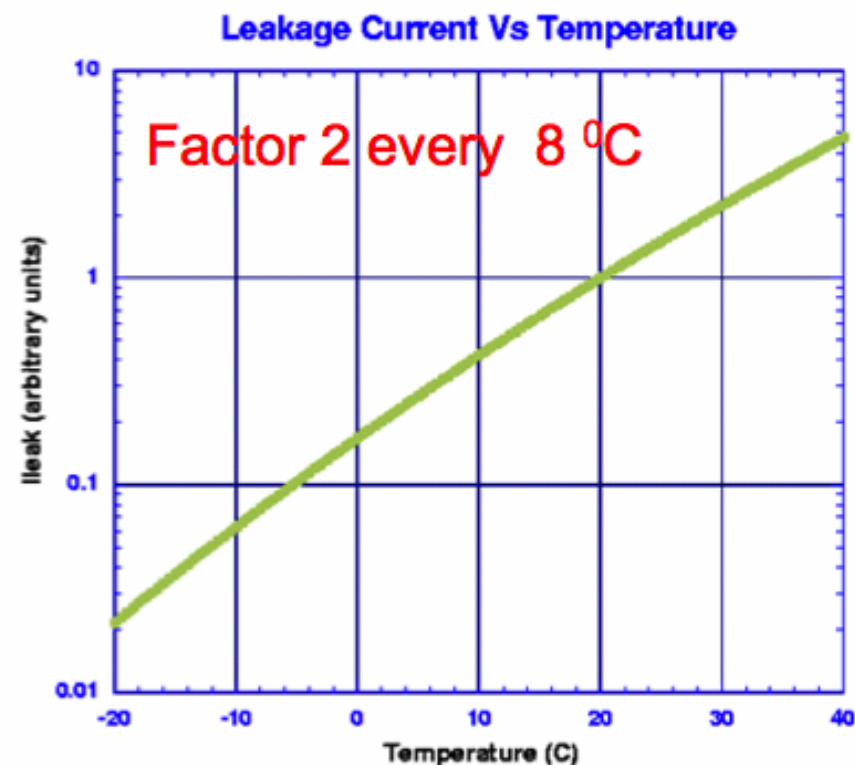
Charge collection

- eh pairs move under the E field

- **Collection time**: time required for a carrier transverse sensitive volume ▶

- Can be reduced over-biasing the sensor

- Simulation of E-field from charge collection after passage of ionizing particle at 45° ▼
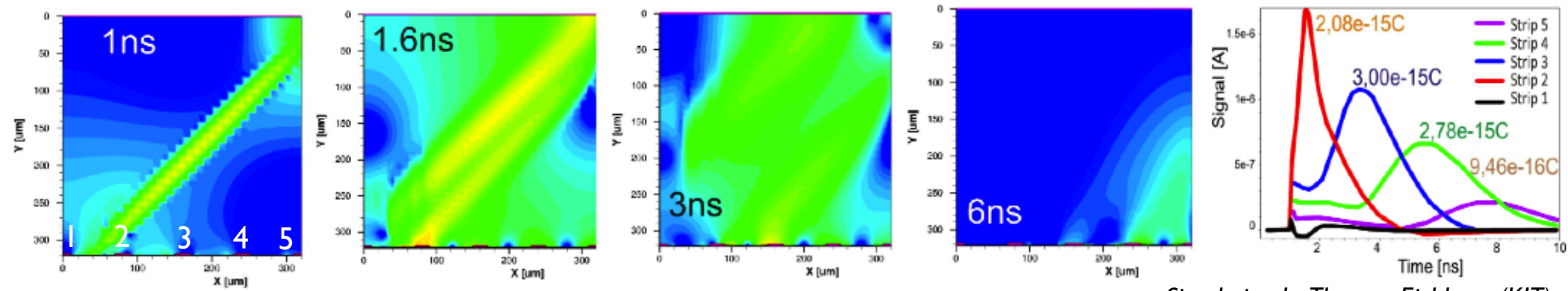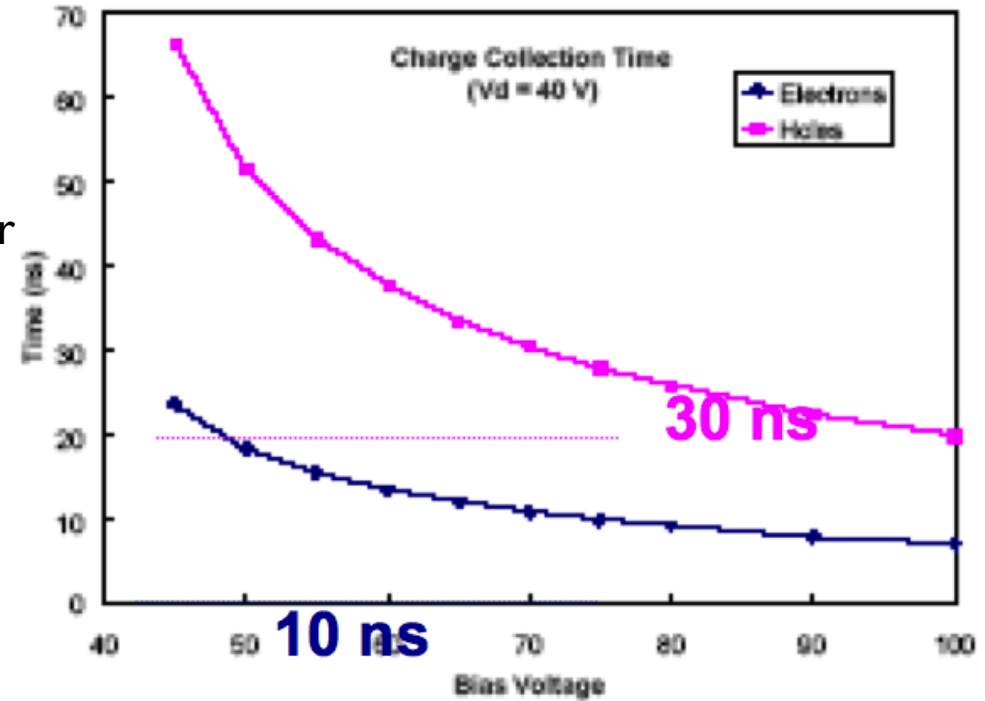
Simulation by Thomas Eichhorn (KIT)

→ 400 V bias, at 20°C, all charge collected after 10ns

Position resolution (DC coupled)

- Segmentation of the implants

  - reconstruct position of the particle

- Standard configuration uses

  - p implants in strips

  - n-doped substract ~300µm (2-10kΩcm)

  - depletion voltage <200 V

  - Backside P implant establishes ohmic contact and prevents early breakdown

  - Al metallization

- Field closest to the collecting electrodes where most of the signal is induced
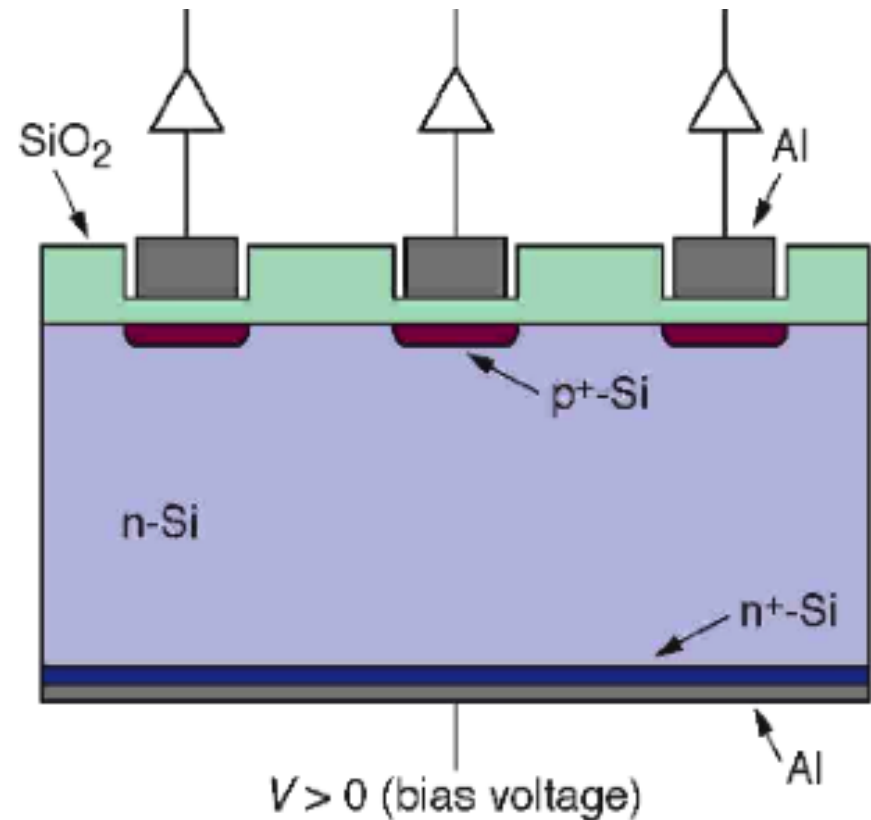
Position resolution (AC coupled)

- **Amplifier generates leakage current**

  - Blocked with AC coupling

- Deposit SiO_2 between p^+ and Al strip

  - Capacitance ~32 pF/cm

  - Shorts through pinholes may be reduced with a second layer of Si_3N_4

- Use large poly silicon resistor (R>1MΩ) connecting the bias voltages to the strips
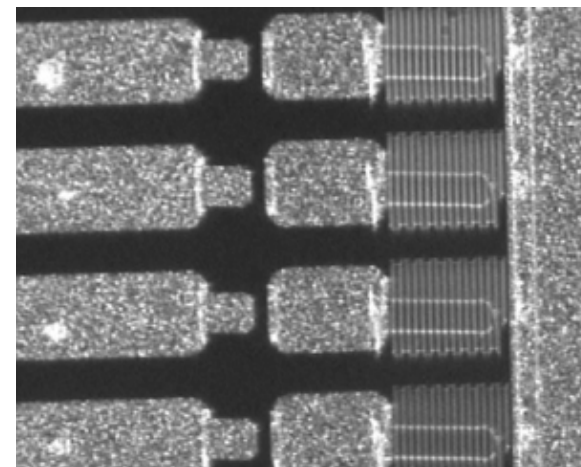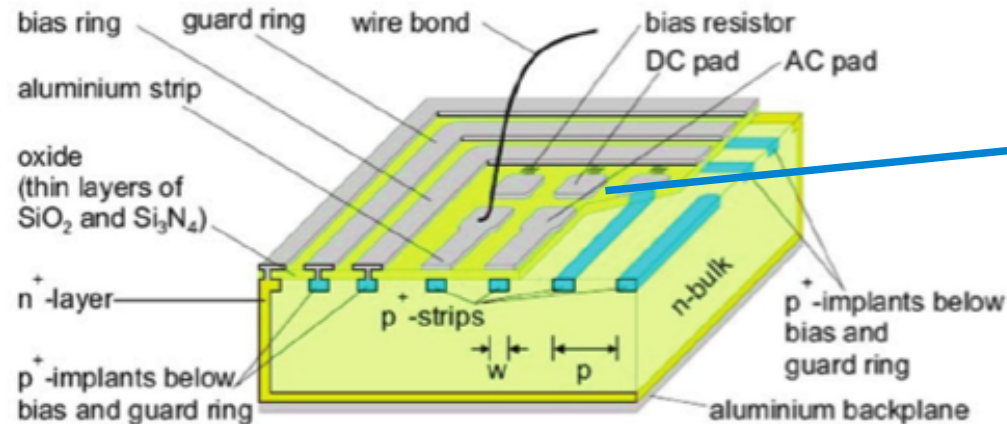
CMS module

silicon sensors
~20 cm strip length

carbon fibre
support

pitch adapter

hybrid
front-end electronics
with read-out chips

kapton flat cables
for power and data

bias ring   guard ring   wire bond   bias resistor
                                         DC pad   AC pad
aluminium strip

oxide
(thin layers of
SiO_2 and Si_3N_4)

n^+-layer

p^+-implants below
bias and guard ring

p-strips

p^+-implants below
bias and
guard ring

aluminium backplane

n-bulk

w   p

DEVICE #A
WIRE #9, 1ST BOND

aluminum
wedge

bond
pad

600x   10.0 kV   10µm   #0019

Pixel sensors

- High track density better resolved with 2D position information

  → back-to-back strips for 2D position information → yields "ghost" hits

- **Hybrid pixel detectors** with sensors and readout chips bump-bonded together in model

  → e.g. one sensor, 16 front-end chips and 1 master controller chip

bump-bond

Hybrid Pixel Module for CMS

Sensor:

- Pixel Size: 150mm x 100mm
  - Resolution $\sigma_{r\text{-}\varphi}$ ~ 15µm
  - Resolution σ_z ~ 20µm

- n+-pixel on n-silicon design
  - Moderated p-spray → HV robustness

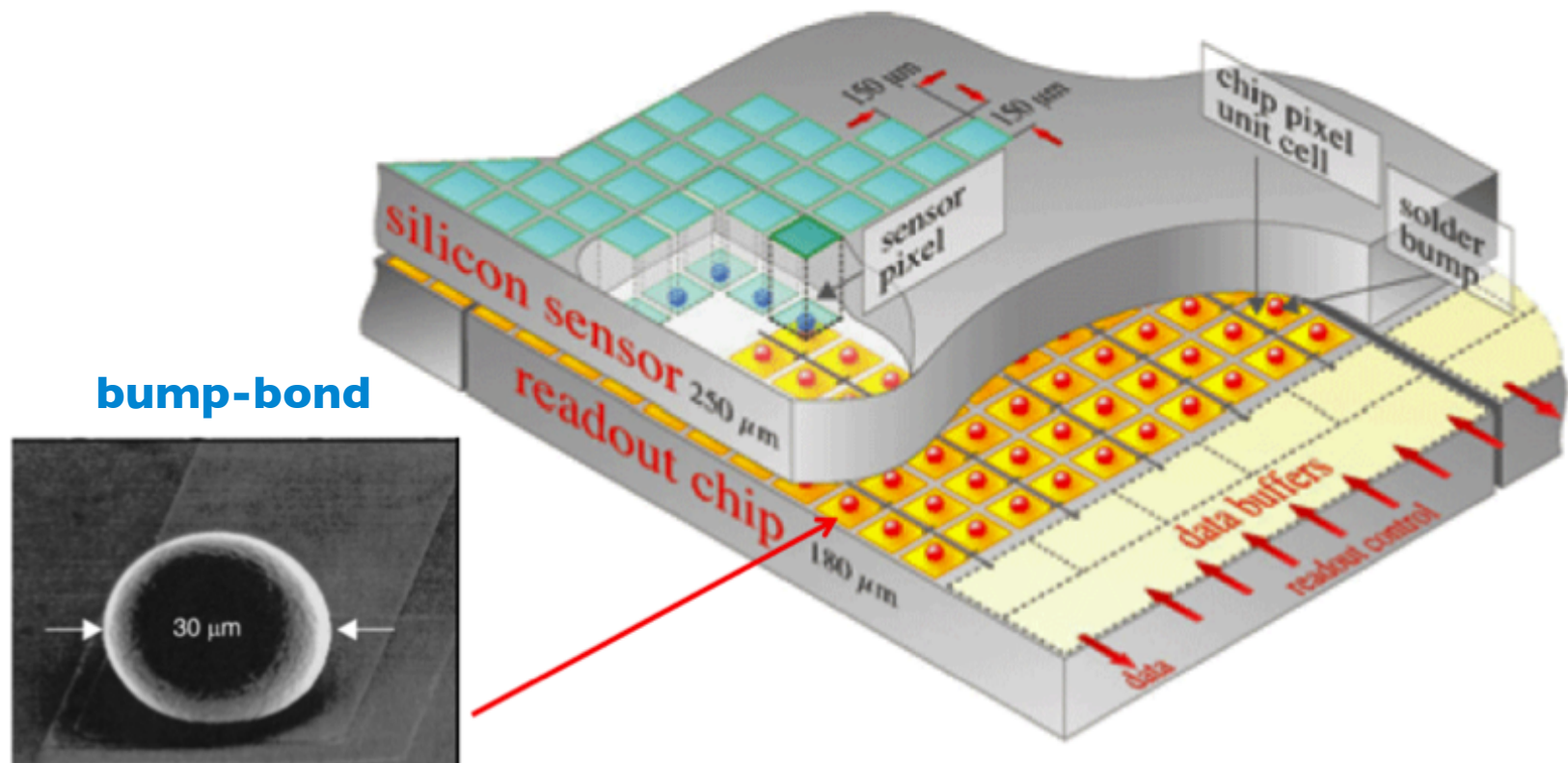## Readout Chip:

- Thinned to 175µm
- 250nm CMOS IBM Process
- 8" Wafer

Kapton signal cable
21 traces, 300µ pitch

Alu-power cable
6 x 250µ ribbon

High Density Print
3 Layers, 48µ thick

Silicon Sensor t=285µ
100µ x 150µ pixels

µ-bump bonding

16 x Readout Chips
(CMOS) 175µ thick

SiN base strips
250m thick, screw holes

screw holes
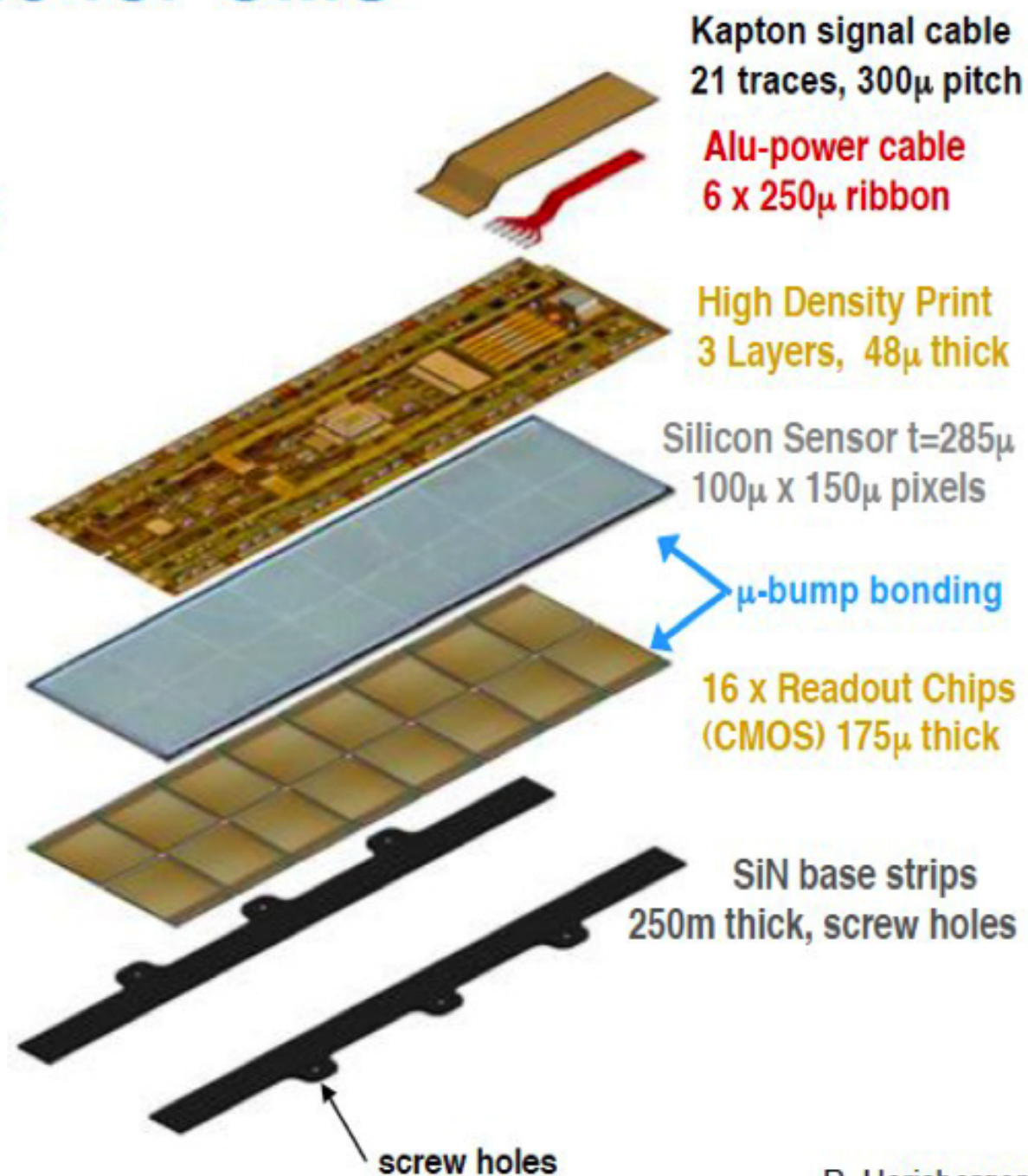
R. Horisberger

Performance: S/N

- **Signal** depends on the thickness of the depletion zone and on dE/dx of the particle

- **Noise** suffers contributions from:

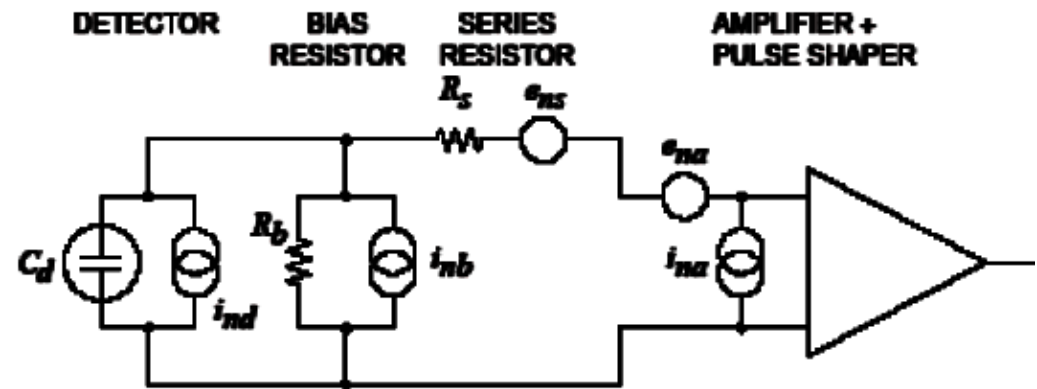$$\text{ENC} = \sqrt{\text{ENC}_C^2 + \text{ENC}_I^2 + \text{ENC}^2 R_\parallel + \text{ENC}^2_{R_{series}}}$$

capacitance   leakage current   parallel resistor   series resistor

DETECTOR   BIAS RESISTOR   SERIES RESISTOR   AMPLIFIER + PULSE SHAPER
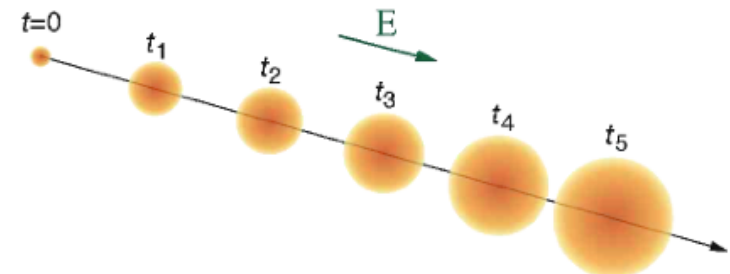
$$\text{ENC}_{peak} = (36.6 \pm 1.9)\, e^-/\text{cm} \cdot L + (405 \pm 27)\, e^-$$
$$\text{ENC}_{dec} = (49.9 \pm 3.2)\, e^-/\text{cm} \cdot L + (590 \pm 47)\, e^-$$

CMS strips

- **Optimizing S/N**

  → $N_{ADC} >$ thr, given high granularity most channels are empty

  → decrease noise terms (see above)

  → minimize diffusion of charge cloud after thermal motion ▶

  (typically ~8μm for 300μm drift)

  → radiation damage severely affects S/N (next slide)

$t=0$ t_1 t_2 E t_3 t_4 t_5

Influence of radiation

- In operation at the LHC **Si performance is affected by radiation** - e.g. from CMS

  - depletion voltage increases with fluence, kept within 500 V design limit

  - mild S/N degradation

  - expected hit finding efficiency after 10 years of LHC operation: 95%

Position resolution
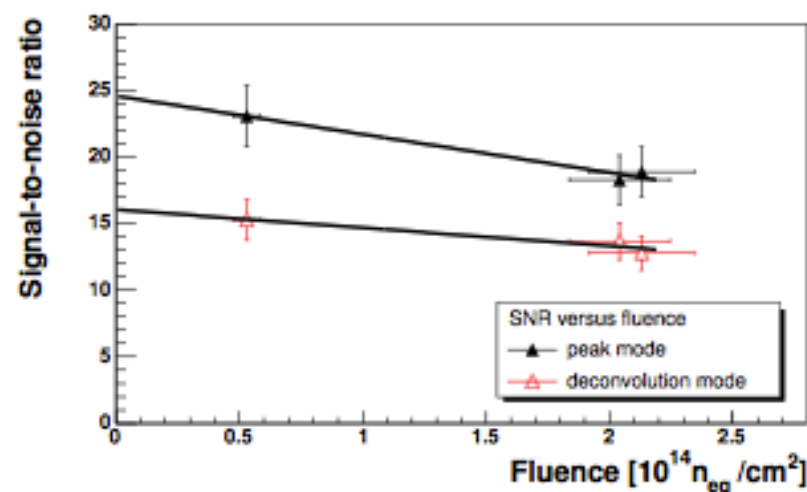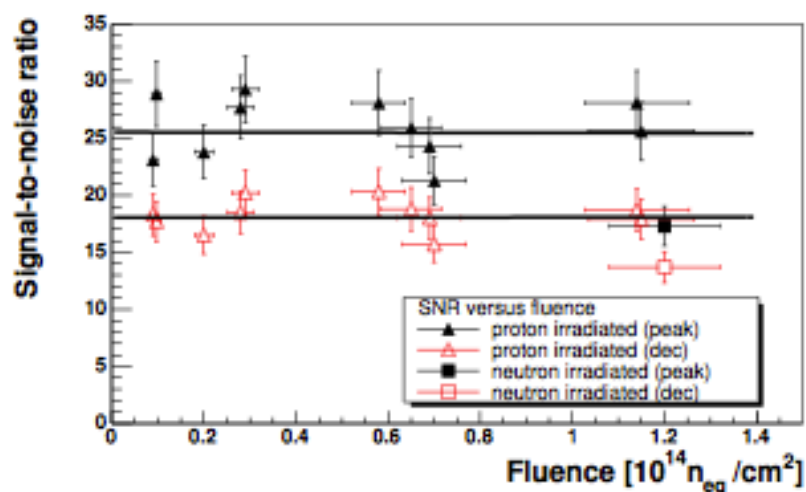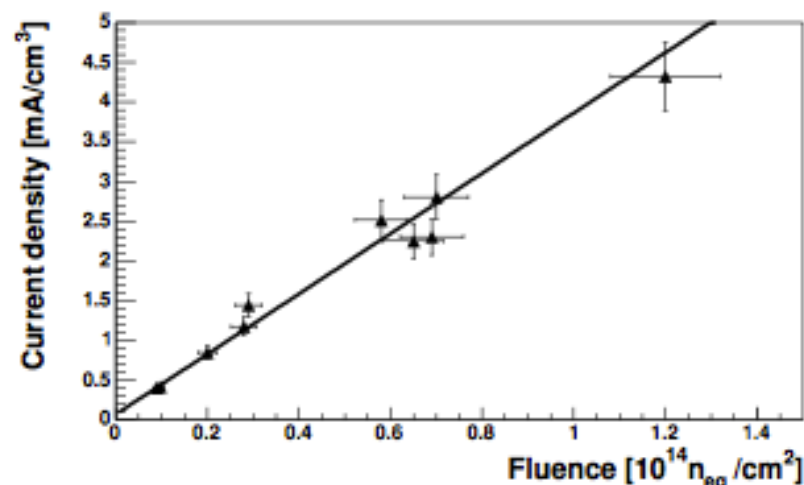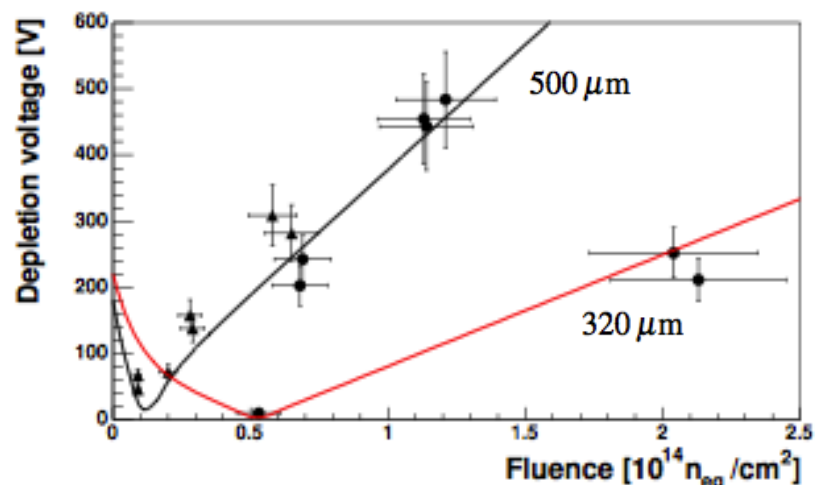
One Strip Clusters

One strip clusters

- Affected by different factors

  - transverse drift of electrons to track

  - strip pitch to diffusion width relationship

  - statistical fluctuations on energy deposition
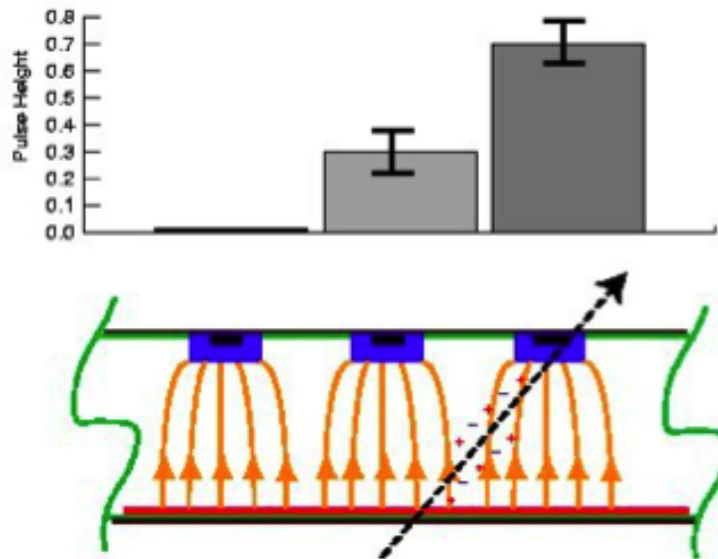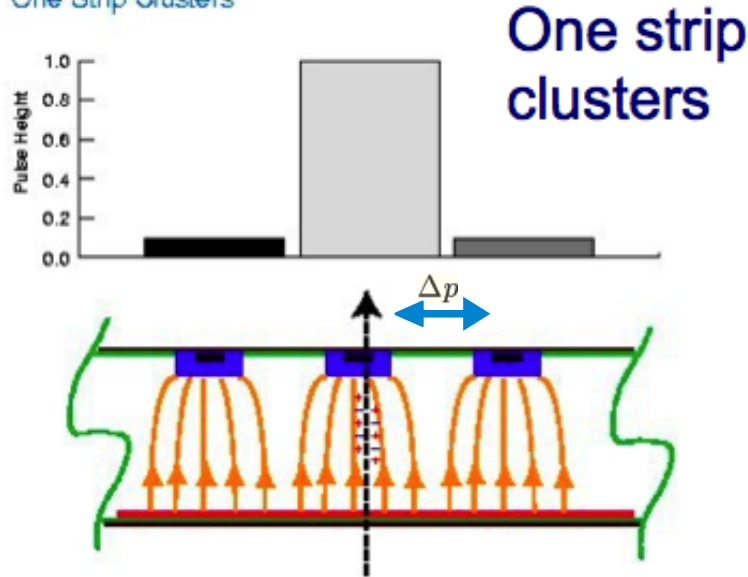
  $$\sigma_x \propto \frac{\Delta p}{S/N}$$

- Single strip resolution tends to dominate

A. Peisert, *Silicon Microstrip Detectors*, DELPHI 92-143 MVX 2, CERN, 1992

Coordinates for tracking

- The LHC experiments use a uniform B field along the beam line (z-axis)

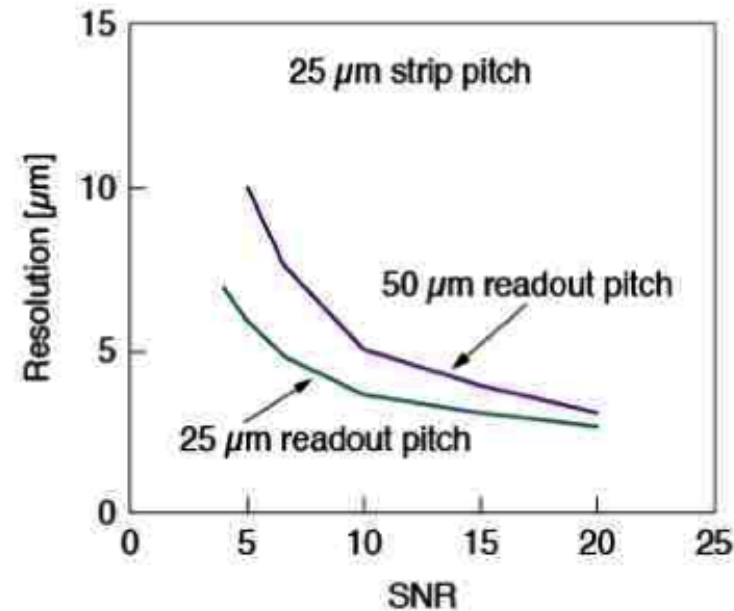 → **Trajectory of charged particles is an helix** – radius R

  → Use transverse (xy) and longitudinal (rz) projections

  → Pseudo-rapidity: $\eta = -\ln \tan \frac{\theta}{2}$ Transverse momentum: $p_T = p \sin \theta = p / \cosh \eta$

- Impact parameter is defined from dca to origin or PV:
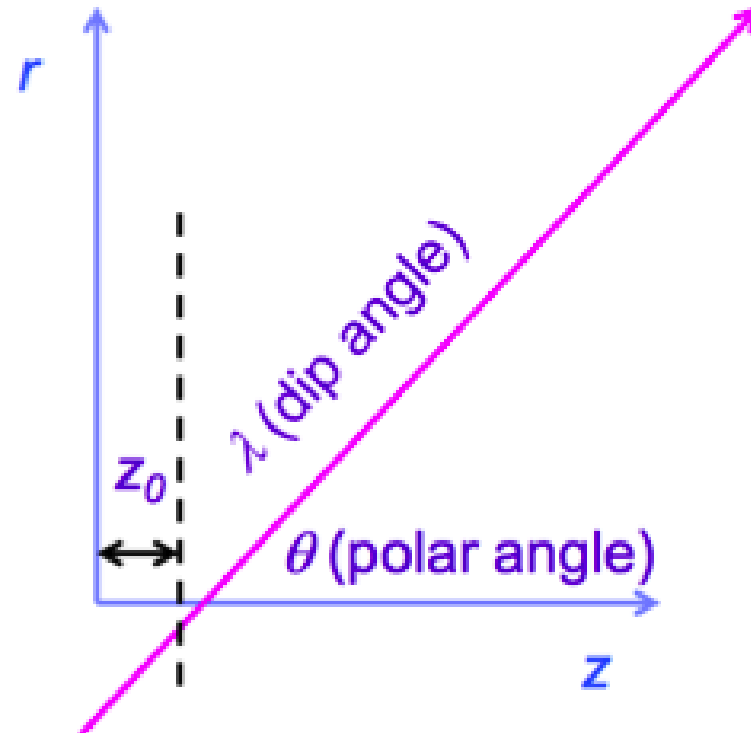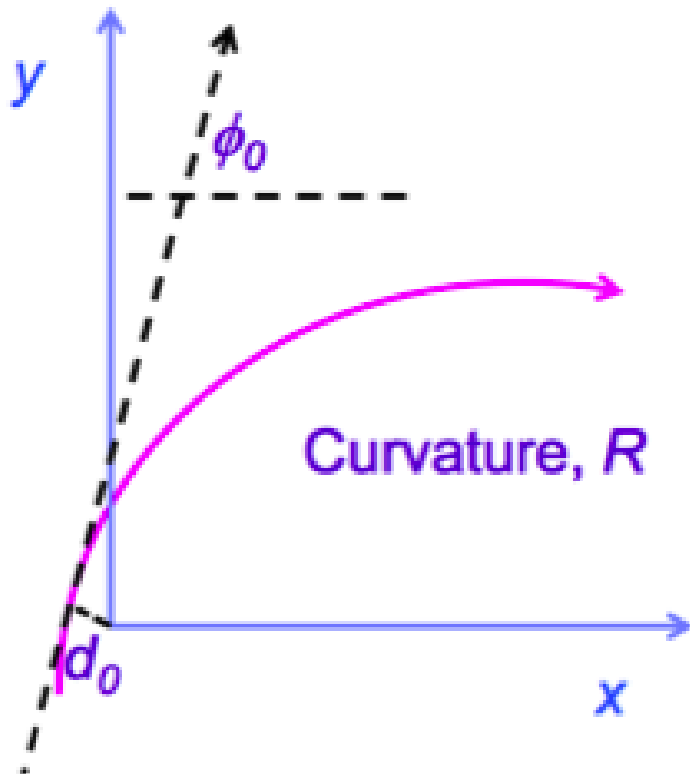
Resolution for the impact parameter

- **Depends on radii+space point precisions**

- For two layers we expect

$$\sigma_{d_0}^2 = \frac{r_2^2\sigma_1^2 + r_1^2\sigma_2^2}{(r_2 - r_1)^2}$$

  - Improve with small r_1, large r_2

  - Improves with better σ_i
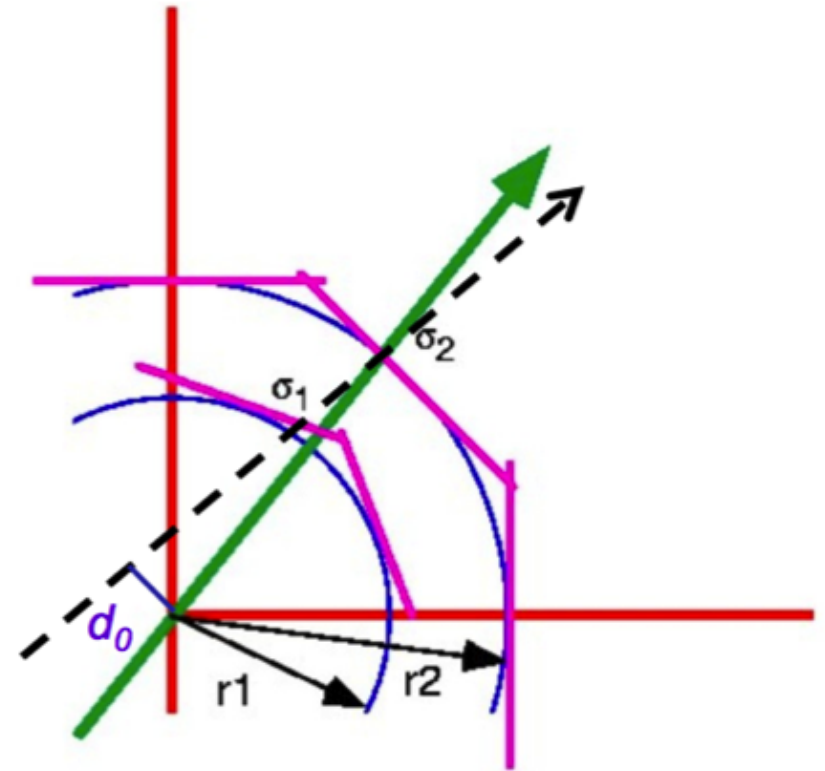
- Precision is degraded by **multiple scattering**

  - Gaussian approximation is valid, width given by

$$\theta_0 = \frac{13.6\text{MeV}}{\beta c p} z\sqrt{x/X_0}\left[1 + 0.038\ln(x/X_0)\right]$$

  - extra degradation term for d_0

$$\sigma_{d_0} \sim \theta_0$$

Resolution for the impact parameter

- For a track with $\theta \neq 90^0$ we can write $r \rightarrow r/\sin\theta$ and $x \rightarrow x/\sin\theta$

- By substitution in the formulas of the previous slide we have:

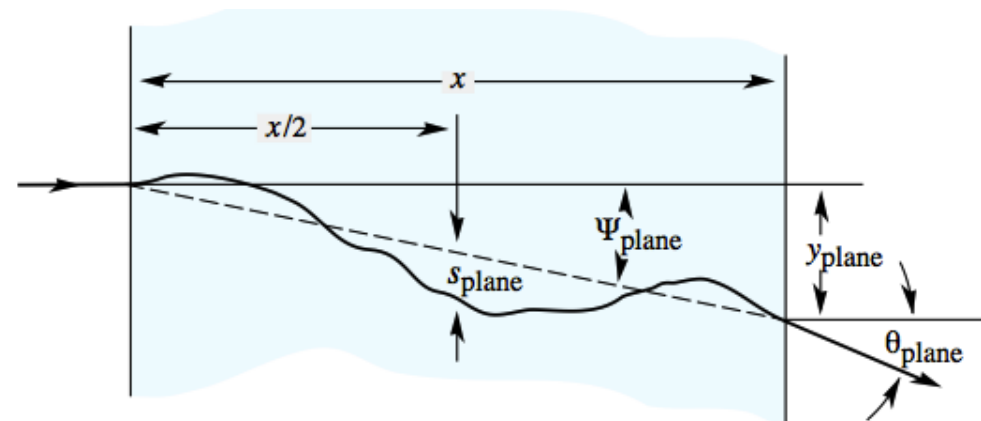$$\sigma_{d0} \sim \sqrt{\frac{r_2^2\sigma_1^2 + r_1^2\sigma_2^2}{(r_2-r_1)^2}} \oplus \frac{r}{p\sin^{3/2}\theta} \rightarrow a \oplus \frac{b}{p_T\sin^{1/2}\theta}$$

geometry-dependent   **Material- and p_T-dependent**

- **Resolution estimated with early pp data**

  - Observed

    100 µm   @ 1 GeV

    20 µm   @ 20 GeV

  - Excellent agreement with simulation

CMS preliminary 2010 $\sqrt{s}$ = 7 TeV

Transv. Impact Parameter Resolution (µm) vs Track p_T (GeV/c)

- Data   track $|\eta| < 0.4$
- Simulation track $|\eta| < 0.4$
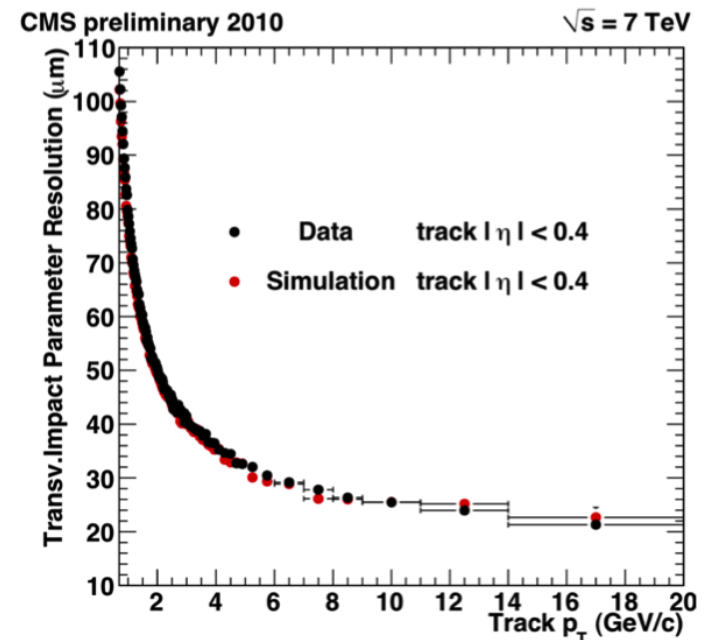
Examples from data: jets

- **Number of tracks** reconstructed in jets

  - → two samples compared: multijets and top-pairs

  - → track multiplicity is not well described by standard PYTHIA generator

  - → $t \rightarrow Wb$ naturally enriches the top-pair sample in b-jets

  - → B-hadrons are long-lived, b-jets often contain tracks with high d_0
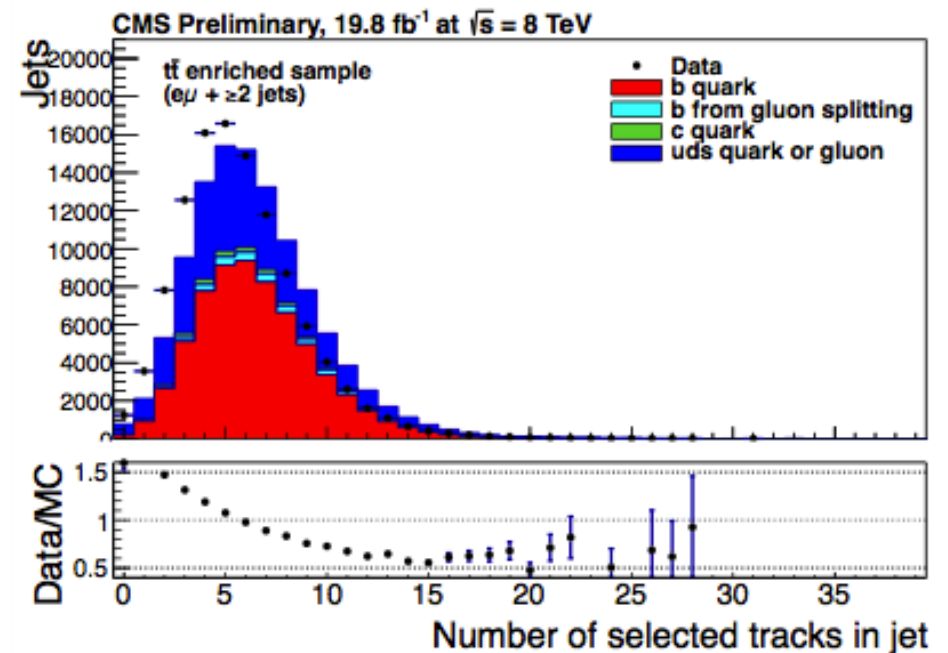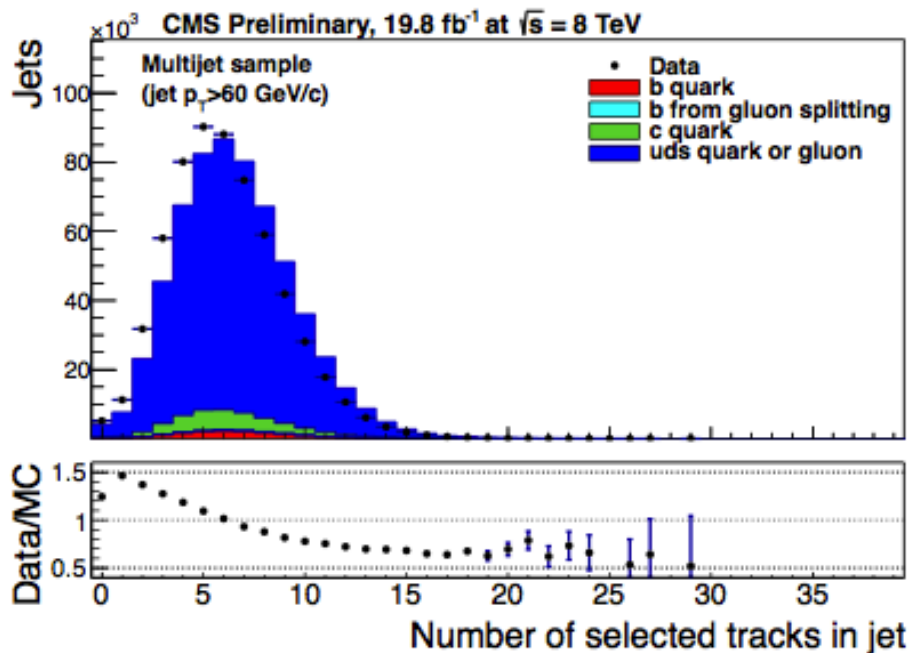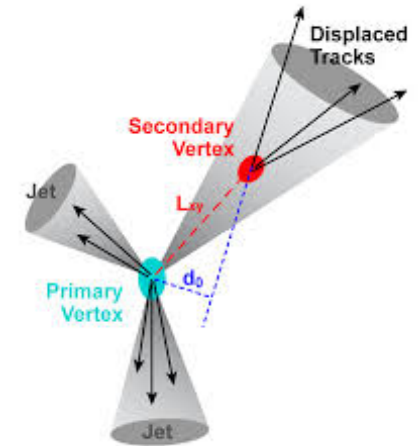
Examples from data: IP of tracks in jets

- Overall better agreement for b-jets: real displaced tracks

- Uncertainty on IP (resolution on IP) depends on the number of hits in pixels

  - jets from top pairs are more central with respect to a multijets sample
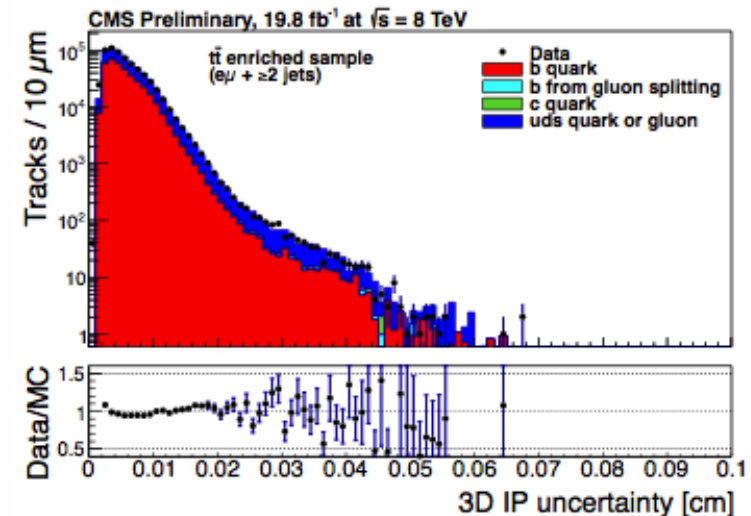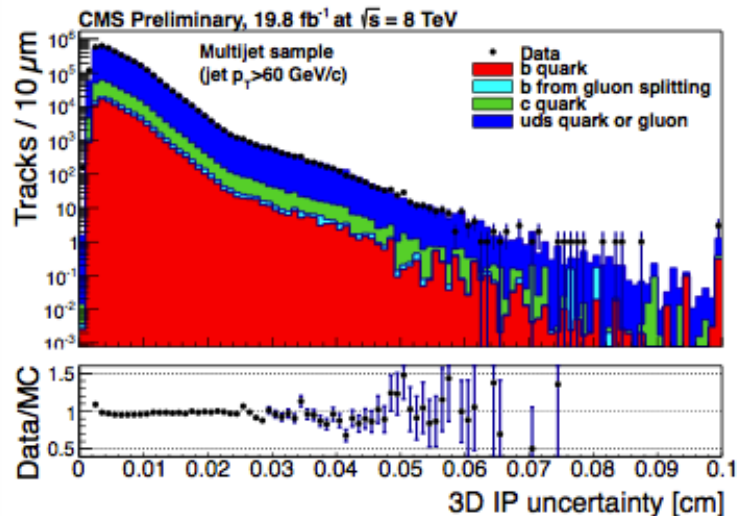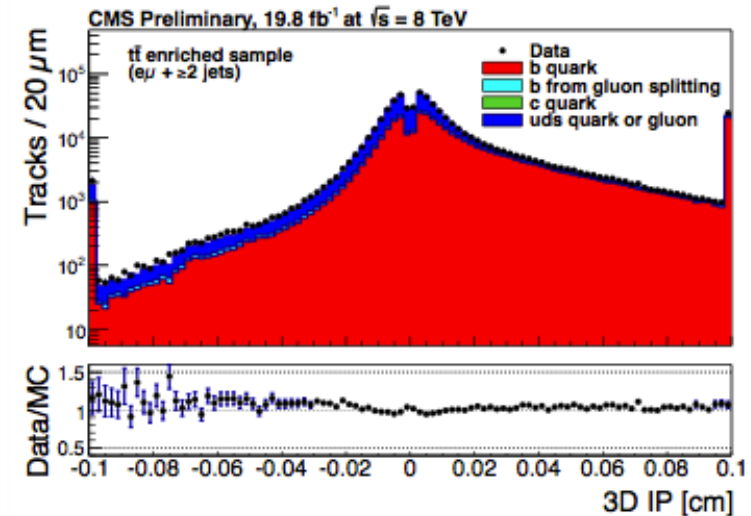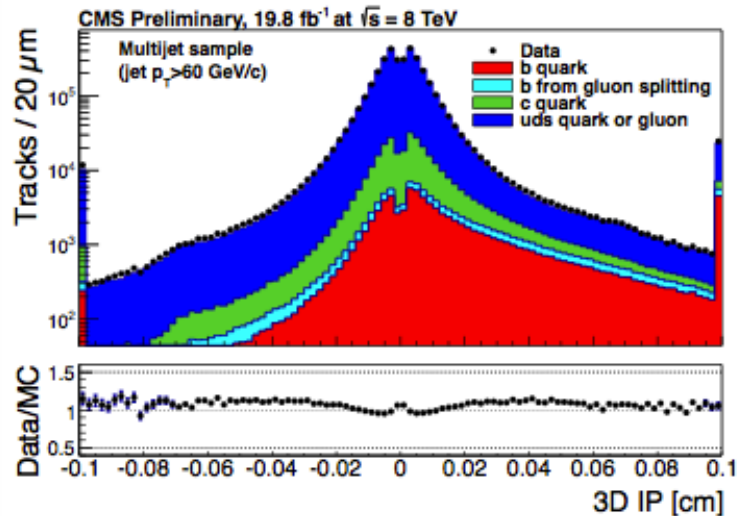
- Distribution of the **third track with highest d_0/σ_{d0}**

  - Simple b-tagging algorithm, with high purity – track counting high purity (TCHP)

  - Good description of the b-jets

  - Light jets hard to model in simulation: multiple scattering, fake hits, missing hits, conversions, V_0 decays
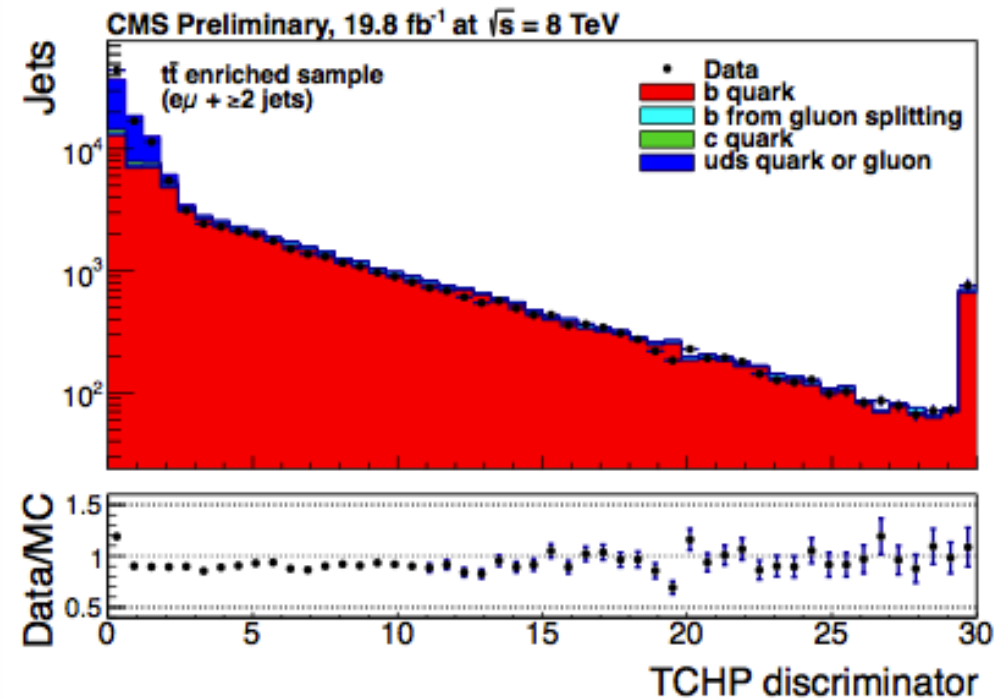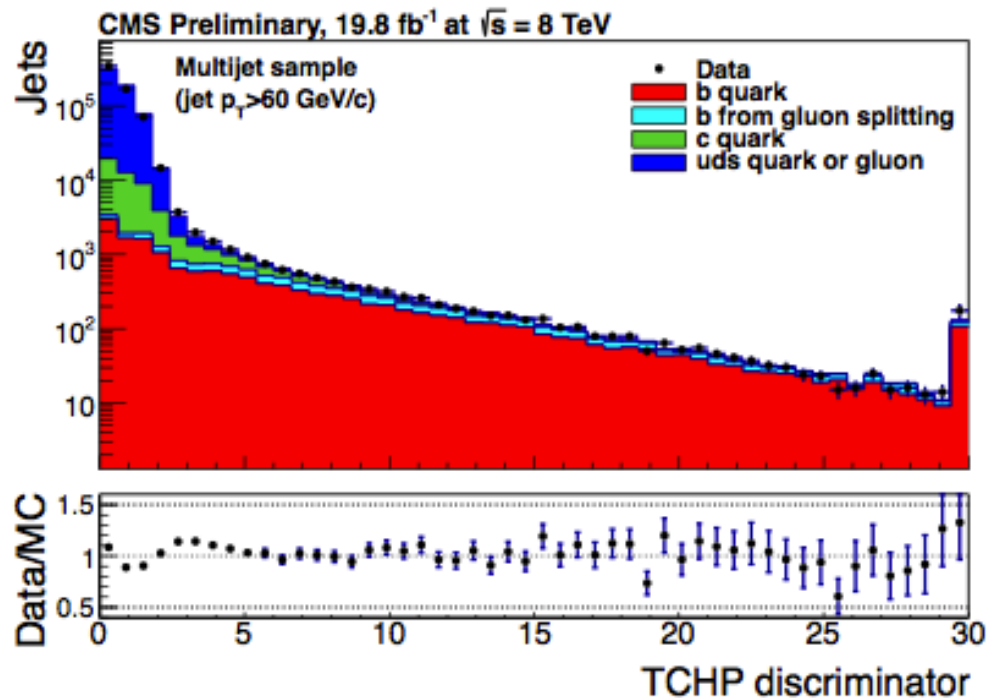
How can we profit from precision in d_0?

- …it's not only the b-tagging performance that benefits

- Can use measurement of the displaced vertices to measure fundamental properties

- **Boost of B-hadrons: proportional to the mass of a top quark when t→ Wb**

  → $$L_{xy} = \gamma_B \beta_B \tau_B \approx 0.4 \frac{m_t}{m_B} \beta_B \tau_B$$

  → Average shift of 30μm per 1 GeV

  → Use observed media to measure m_t

  $$m_t = 173.5 \pm 1.5_{stat} \pm 1.3_{syst} \pm 2.6_{p_T(top)} \text{GeV}$$

  → Simple, robust observables can measure fundamental properties
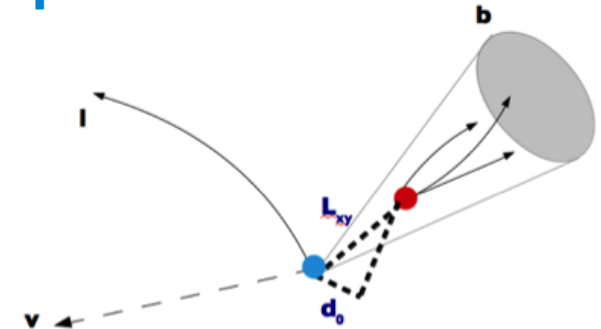
CMS Simulation, √s=8 TeV

TOP-12-030
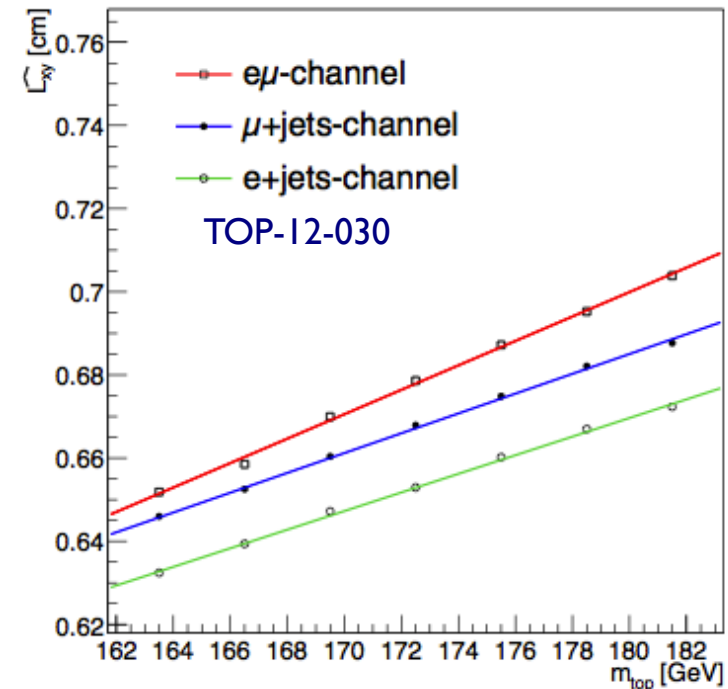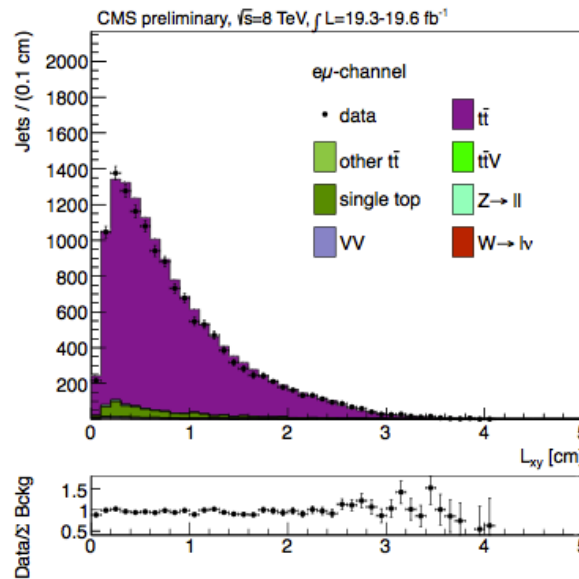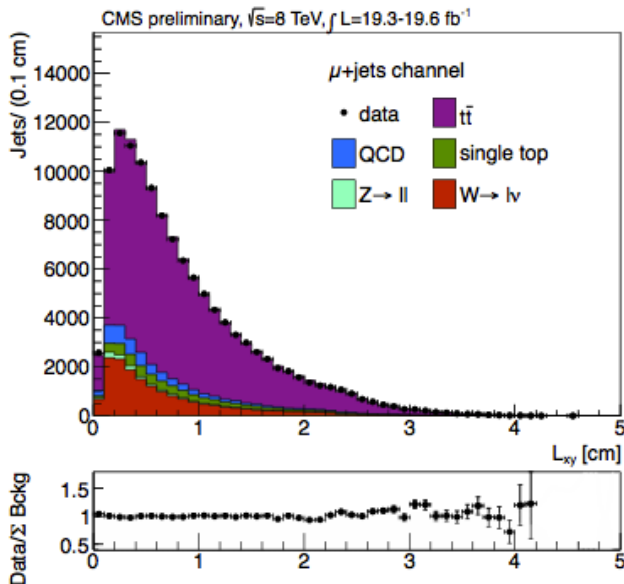
How can we profit to search for exotic signatures?

- ...it's not only precision measurements that benefit

- Search for long-lived particles decaying to jets

  → many displaced tracks: secondary vertex yielding two jets $X \to qq'$

  → e.g. $H \to 2X$, $\tilde{q} \to X^0 q \to 3q+\mu$
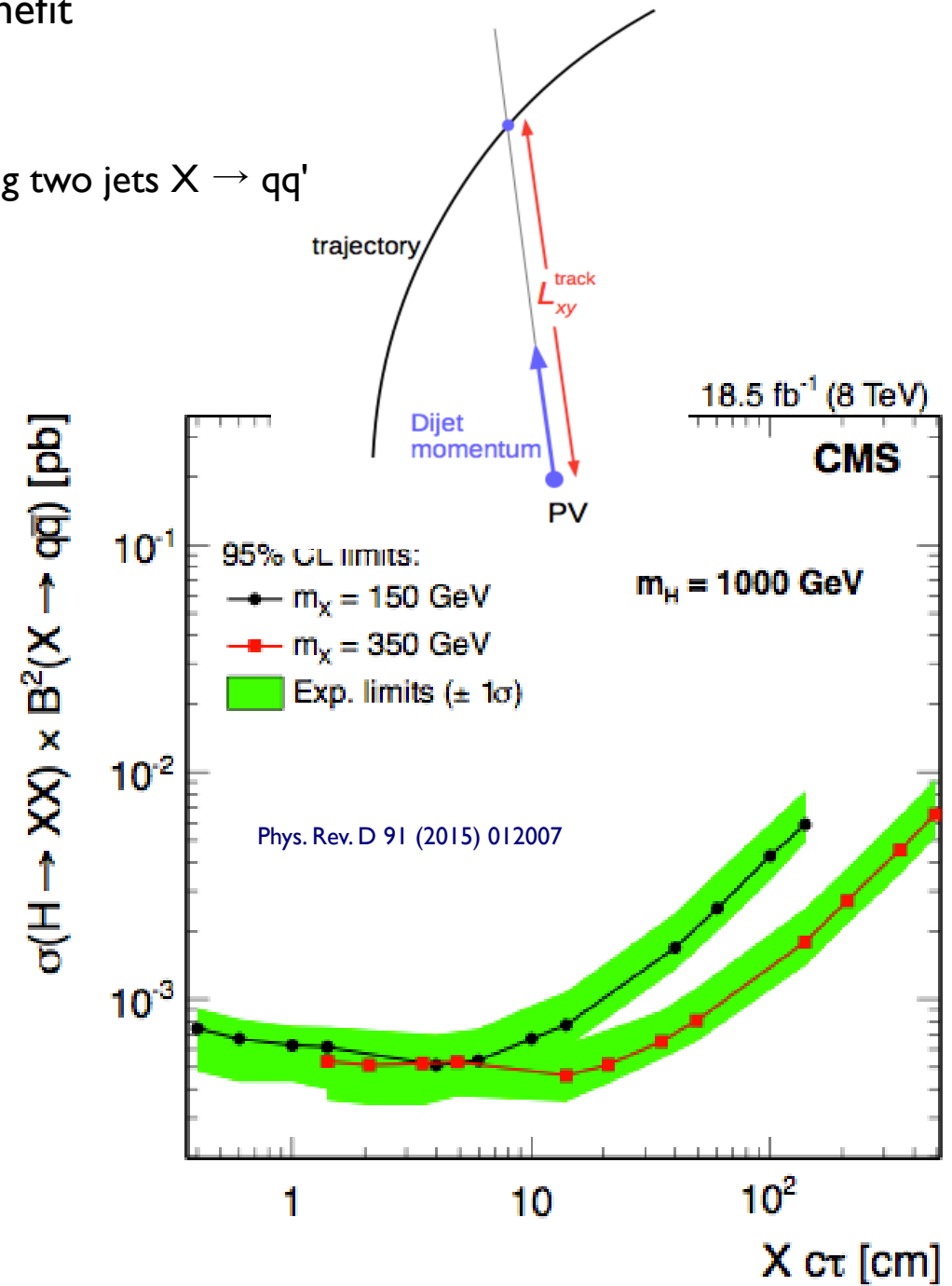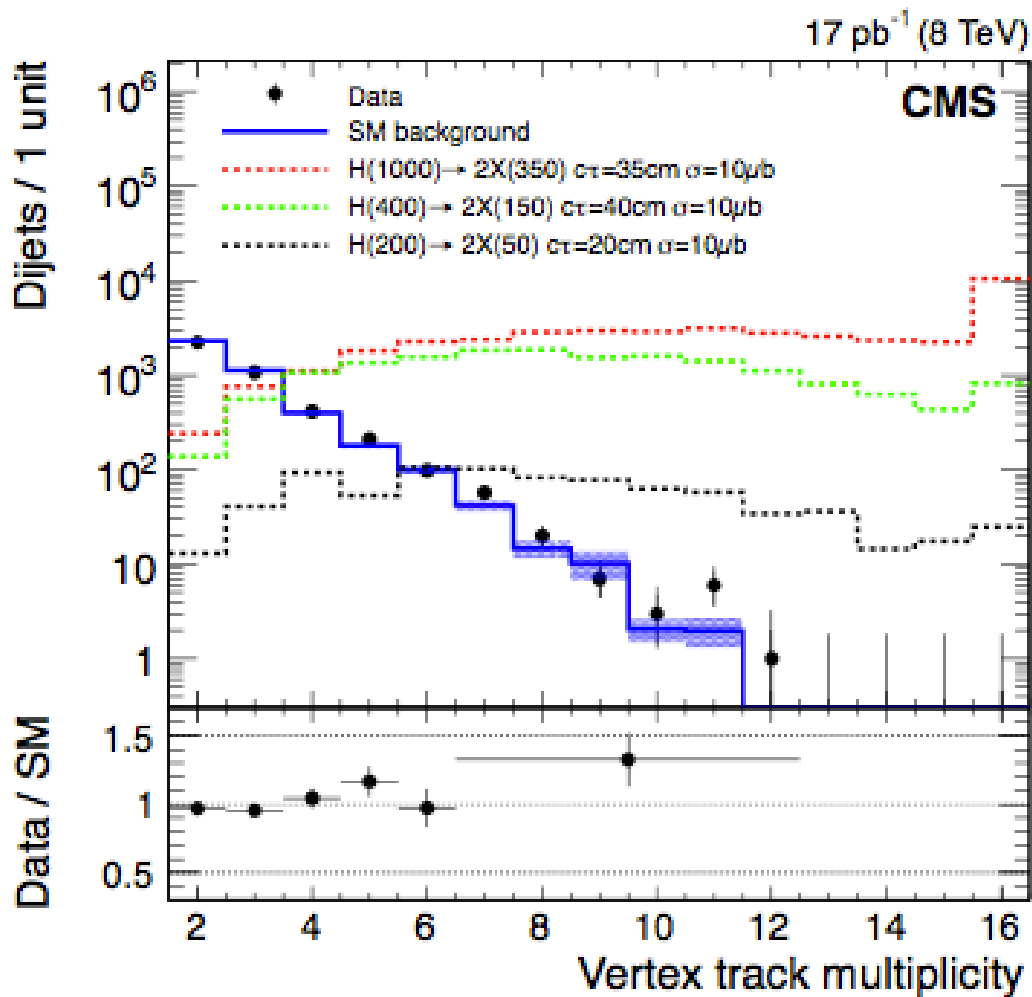
Momentum measurement

- Circular motion under uniform B-field

$$R[m] = 0.3 \frac{B[T]}{p_T[GeV]}$$

- **Measure sagitta**, s, from track ark

  → yields R estimate:

  $$R = \frac{L^2}{2s} + \frac{s}{2} \approx \frac{L^2}{2s}$$

  → relate to B and estimate p_T

$$\sigma_s = \sqrt{\frac{A_N}{N+4} \frac{\sigma_{r\phi}}{8}}$$

$A_N \approx 720$

- Uncertainty improves with B, number of hits, longer path L

$$\frac{\sigma_{p_T}}{p_T} = \frac{8 p_T}{0.3 B L^2} \sigma_s$$

- **Again, spoiled with multiple scattering:**

$$\frac{\sigma_{p_T}}{p_T} \sim a\, p_T \oplus \frac{b}{\sin^{1/2}\theta}$$
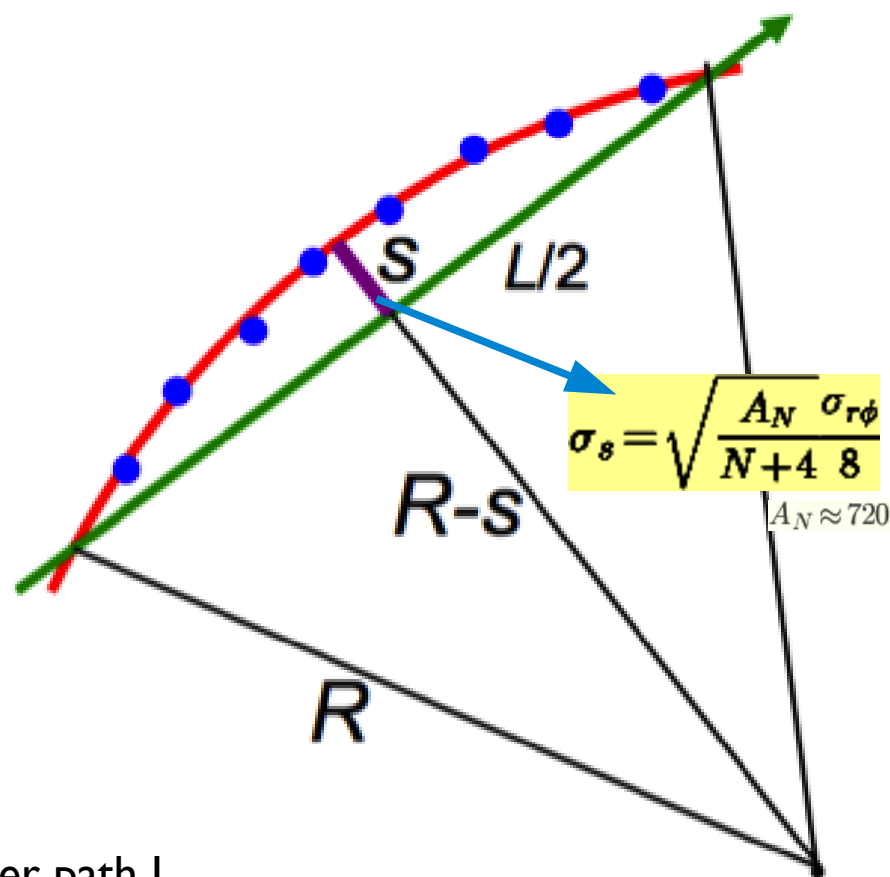
Momentum resolution

$$\frac{\sigma_{p_{\mathrm{T}}}}{p_{\mathrm{T}}} \sim a\, p_{\mathrm{T}} \oplus \frac{b}{\sin^{1/2}\theta}$$

$$\theta = 2\arctan(e^{-\eta})$$

Performance: ATLAS vs CMS

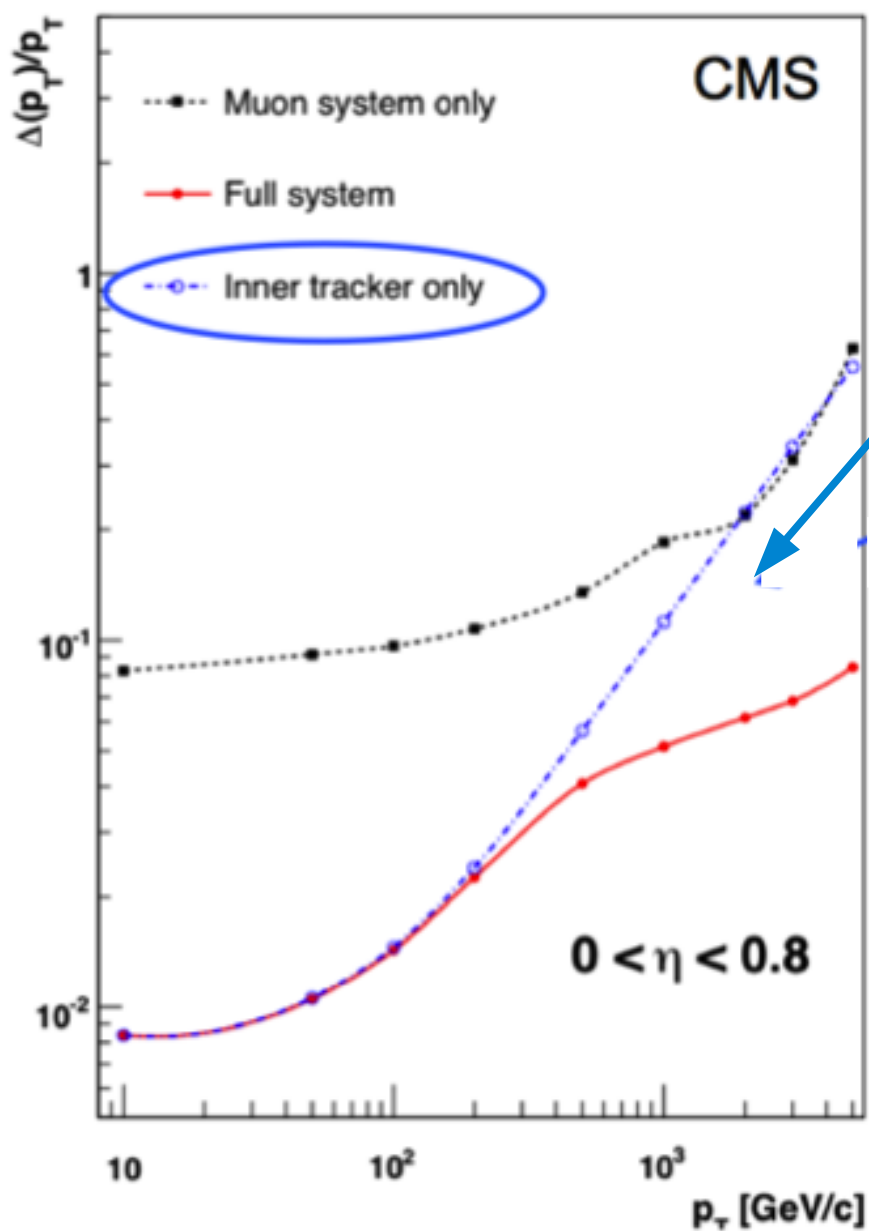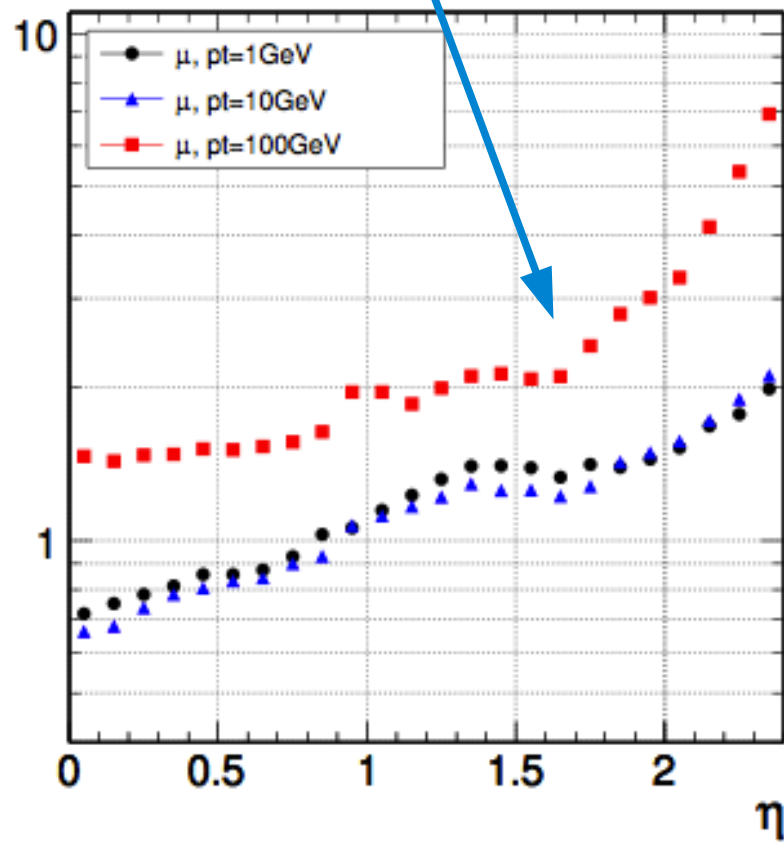|	ATLAS	CMS
Reconstruction efficiency for muons with $p_T = 1$ GeV	96.8%	97.0%
Reconstruction efficiency for pions with $p_T = 1$ GeV	84.0%	80.0%
Reconstruction efficiency for electrons with $p_T = 5$ GeV	90.0%	85.0%
Momentum resolution at $p_T = 1$ GeV and $\eta \approx 0$	1.3%	0.7%
Momentum resolution at $p_T = 1$ GeV and $\eta \approx 2.5$	2.0%	2.0%
Momentum resolution at $p_T = 100$ GeV and $\eta \approx 0$	3.8%	1.5%
Momentum resolution at $p_T = 100$ GeV and $\eta \approx 2.5$	11%	7%
Transverse i.p. resolution at $p_T = 1$ GeV and $\eta \approx 0$ (μm)	75	90
Transverse i.p. resolution at $p_T = 1$ GeV and $\eta \approx 2.5$ (μm)	200	220
Transverse i.p. resolution at $p_T = 1000$ GeV and $\eta \approx 0$ (μm)	11	9
Transverse i.p. resolution at $p_T = 1000$ GeV and $\eta \approx 2.5$ (μm)	11	11
Longitudinal i.p. resolution at $p_T = 1$ GeV and $\eta \approx 0$ (μm)	150	125
Longitudinal i.p. resolution at $p_T = 1$ GeV and $\eta \approx 2.5$ (μm)	900	1060

- CMS tracker outperforms ATLAS: better momentum resolution, similar vertexing

- However it comes with a cost (next slide)

CMS tracker
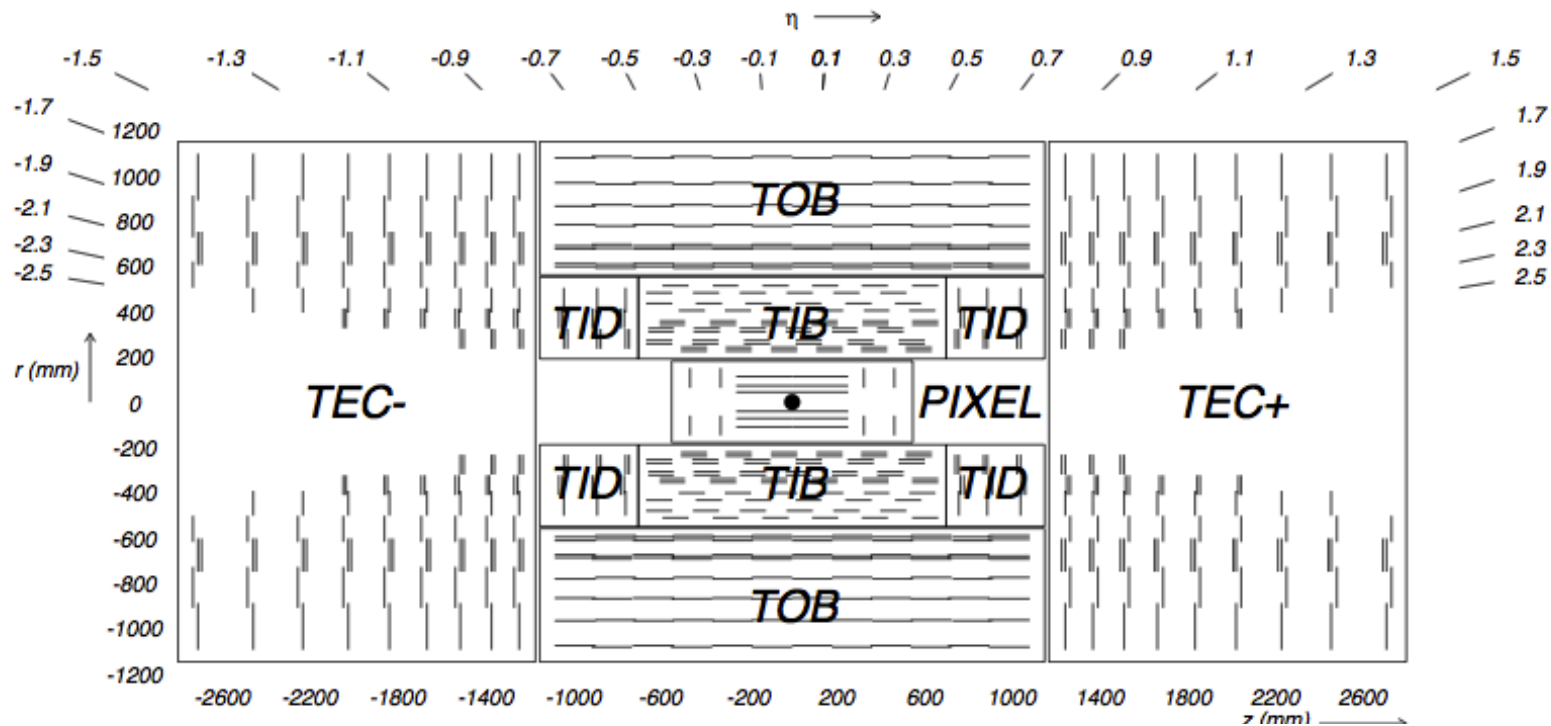
- Pixel detector: ~1m² area

  - 1.4k modules

  - 66M pixels

- Strips: ~200m² area

  - 24k single sensors, 15k modules

  - 9.6M strips = electronics channels

  - 75k readout chips
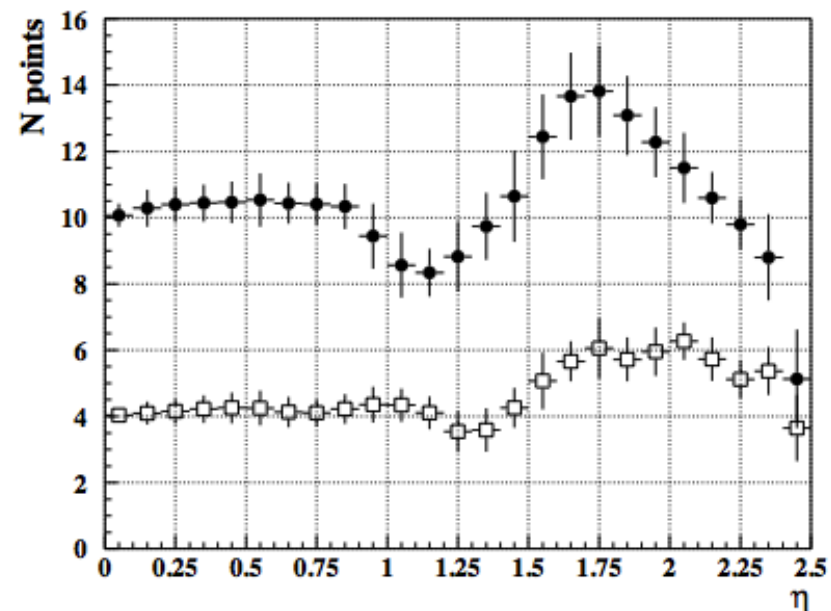
CMS tracker budget

- In some regions can attain $1.8X_0$ → photons convert, electrons radiate often

- Use for alignment and material budget estimation

  - Simulation crucial for H → γγ, H → ZZ → 2e2μ, 4e
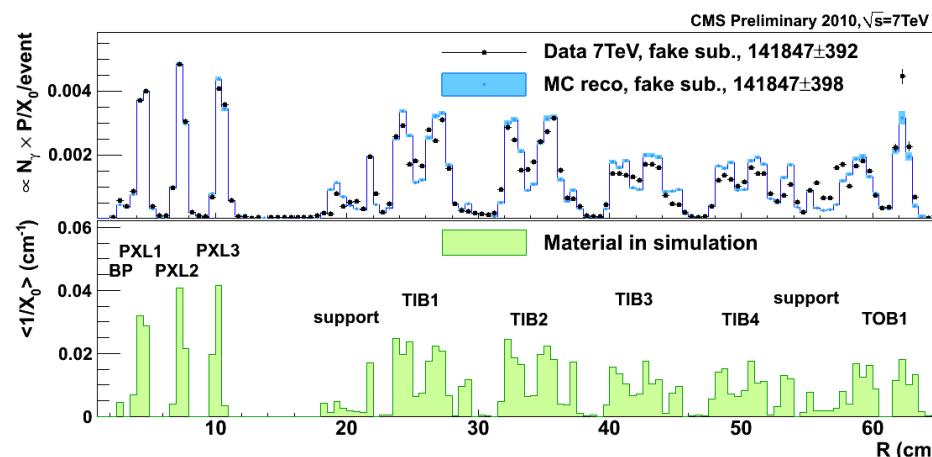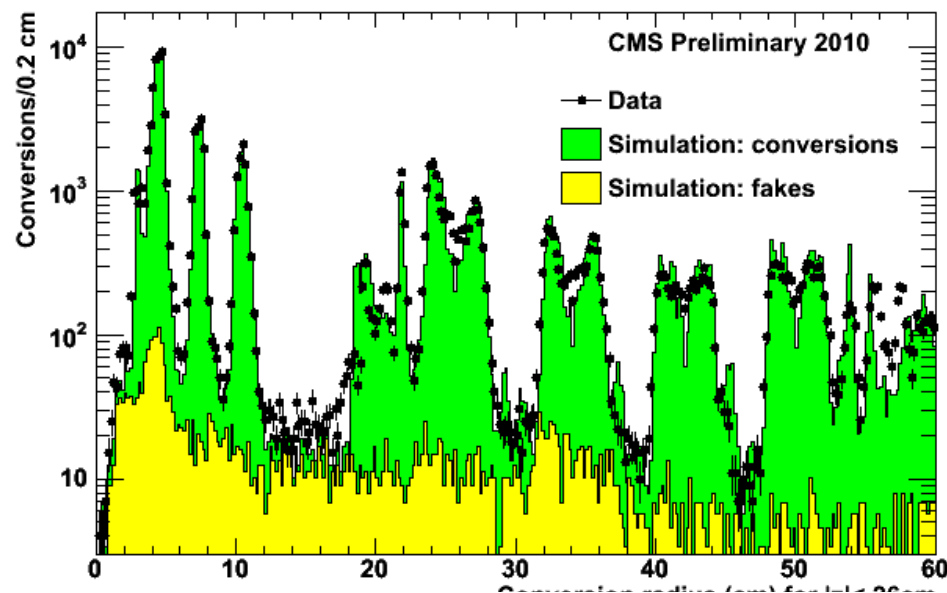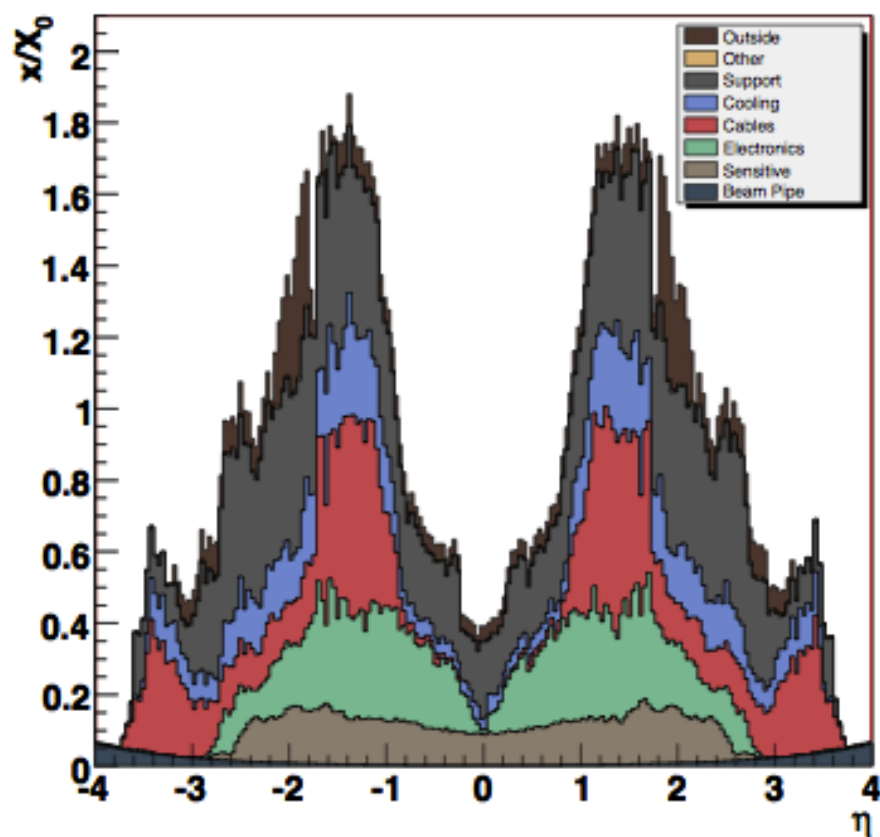
X-ray of the CMS tracker

- Conversions: γ → e⁺e⁻

  - two op. Charged tracks consistent from the same point

  - consistent with fit to a common vertex with M=0 GeV

  - Note: 54% of the H → γγ events have are expected to have at least one conversion
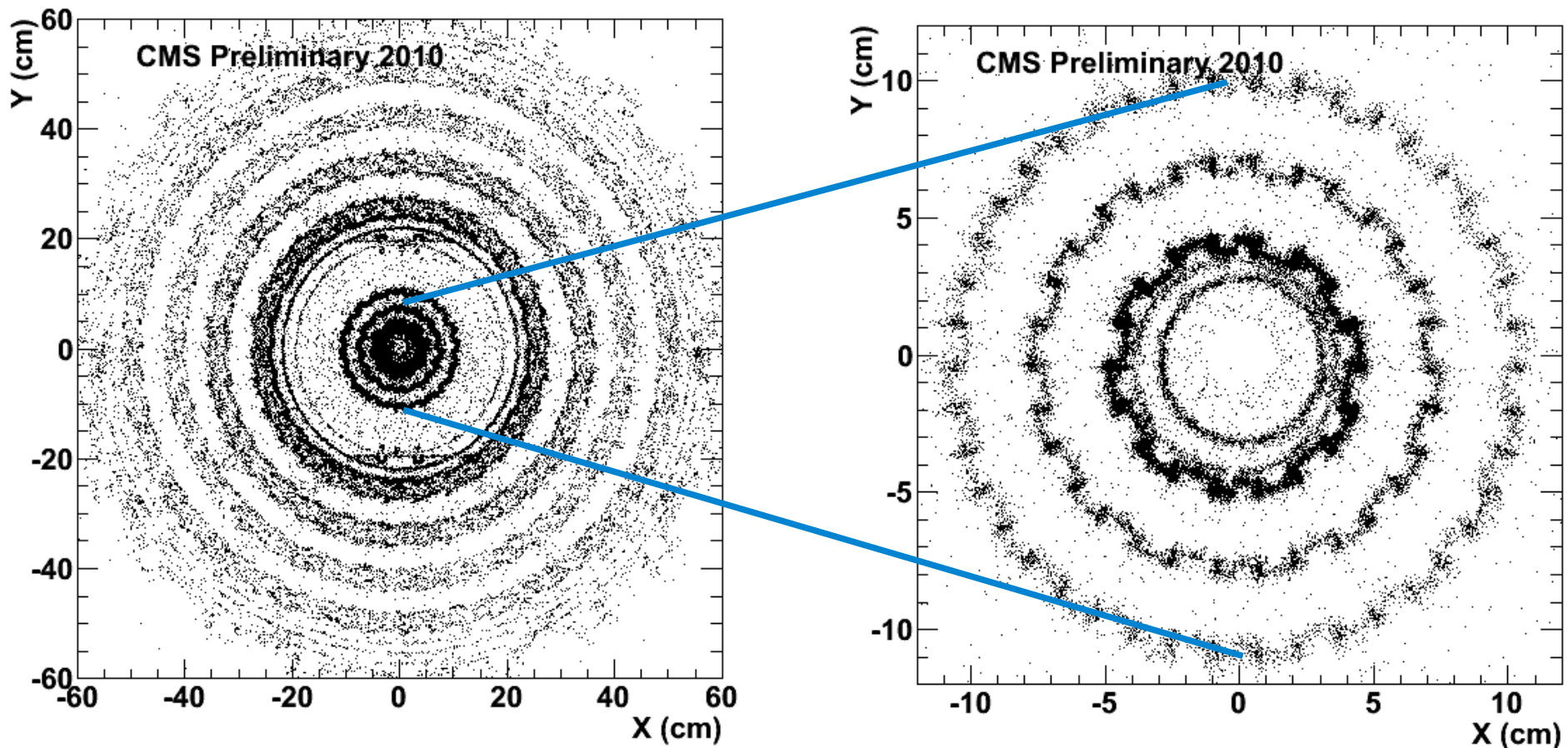
Alignment check

- Use reconstructed long-lived neutral hadrons to compare simulation, PDG and data

V^0	Mass (MeV/c^2)			
	Data	PDG	Simulation	Generated
K_S^0	497.68 ± 0.06	497.61 ± 0.02	498.11 ± 0.01	497.670
Λ^0	1115.97 ± 0.06	1115.683 ± 0.006	1115.93 ± 0.02	1115.680

Parameter	K_S^0 Data	K_S^0 Simulation	Λ^0 Data	Λ^0 Simulation
σ_1 (MeV/c^2)	4.53 ± 0.12	4.47 ± 0.04	1.00 ± 0.26	1.71 ± 0.05
σ_2 (MeV/c^2)	11.09 ± 0.41	10.49 ± 0.11	3.25 ± 0.14	3.71 ± 0.09
σ_1 fraction	0.58 ± 0.03	0.58 ± 0.01	0.15 ± 0.05	0.44 ± 0.03
$\bar{\sigma}$ (MeV/c^2)	7.99 ± 0.14	7.63 ± 0.03	3.01 ± 0.08	2.99 ± 0.03

$$\tau_{K_S^0} = 90.0 \pm 2.1\,\text{ps}$$

$$\tau_{\Lambda^0} = 271 \pm 20\,\text{ps}$$, *both consistent with world average*
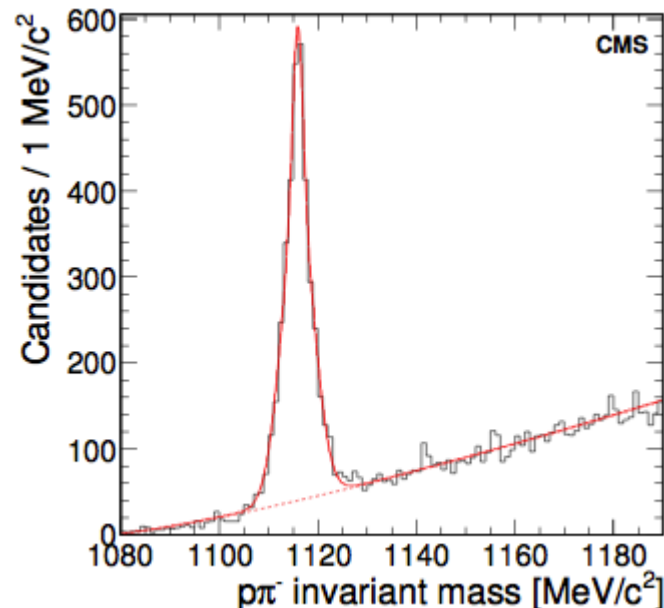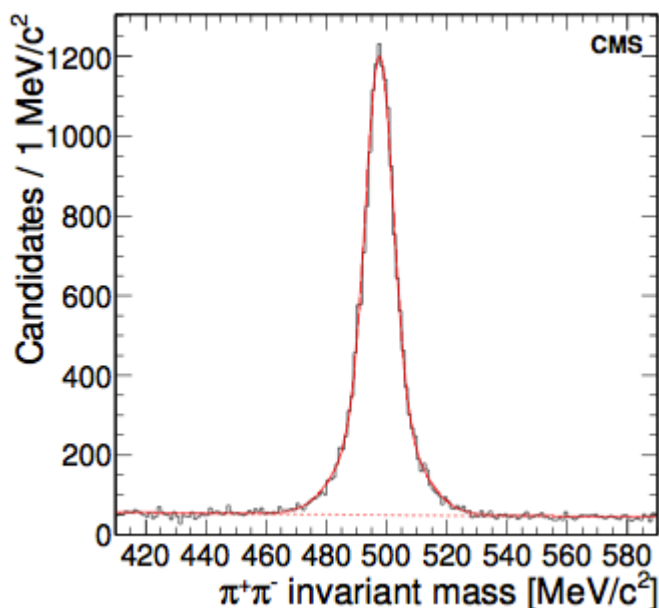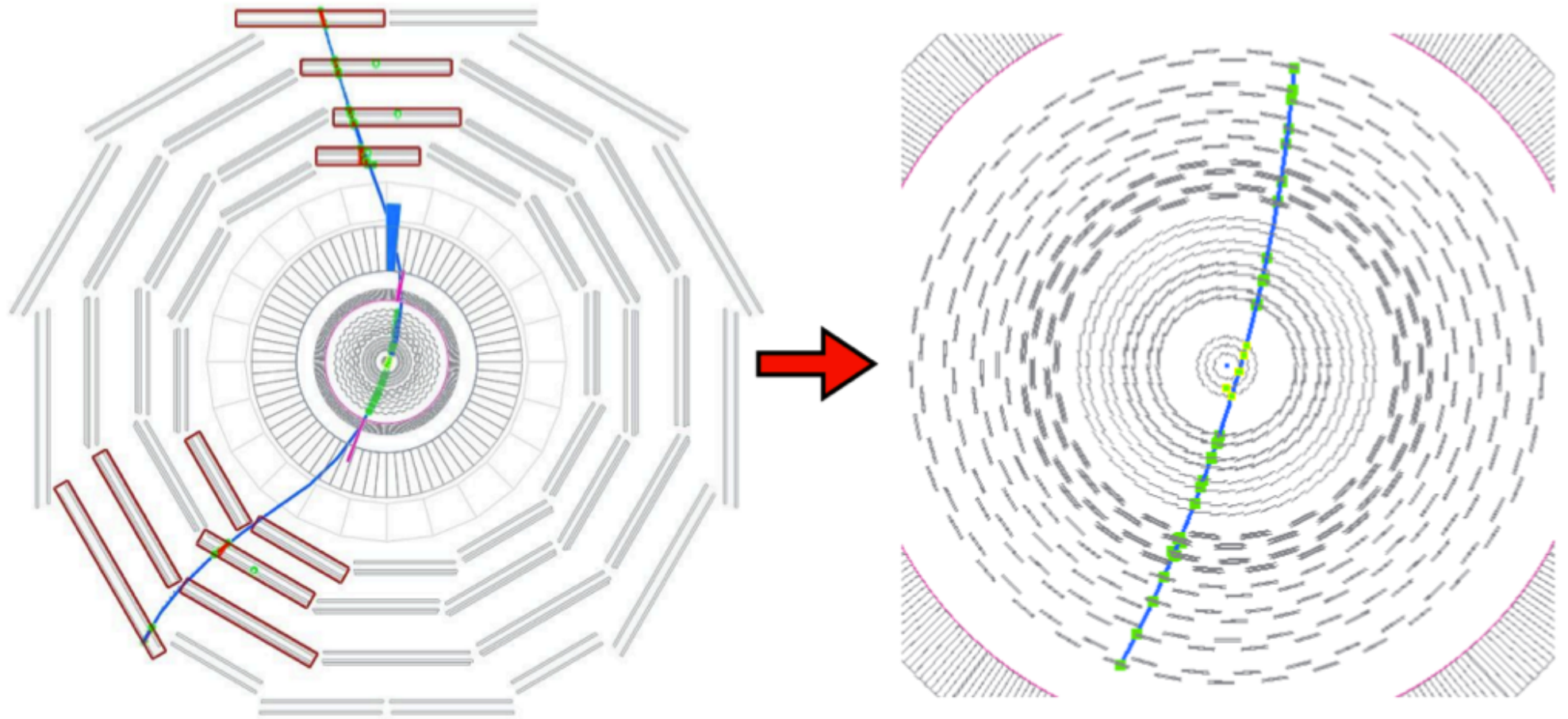
Find muons with the tracking system

- Standard-approach: **outside-in**

  - → Standalone muon

  - → Combine with tracker track

  - → Fit a Global Muon track

- Complementary approach: **inside-out**

  - → Extrapolate every track outward

  - → Find compatible deposits in calorimeters

  - → Define muon compatibility

- **Recovers inefficiencies**

  - → Boundaries of muon chambers, low p_T

p_t = 3.5, 4.0, 4.5, 6.0 GeV

CMS $\sqrt{s}$ = 7 TeV L = 36 pb^{-1}

p_T > 15 GeV/c

■ **Simulation**

┼ **Data**

Standalone to track resolution

1/p_T resolution
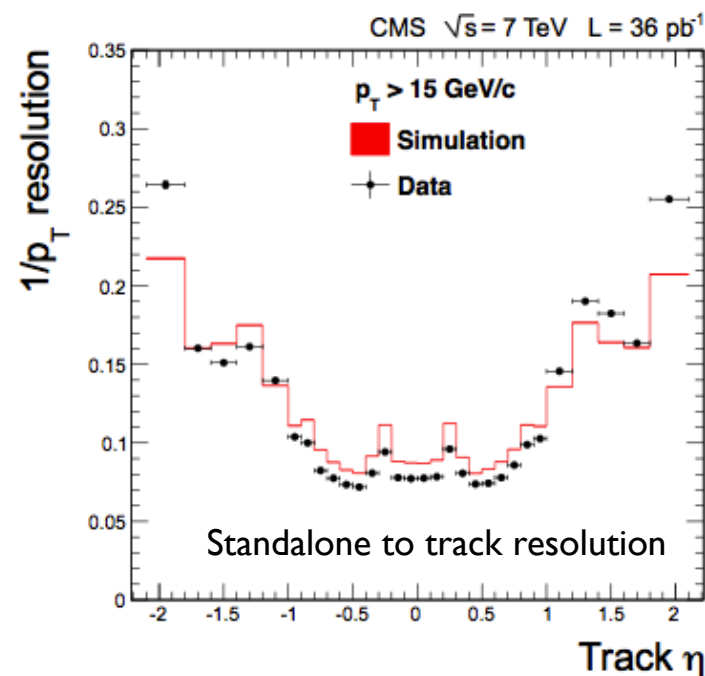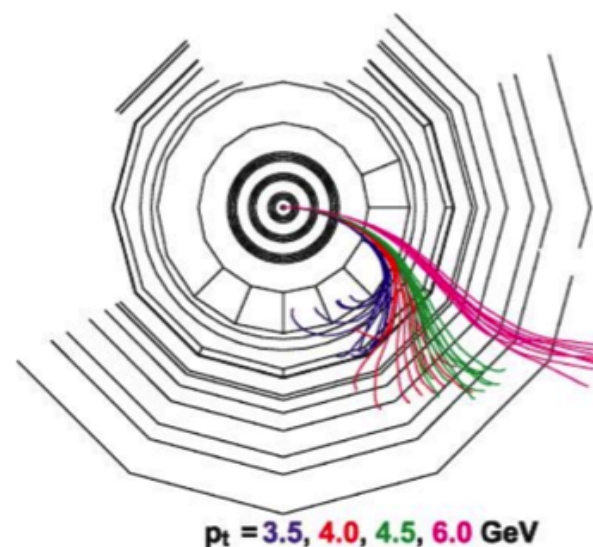
Track η

Performance: ATLAS vs CMS II

ATLAS

- B=0.7 T (toroidal)
- L~5m
- N=3 stations x 8 points
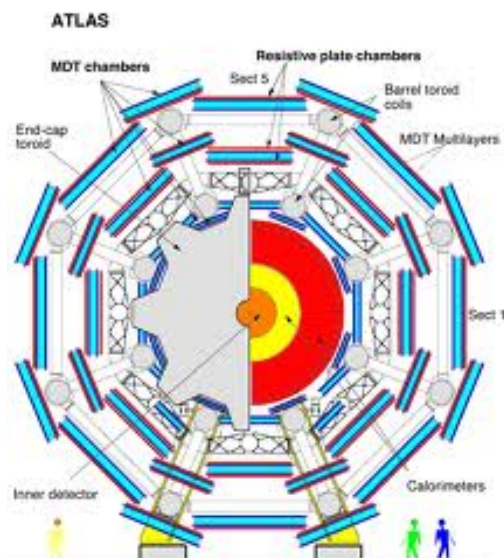
- s=750 μm for 1 TeV track
- 10% → σ=75 μm

Δp/p~6%

CMS

- B~2T (in return yoke)
- L~3.5m
- N=4 stations x 8 points in rφ
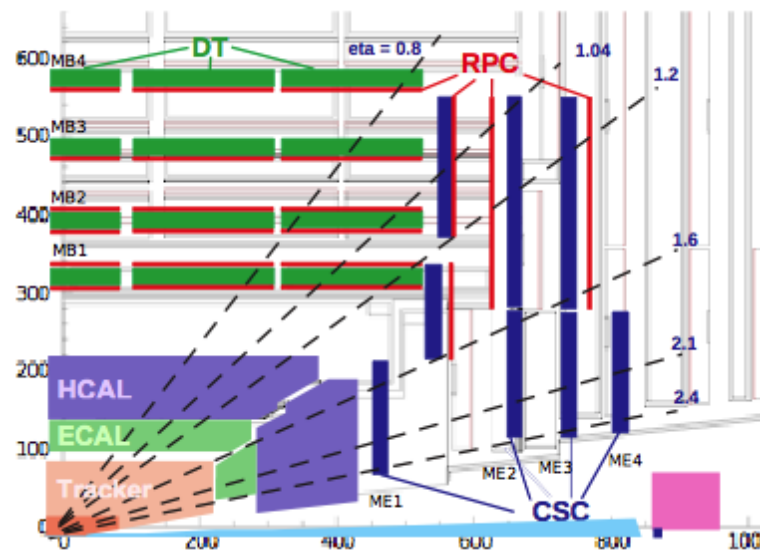
- s=900 μm for 1 TeV track
- 10% → s=90μm

Δp/p~12%

Spoiled by multiple scattering in Fe

Combined muon performance in CMS

Combine with tracker: Δp/p~2%
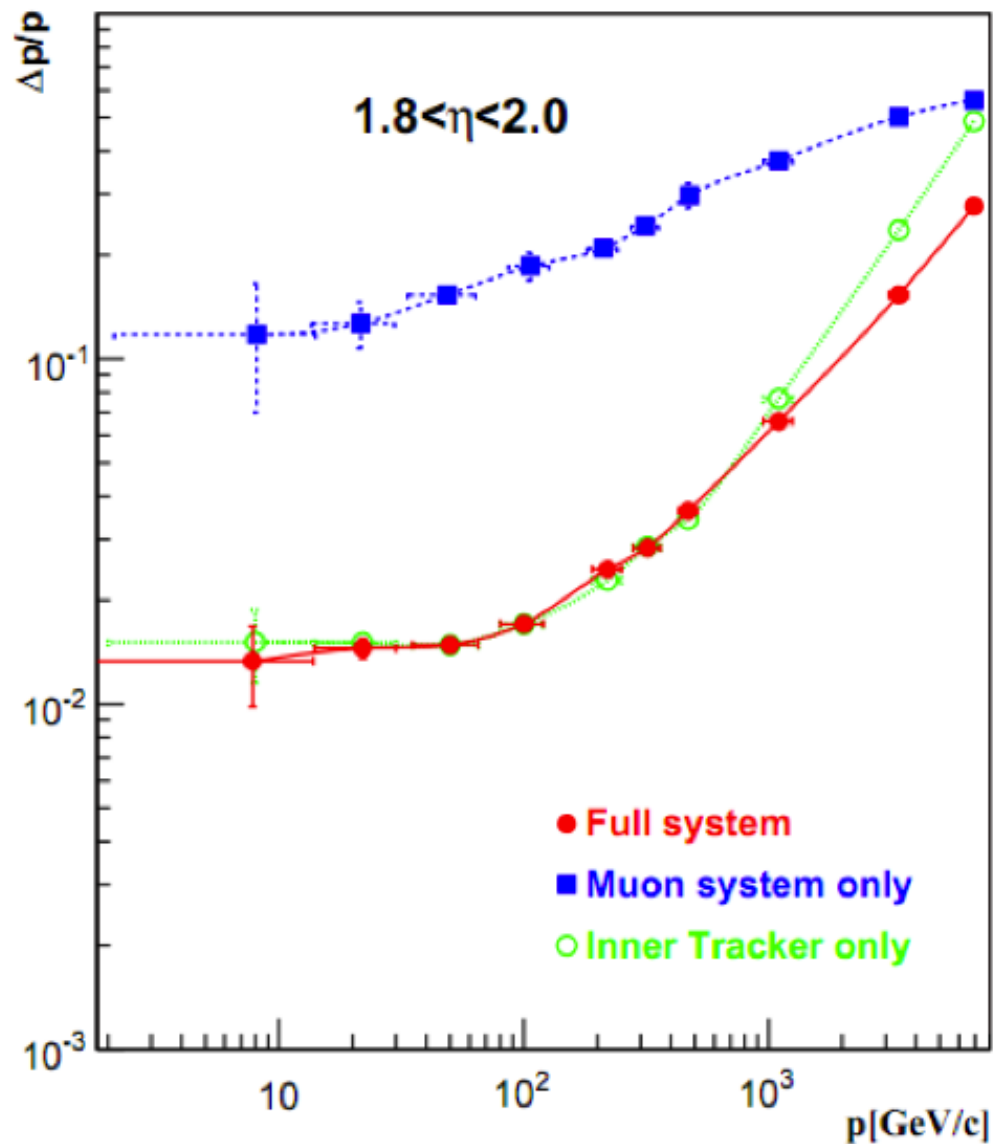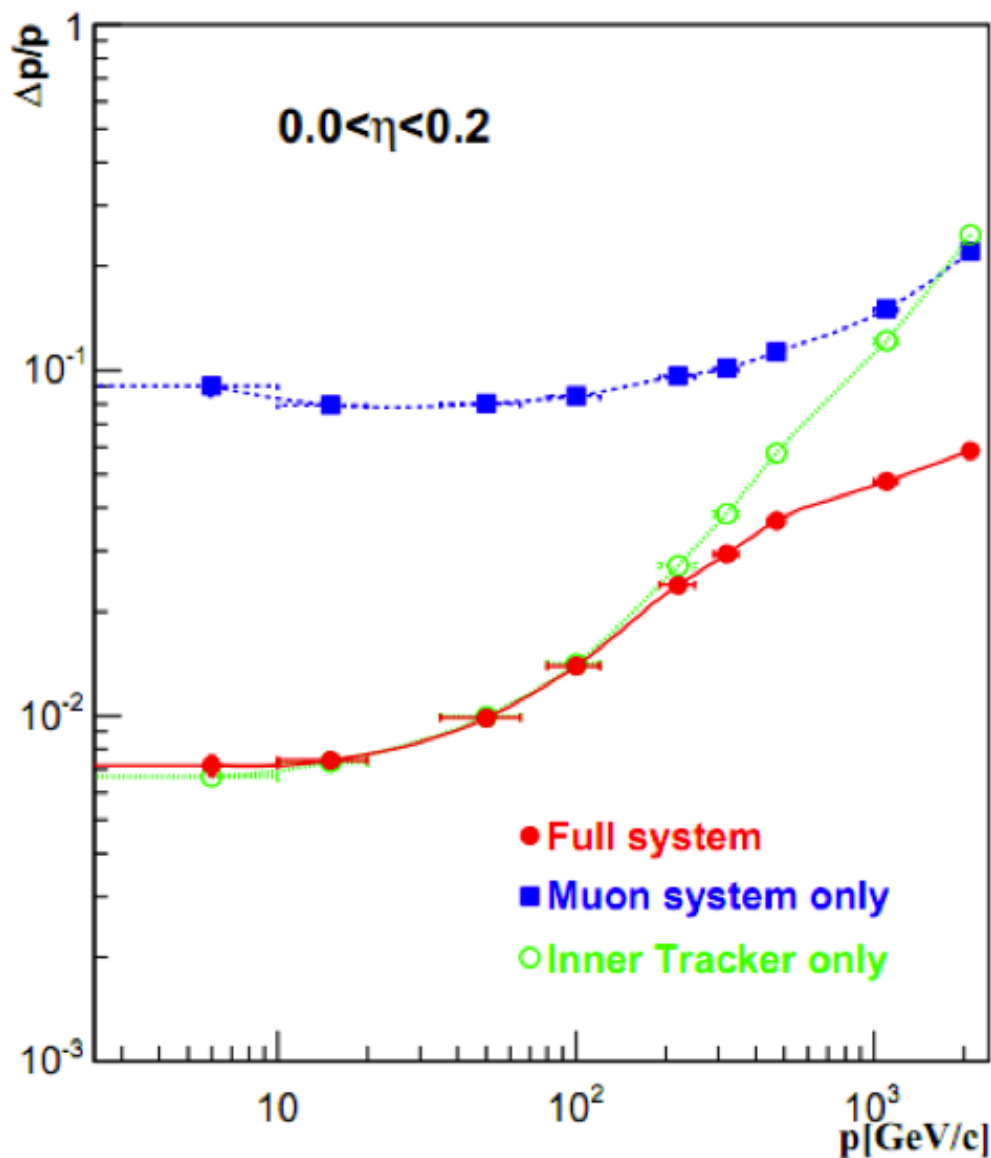
CMS dimuon performance
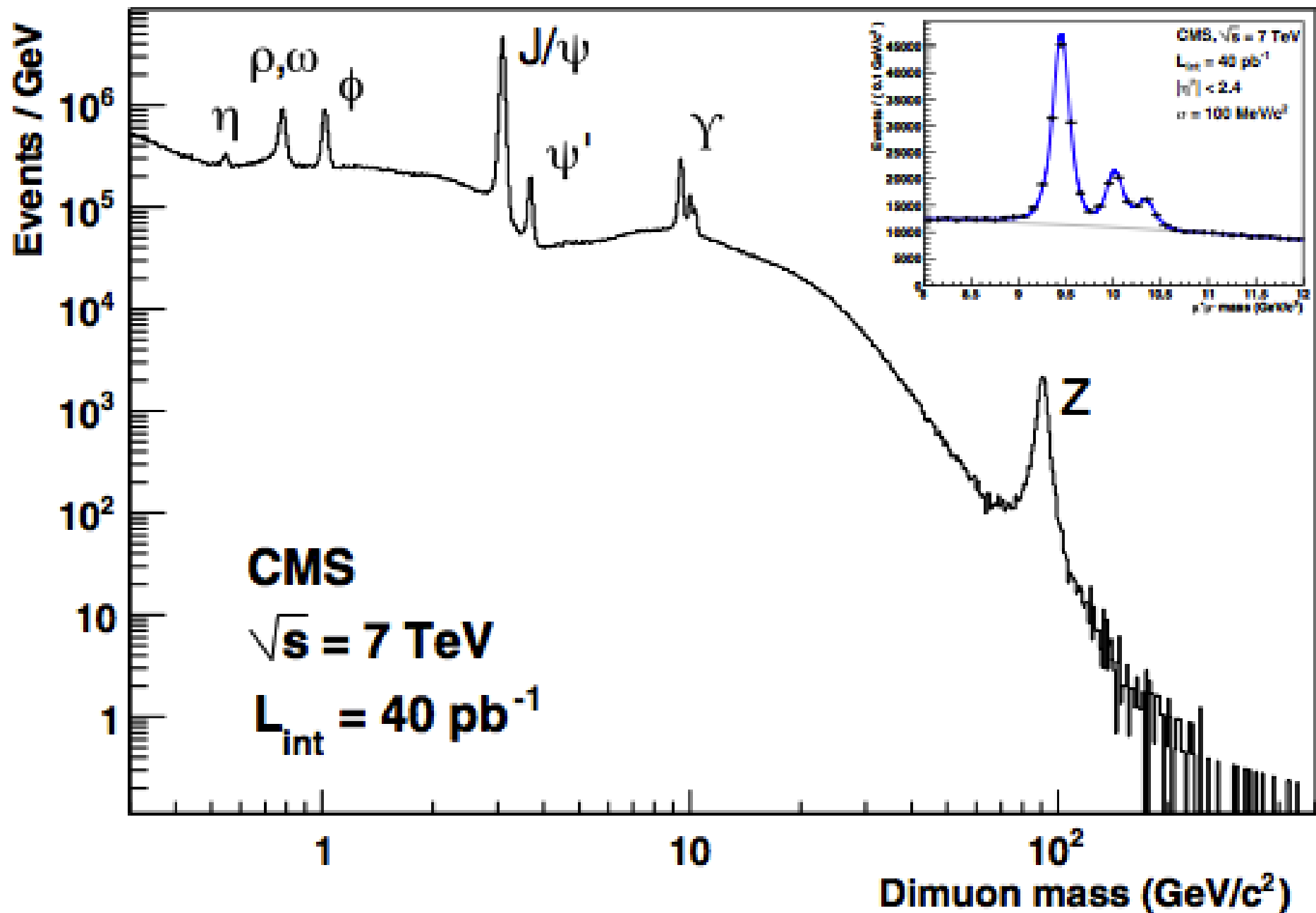
Triggering

Why do we trigger?

- **Data rates at hadron colliders are too high**

    - most events are expected not to be interesting anyway

    - save to tape only relevant physics

    - need a trigger = online selection system which reduces rates by a factor of $\sim 10^5$

Collider	Crossing rate (kHz)	Event size (MB)	Trigger rate	Raw data rate (PB/year)	Data rate after trigger (PB/year)
LEP	45	0.1	5 Hz	10^2	~0.01
Tevatron	2.5	0.25	50-100 Hz	10^4	0.1
HERA	10	0.1	5 Hz	10^4	0.01
LHC	**40**	**1**	**100-200 Hz**	**10^5**	**1**

proton - (anti)proton cross sections

Simplified overview of how it works

Trigger system

A

**DAQ
Data acquisition
system**
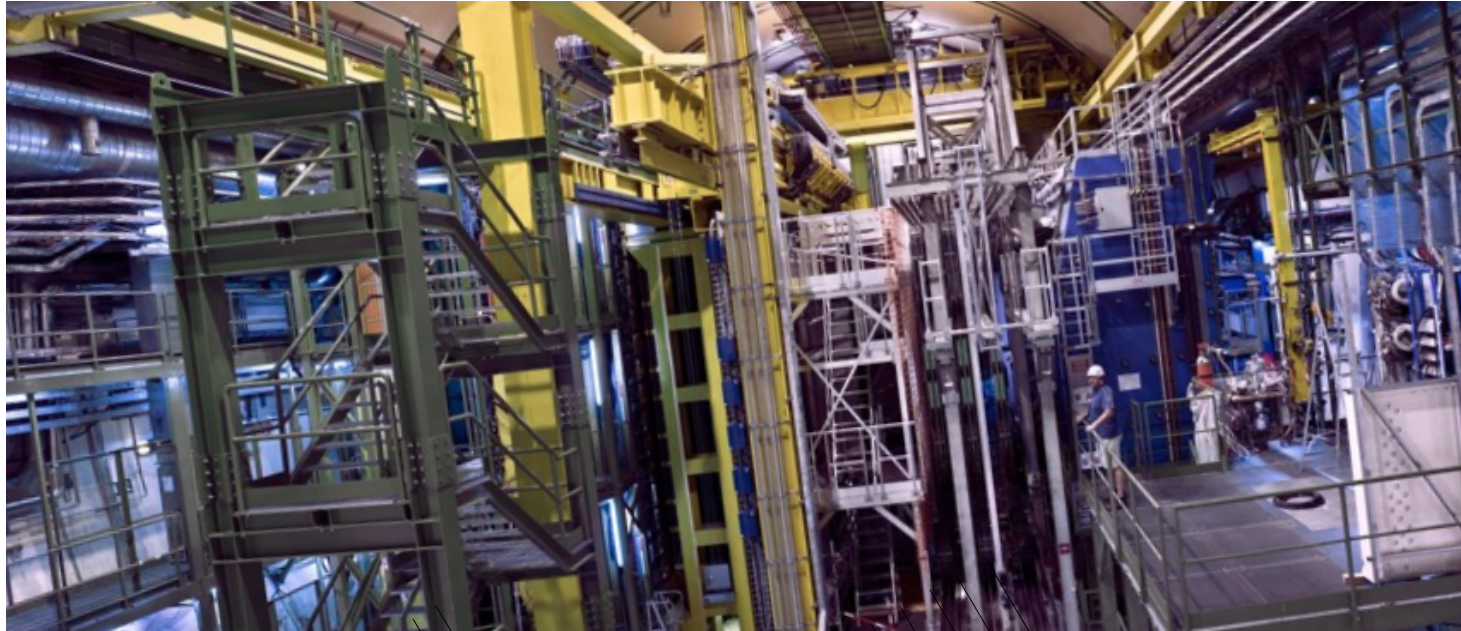
Mass storage

*Performs real-time
selection based on a
subset of the data to
record*

*Collects the data from all the
sub-detectors and trigger
systems and sends them to
mass storage for offline analysis*

Dead time

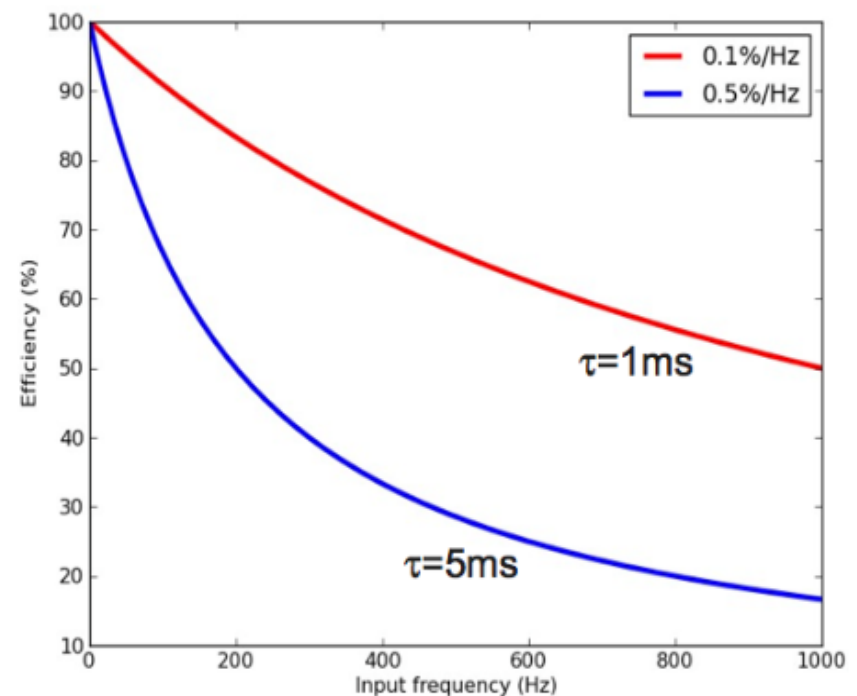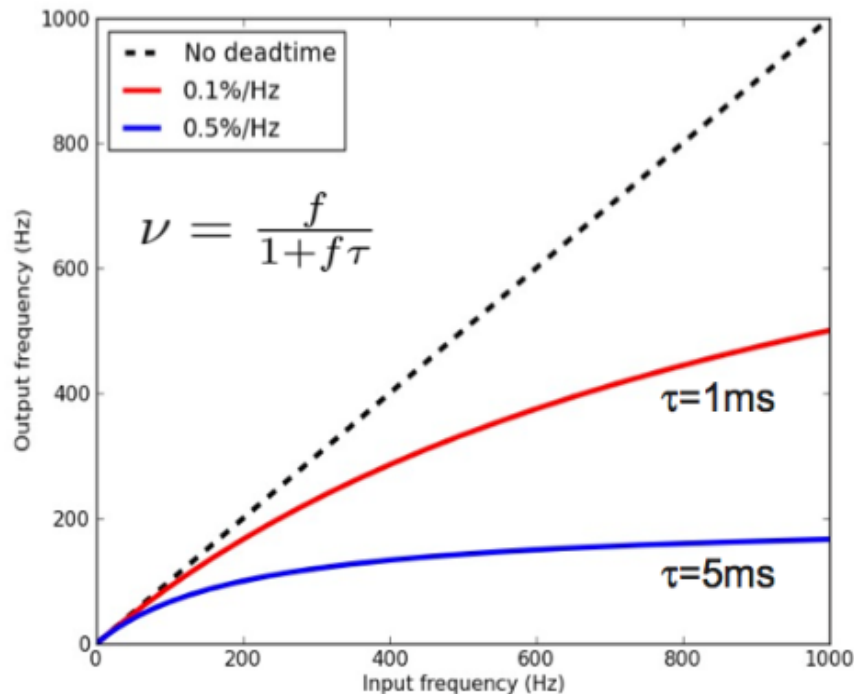- **Signals are incoming at an approximate fixed rate**

- Need a busy logic

  - Active while trigger decides whether the event should be kept or not

  - Induces a deadtime in the system

  - <u>System will only accept a fraction of the triggers</u> $\quad \nu = f(1 - \nu\tau) \Rightarrow \nu = \dfrac{f}{1 + f\tau} < f$
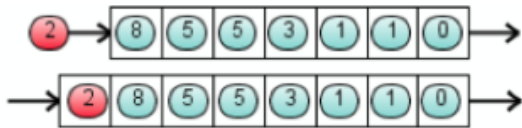
input rate   teadout time

- **System tends to be inefficient for long readout times**

Derandomizing buffer

- **A fast, intermediate buffer can be introduced**

  - Works as a FIFO queue

    (First In First Out)

  - Smooths fluctuations = derandomizes

  - Decouples the slow readout from the fast front-end

- **A moderate size buffer is able to retain good efficiency**

- The ADC are synchronous with beam crossings

- Trigger output is stochastic
  - → FIFO is needed to derandomize

- **ATLAS LHC Run I architecture**
  - → May need to accommodate several levels with increased complexity
  - → If first layer latency is smaller than bunch crossing than the combined latency is $v_{L1} \times t_{L2}$
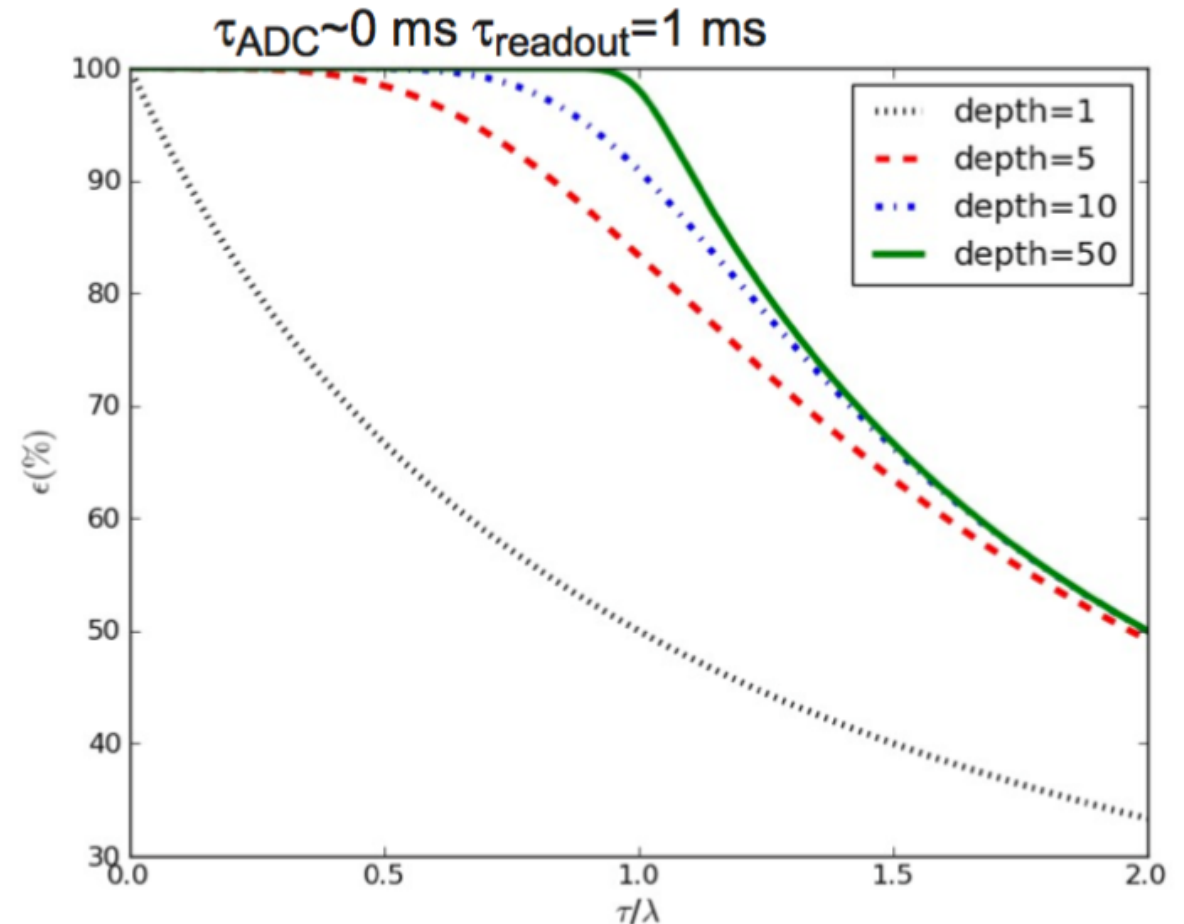
Simplified trigger system for bunched beams

- The ADC are synchronous with beam crossings

- Trigger output is stochastic

  - FIFO is needed to derandomize

- **ATLAS LHC Run I architecture**
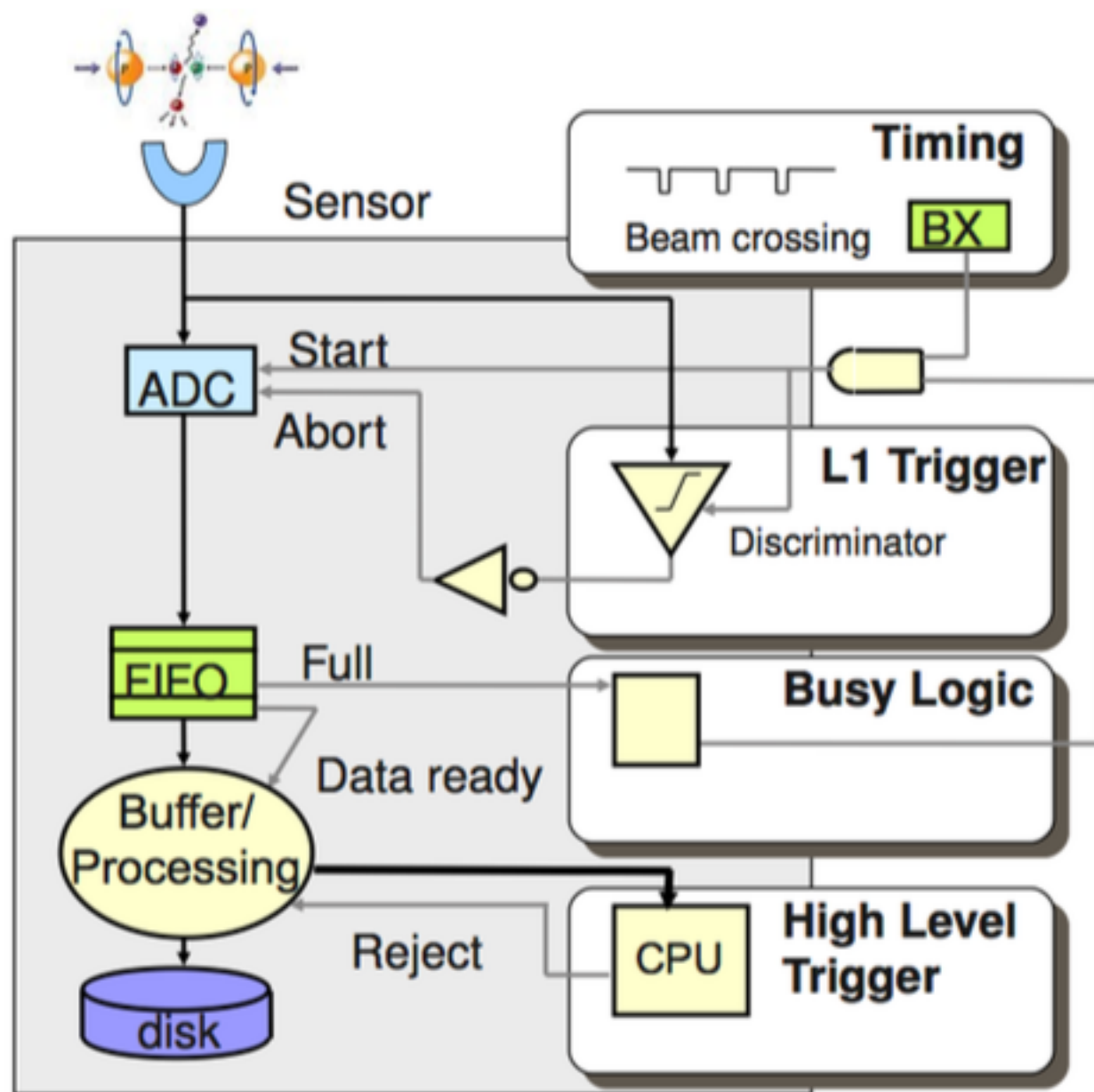
  - May need to accommodate several levels with increased complexity

  - If first layer latency is smaller than bunch crossing than the combined latency is $v_{L1} \times t_{L2}$

- **CMS architecture**

  - Add trigger level between readout and storage

  - CPU Farm used for high level trigger

  - Can access some/all processed data

  - Perform partial/full reconstruction

Information for level 1 trigger

- **Can only use a sub-set of information**

  - Typically energy sums, threshold flags, coarser detector, tracklets

  - Resolutions (energy and position) are coarser by definition
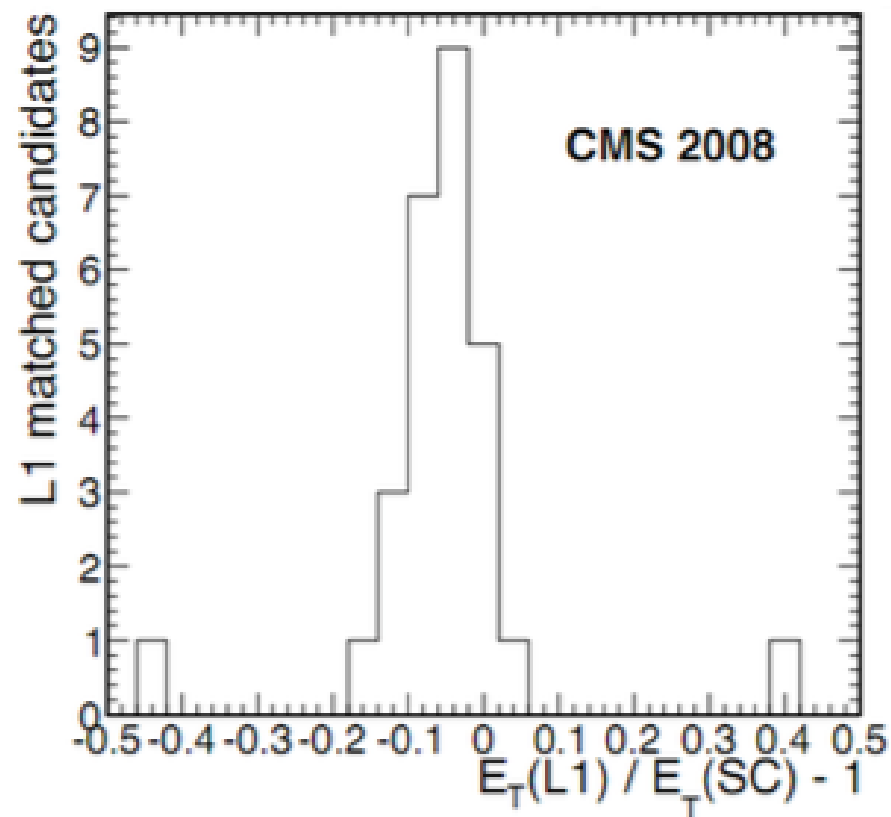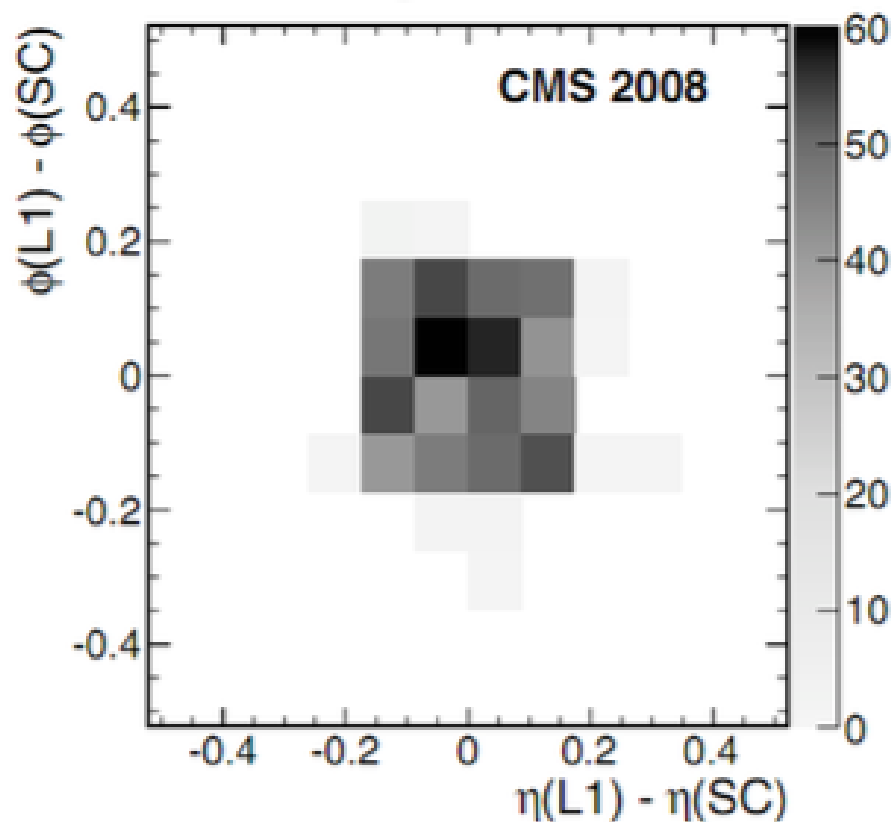
Tracking at L1 (muon example)

Reconstruct segments in each muon chamber
Combine segments to form track
and measure p_T (rough)
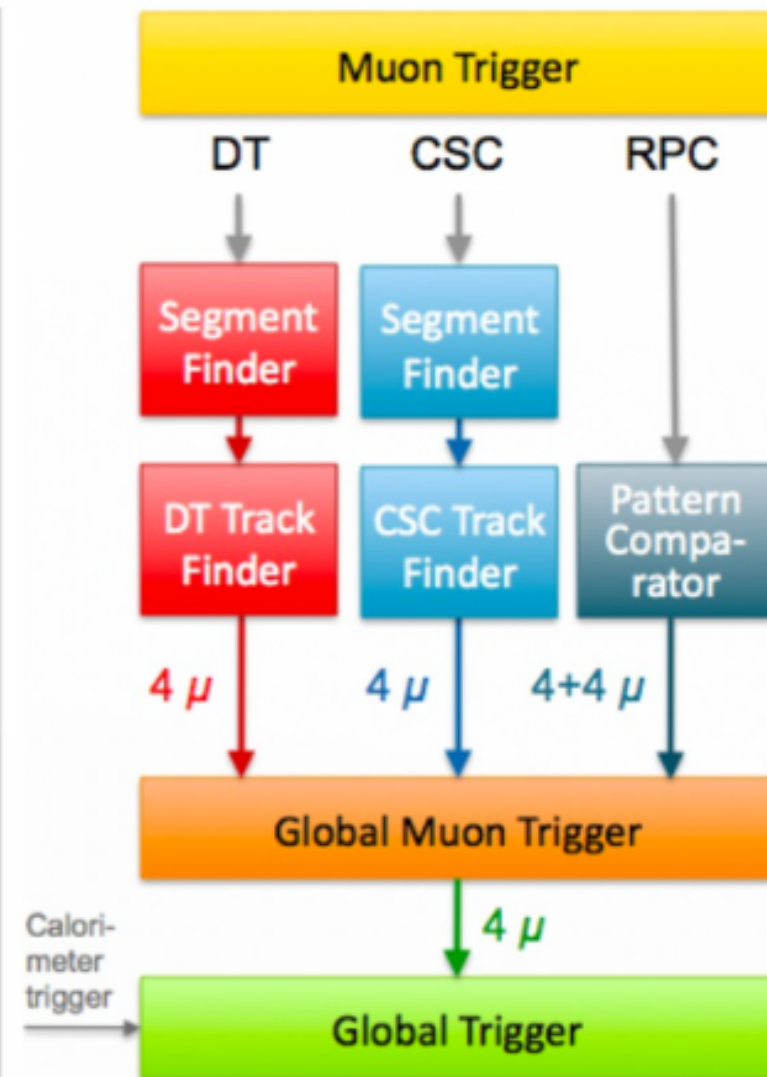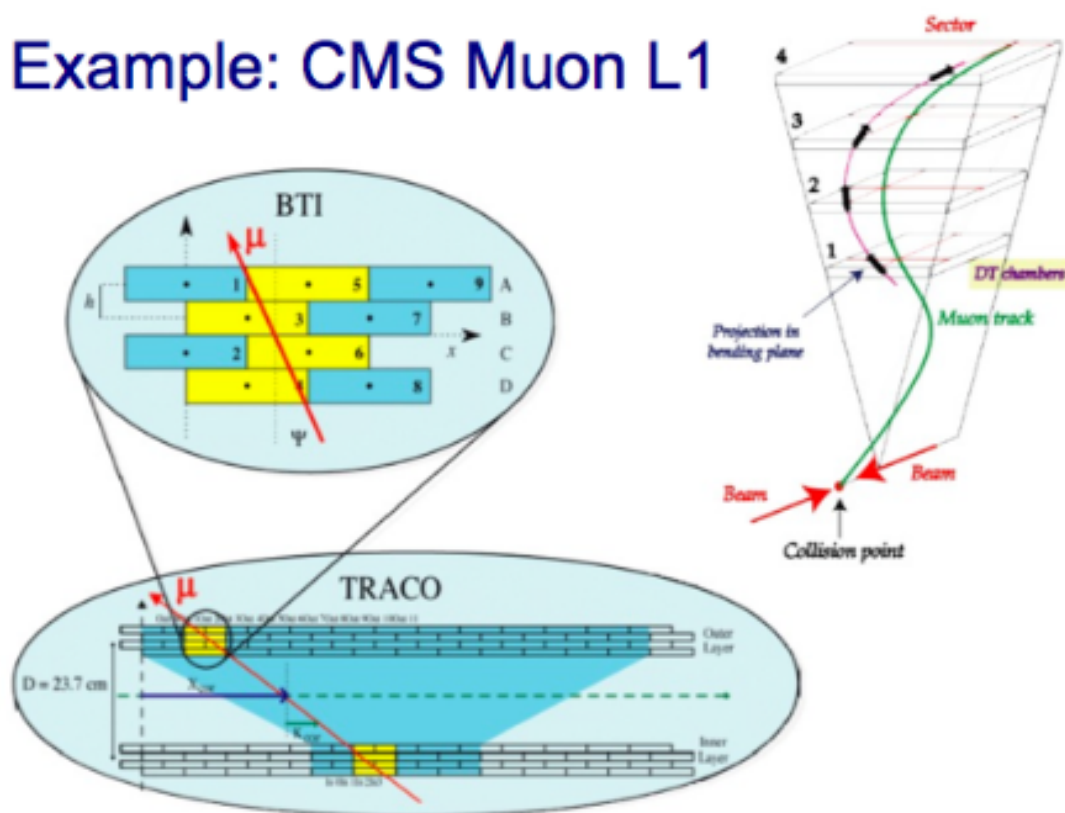
Example: CMS Muon L1

Example: CMS L1 Trigger
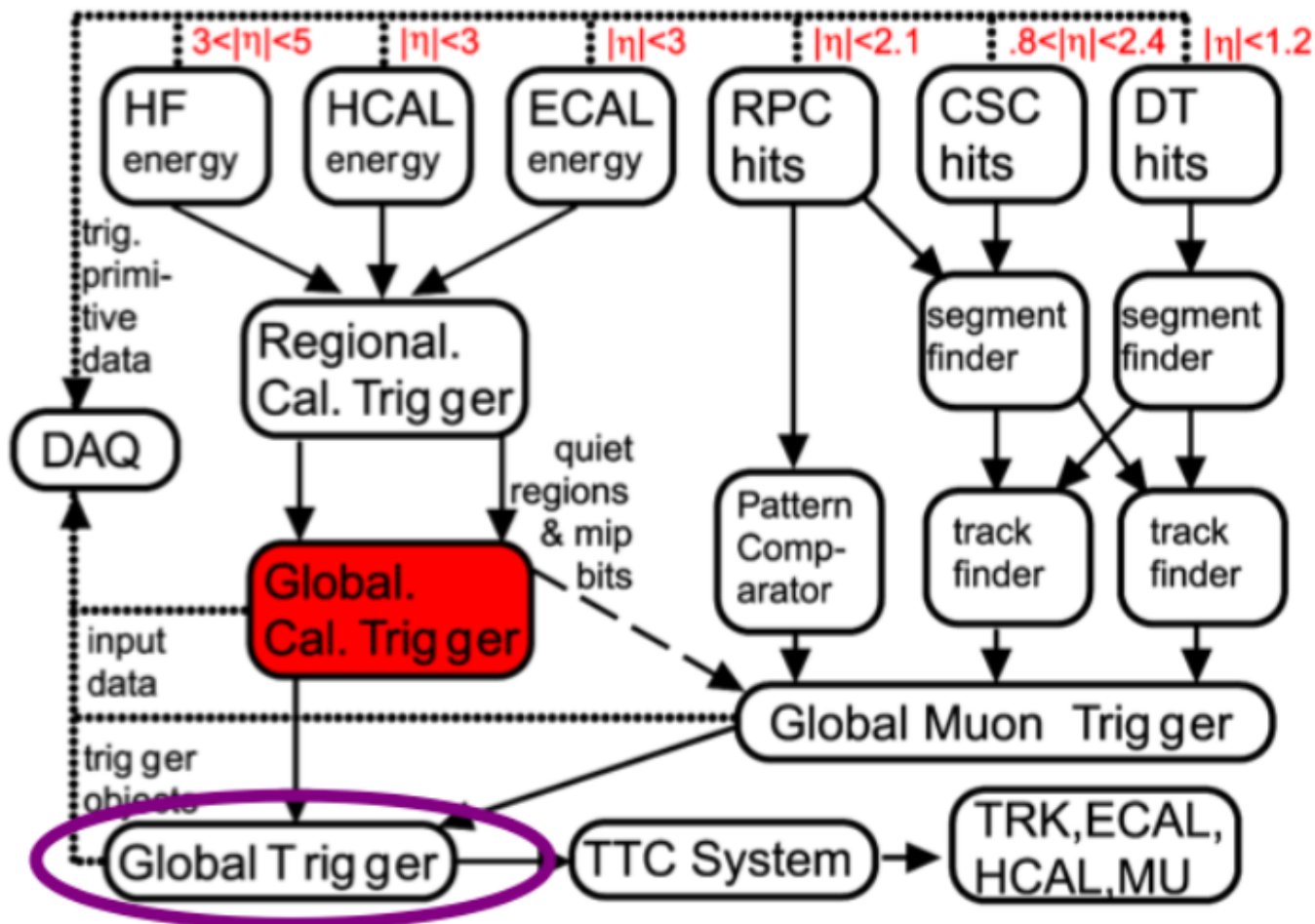
Accommodate several sources

- Busy logic needs to be included
- Can perform a global OR
- Or combine certain trigger objects and apply simple topological cuts
- High level quantities (masses, square roots are expensive! Avoid if possible

TIME

~3µs

Much of the time spent on signal transmission (here CMS)

Level-1 Accept/Reject

Synchronization delay

Level-1 signal distribution

Global Trigger Processor

Regional Trigger Processors

Trigger Primitive Generation

Synchronization delay

Data transportation to Control Room

Detector FrontEnd Digitizer
Particle Time of Fligth

Light cone

SPACE

Control Room

Experiment
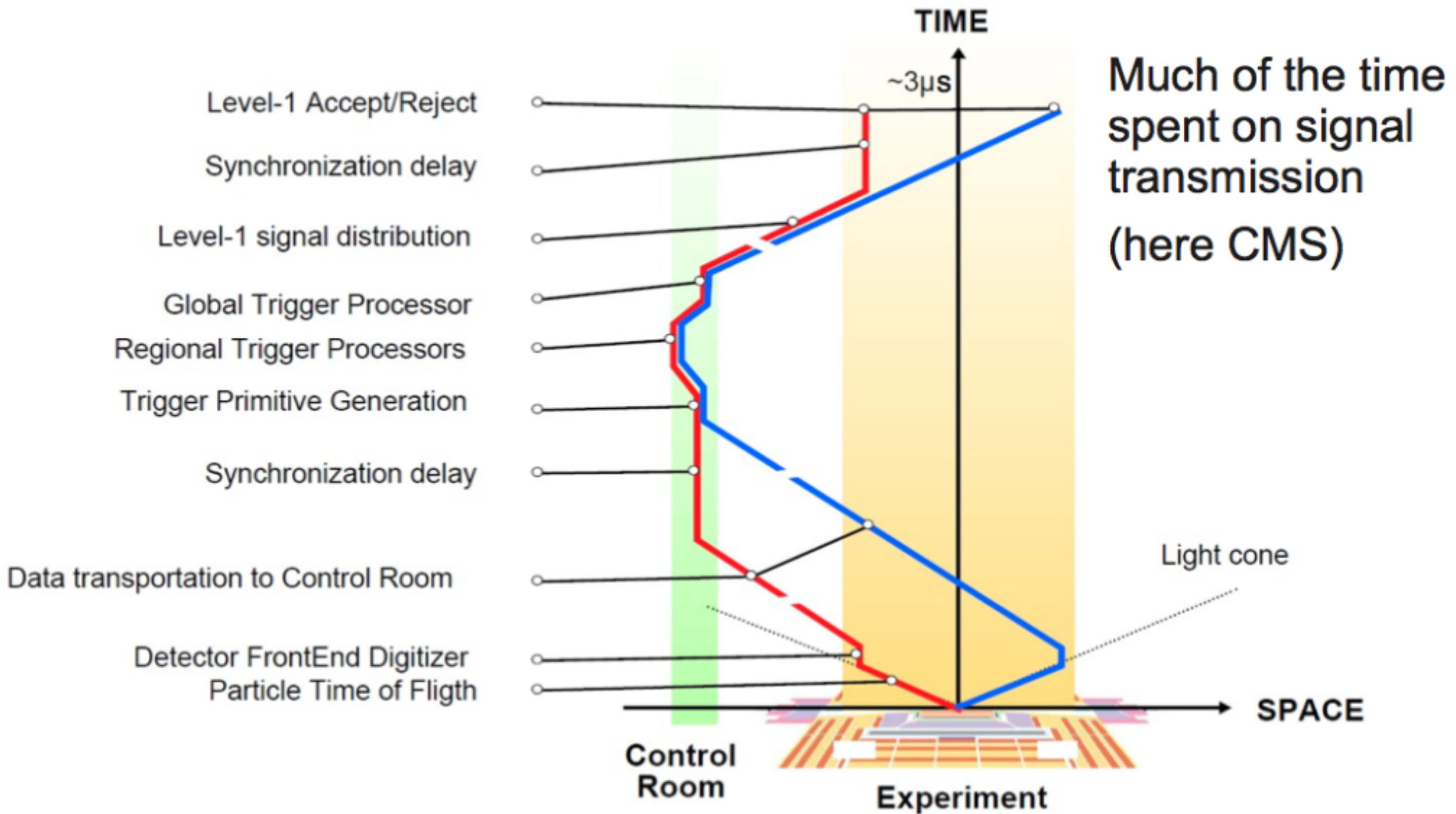
Event building

- Parallelize the sum of the parts of the event to build = slicing

- At CMS 8 independent "slices" are used in order to achieve a 100 kHz rate
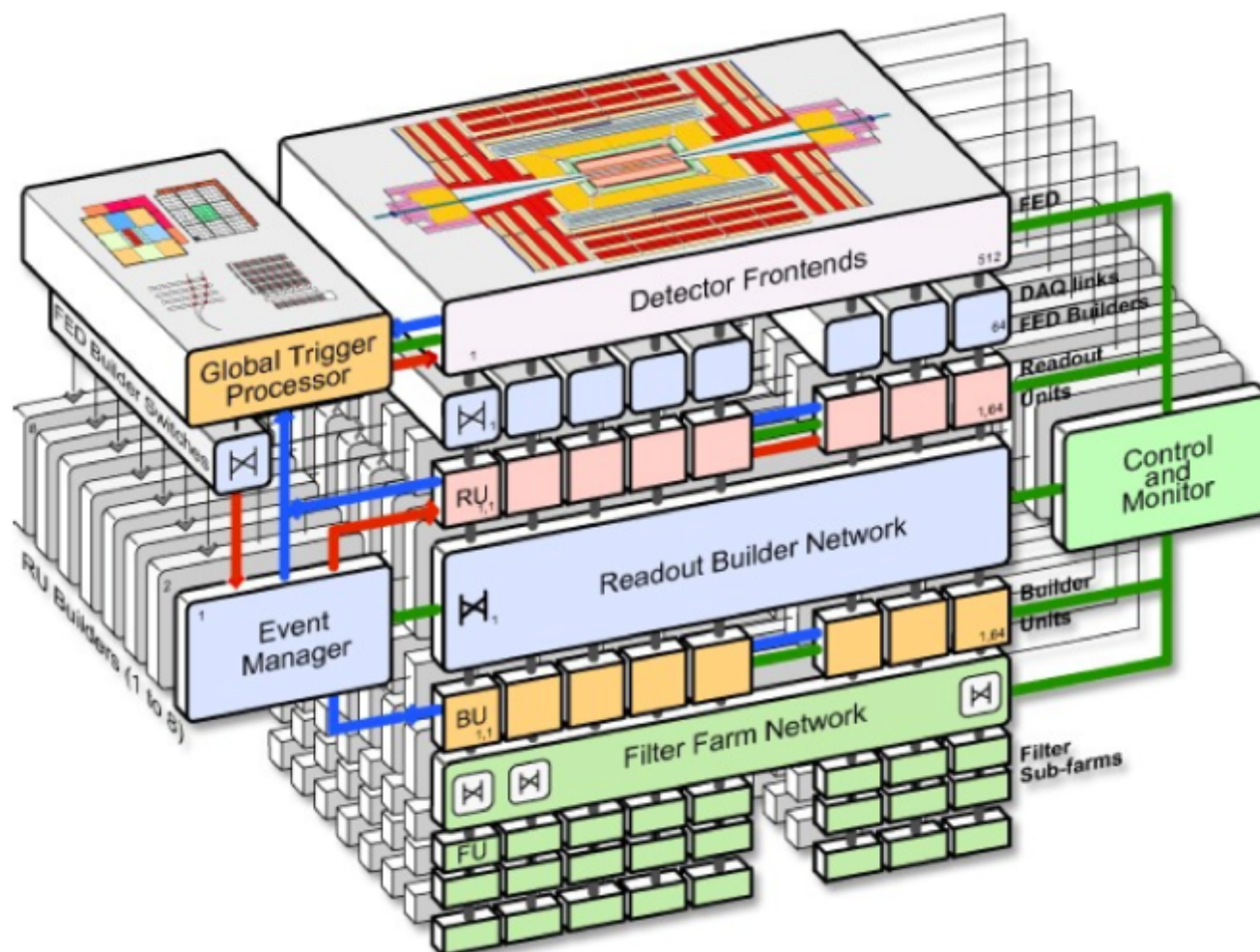
High level trigger

- After event is built can be shipped to a farm for processing before storage

- Events are independent : easy to parallelize

- Keep out rate at ~300Hz / latency at ~40-50 ms, can afford to use
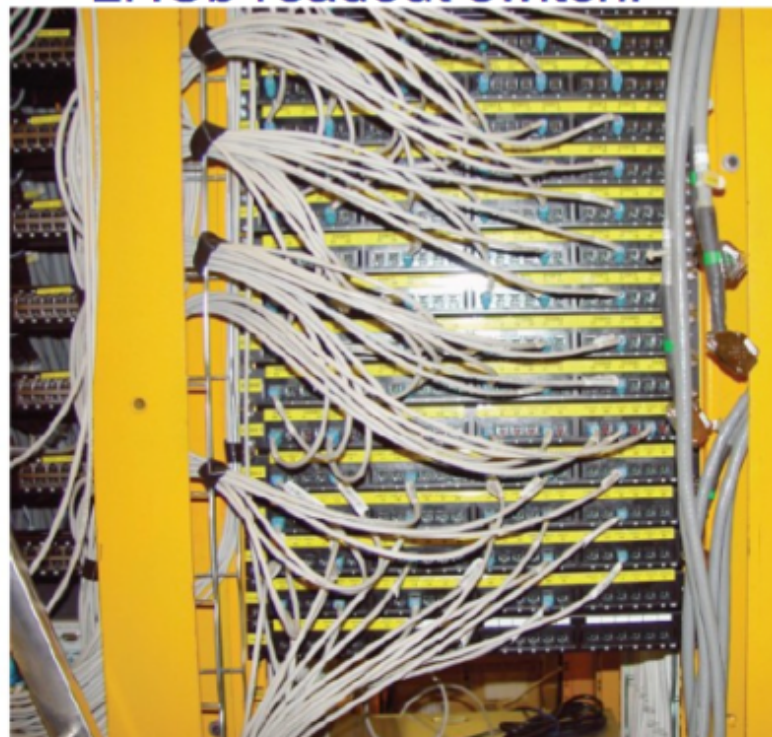
    - high granularity of the detectors

    - offline reconstruction-like algorithms

ATLAS HLT farm:

LHCb readout switch:

LHC trigger/DAQ comparison

- Typical values for LHC run I

  - May depend on luminosity

- Notice that the final bandwidth has to be kept

  - total trigger rate must not exceed allocated bandwidth

  - prescale triggers if needed

Collider	ATLAS	CMS	LHCb	ALICE
L1 latency [μs]	2.5	3.2	4	1.2/6/88
L1 output rate [kHz]	75	100	1000	2
FE readout bandwidth [GB/s]	120	100	40	25
Max. average latency at HLT [ms]	40 (EF 1000)	50	20	
Event building bandwidth [ms]	4	100	40	25
Trigger output rate [Hz]	200	300	2000	50
Output bandwidth [MB/s]	300	300	100	1200
Event size [MB]	1.5	1	0.035	Up to 20

A note on trigger efficiency

Does the trigger record all signal events?
Different ways to measure trigger efficiency
- "tag-and-probe"
  Trigger on 1 particle from resonance and
  measure how often 2nd particle is triggered
- "Boot-strap"
  Use looser (prescaled) trigger line
- "Orthogonal" trigger
  Trigger on one physics signature, measure a different
- Simulation
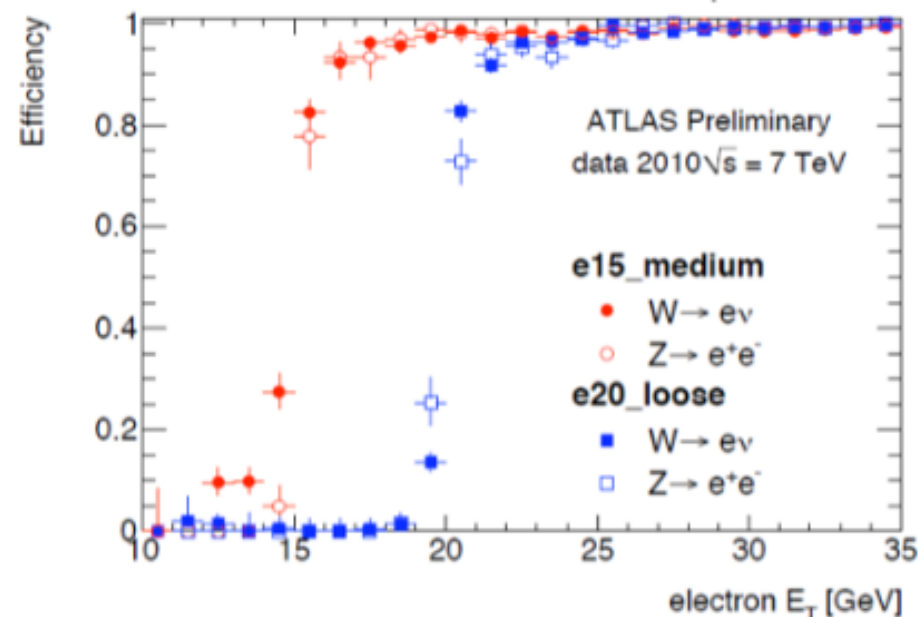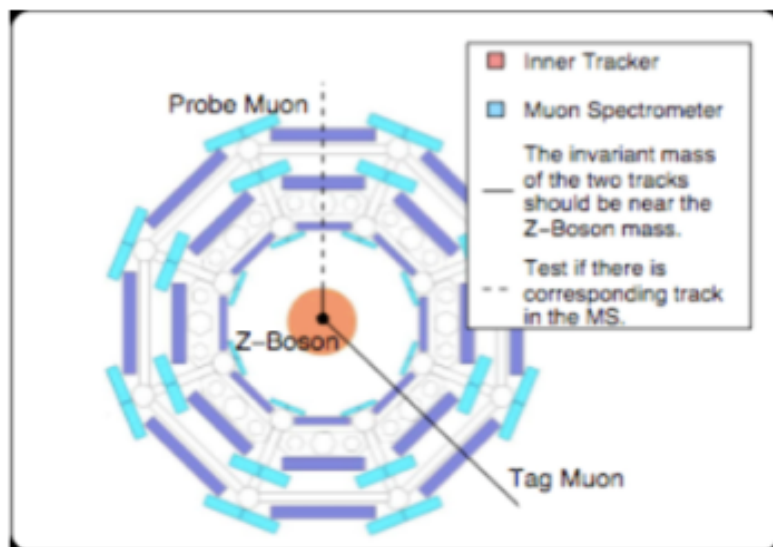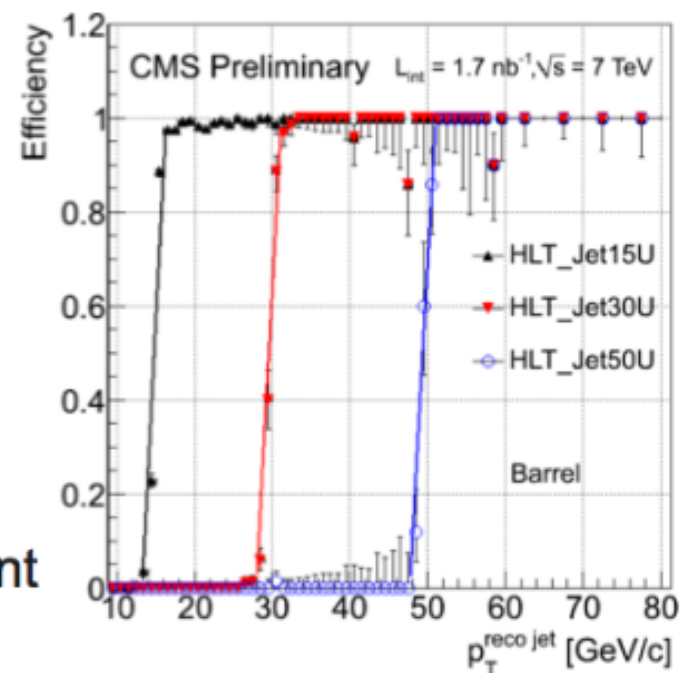
Summary

Summary

- **Tracking system is crucial for reconstruction**

  - **Detector design must be physics-driven: optimal reconstruction+performance**

  - **Combine powerful tracker with field integral: base for particle-flow**

- **Trigger is where the analysis starts**

  - **Must reduce initial rate by almost 10^5 : make sure nothing of interest is lost**

  - **Possible to cope with high rates with dedicated architectures**

  - **Collection of triggers must allow for self-calibration (i.e. efficiency measurement)**

Bibliography

- Particle data group, "2013 Review of Particle Physics", PRD 86 010001 (2012)

- CMS Collaboration, "The CMS experiment at the CERN LHC", JINST 3 (2008) S08004

- D. Bortoletto, "Detectors for particle physics – semiconductors", Purdue

- A. David, "Tracking and trigger", LIP

- M. Kranmer, "Silicon detectors", HEPHY